

RL78/G11

RENESAS MCU

R01DS0282EJ0260 Rev.2.60 Mar 29, 2024

True low-power platform (58.3 μ A/MHz, and 0.64 μ A for operation with only LVD) for the general-purpose applications, with 1.6-V to 5.5-V operation, 16-Kbyte code flash memory, and 33 DMIPS at 24 MHz

1. OUTLINE

1.1 Features

Ultra-low power consumption technology

- VDD = 1.6 V to 5.5 V
- HALT mode
- STOP mode
- SNOOZE mode

RL78 CPU core

- CISC architecture with 3-stage pipeline
- Minimum instruction execution time: Can be changed from high speed (0.04167 μs: @ 24 MHz operation with high-speed on-chip oscillator) to ultra-low speed (66.6 μs: @ 15 kHz operation with low-speed on-chip oscillator clock)
- Multiply/divide/multiply & accumulate instructions are supported.
- Address space: 1 Mbytes
- General-purpose registers: (8-bit register × 8) × 4 banks
- On-chip RAM: 1.5 Kbytes

Code flash memory

- Code flash memory: 16 Kbytes
- Block size: 1 Kbytes
- On-chip debug function
- Self-programming (with boot swap function/flash shield window function)

Data flash memory

- Data flash memory: 2 Kbytes
- Back ground operation (BGO): Instructions can be executed from the program memory while rewriting the data flash memory.
- Number of rewrites: 1,000,000 times (TYP.)
- Voltage of rewrites: VDD = 1.8 to 5.5 V

High-speed on-chip oscillator

- Select from 48 MHz, 24 MHz, 16 MHz, 12 MHz, 8 MHz, 6 MHz, 4 MHz, 3 MHz, 2 MHz, and 1 MHz
- High accuracy: ±1.0% (VDD = 1.8 to 5.5 V, TA = -20 to +85°C)

Middle-speed on-chip oscillator

Selectable from 4 MHz, 2 MHz, and 1 MHz.

Operating ambient temperature

- TA = -40 to +85°C (A: Consumer applications)
- TA = -40 to +105°C (G: Industrial applications)

Power management and reset function

- On-chip power-on-reset (POR) circuit
- On-chip voltage detector (LVD) (Select interrupt and reset from 14 levels)

Data transfer controller (DTC)

- Transfer modes: Normal transfer mode, repeat transfer mode, block transfer mode
- Activation sources: Activated by interrupt sources
- Chain transfer function

Event link controller (ELC)

 Event signals of 18 types can be linked to the specified peripheral function.

Serial interfaces

- Simplified SPI (CSI Note 1): 4 channels
- UART: 2 channels
- I²C/simplified I²C: 4 channels
- Multimaster I²C: 2 channels

Timers

• 16-bit timer (TAU): 4 channels

TKB: 1 channel

12-bit interval timer: 1 channel

8-bit interval timer: 2 channels

Watchdog timer: 1 channel

A/D converter

● 8/10-bit resolution A/D converter (VDD = 1.6 to 5.5 V)

Analog input: 10 to 11 channels

 Internal reference voltage (1.45 V) and temperature sensor

D/A converter

8/10-bit resolution D/A converter (VDD = 1.6 to 5.5 V)

 Analog input: 2 channels (channel 1: output to the ANO1 pin, channel 0: output to the comparator)

Output voltage: 0 V to VDDReal-time output function

Comparator

2 channels

 Operating modes: Comparator high-speed mode, comparator low-speed mode, window mode

PGA

1 channels

I/O ports

 I/O port: 17 to 21 (N-ch open drain I/O [VDD withstand voltage^{Note 2}/EVDD withstand voltage^{Note 3}]: 10 to 14)

 Can be set to N-ch open drain, TTL input buffer, and on-chip pull-up resistor

 Different potential interface: Can connect to a 1.8/2.5/3.0 V device

On-chip key interrupt function

 On-chip clock output/buzzer output controller Others

On-chip BCD (binary-coded decimal) correction circuit

On-chip data operation circuit

Note 1. Although the CSI function is generally called SPI, it is also called CSI in this product, so it is referred to as such in this manual.

Note 2. 16, 20, 24-pin products

Note 3. 25-pin products

Remark The functions mounted depend on the product. See **1.6 Outline of Functions**.

○ ROM, RAM capacities

Flash	Data	RAM			RL78/G11		
ROM	flash	IXAIVI	10 pins	16 pins	20 pins	24 pins	25 pins
16 KB	2 KB	1.5 KB	R5F1051A	R5F1054A	R5F1056A	R5F1057A	R5F1058A

Remark The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F105xA (x = 1, 4, 6, 7, 8): Start address FF900H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

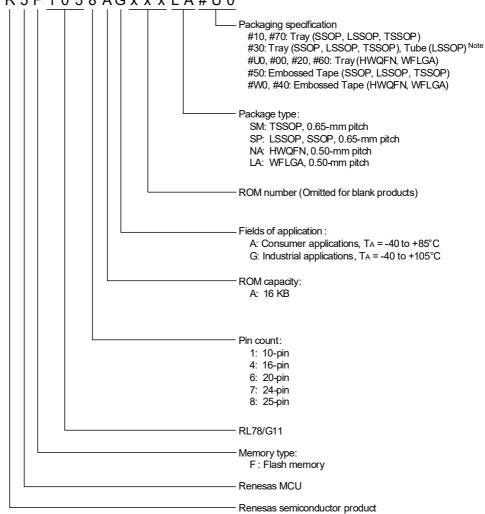
1.2 Ordering Information

<R>

Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G11

Product name

Ordering part number R 5 F $\underline{1}$ 0 $\underline{5}$ 8 A G \underline{x} \underline{x} \underline{x} \underline{L} \underline{A} # \underline{U} 0



Note The packaging specification is only "Tube" for products in the 20-pin LSSOP.

Table 1 - 1 List of Ordering Part Numbers

		_			
Pin		Ordering Part Number	er	RENESAS Code	
Count	Package	Product Name	Packaging Specifications		
10 pins	10-pin plastic LSSOP (4.4 × 3.6 mm, 0.65-mm pitch)	R5F1051AGSP, R5F1051AASP	#10, #30, #50, #70	PLSP0010JA-A	
16 pins	16-pin plastic SSOP (4.4 × 5.0 mm, 0.65-mm pitch)	R5F1054AGSP, R5F1054AASP	#10, #30, #50, #70	PRSP0016JC-B	
	16-pin plastic HWQFN (3 × 3 mm, 0.50-mm pitch)	R5F1054AGNA, R5F1054AANA	#00, #20, #40, #60	PWQN0016KD-A PWQN0016KE-A	
20 pins	20-pin plastic LSSOP (4.4 × 6.5 mm, 0.65-mm pitch)	R5F1056AGSP, R5F1056AASP	#30, #50	PLSP0020JB-A	
	20-pin plastic TSSOP (4.4 × 6.5 mm, 0.65-mm pitch)	R5F1056AGSM, R5F1056AASM	#10, #30, #50, #70	PTSP0020JI-A	
24 pins	24 pip plantia LIMOEN	R5F1057AGNA, R5F1057AANA	#U0, #W0	PWQN0024KE-A	
	24-pin plastic HWQFN (4 × 4 mm, 0.50-mm pitch)	R5F1057AGNA, R5F1057AANA	#00, #20, #40, #60	PWQN0024KF-A PWQN0024KH-A	
25 pins	25-pin plastic WFLGA (3 × 3 mm, 0.50-mm pitch)	R5F1058AGLA, R5F1058AALA	#U0, #W0	PWLG0025KA-A	

Caution 1. For the fields of application, refer to Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G11.

<R>

<R>

<R>

<R>

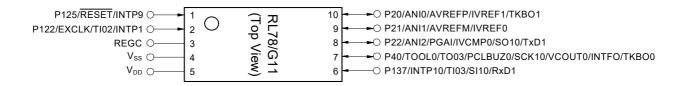
<R>

[•] The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

1.3 Pin Configuration (Top View)

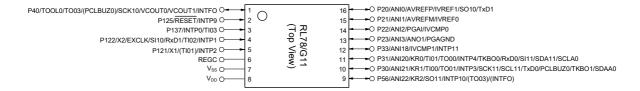
1.3.1 10-pin products

• 10-pin plastic LSSOP (4.4 × 3.6 mm, 0.65-mm pitch)



1.3.2 16-pin products

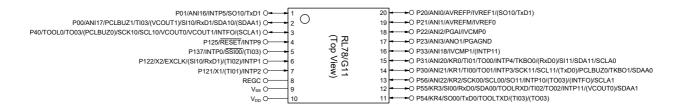
• 16-pin plastic SSOP (4.4 × 5.0 mm, 0.65-mm pitch)



• 16-pin plastic HWQFN (3 × 3 mm, 0.5-mm pitch) → C P30/ANI21/KR1/∏00/T001/INTP3/SCK11/SCL11/TxD0/PCLBUZ0/TKBO1/SDAA0 ►O P31/ANI20/KR0/TI01/T000/INTP4/TKB00/RxD0/S111/SDA11/SCLA0 → O P23/ANI3/ANO1/PGAGND exposed die pad 12 11 10 P22/ANI2/PGAI/IVCMP0 O O P56/ANI22/KR2/SO11/INTP10/(TO03)/(INTFO) 13 O P125/RESET/INTP9 P21/ANI1/AVREFMIVREF0 O RI 78/G11 (Top View) -O P137/INTP0/TI03 P20/ANI0/AVREFP/IVREF1/SO10/TxD1 O 15 P40/TOOL0/TO03/(PCLBUZ0)/SCK10/VCOUT0/VCOUT1/INTFO INDEX MARK P122/X2/EXCLK/SI10/RxD1/TI02/INTP1 O-P121/X1/(TI01)/INTP2 O-REGCO

1.3.3 20-pin products

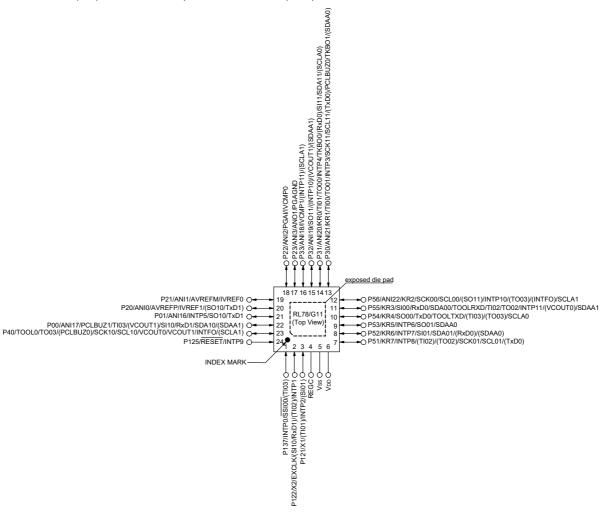
- 20-pin plastic LSSOP (4.4 × 6.5 mm, 0.65-mm pitch)
- 20-pin plastic TSSOP (4.4 × 6.5 mm, 0.65-mm pitch)



- Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μ F).
- Remark 1. For pin identification, see 1.4 Pin Identification.
- **Remark 2.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0 to 3 (PIOR0 to PIOR3).

1.3.4 **24-pin products**

• 24-pin plastic HWQFN (4 × 4 mm, 0.5-mm pitch)

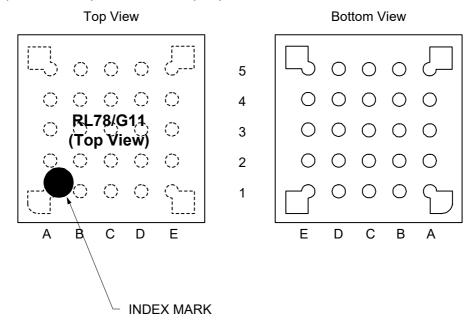


Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μ F).

- Remark 1. For pin identification, see 1.4 Pin Identification.
- Remark 2. It is recommended to connect an exposed die pad to Vss.
- **Remark 3.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0 to 3 (PIOR0 to PIOR3).

1.3.5 **25-pin products**

• 25-pin plastic WFLGA (3×3 mm, 0.5-mm pitch)



	Α	В	С	D	E	
5	P40/TOOL0/TO03/(PC LBUZ0)/SCK10/SCL10 /VCOUT0/VCOUT1/IN TFO/(SCLA1)	P125/RESET/INTP9	P01/ANI16/INTP5/SO1 0/TxD1	P20/ANI0/AVREFP/IV REF1/(SO10/TxD1)	P21/ANI1/AVREFM/IV REF0	5
4	P122/X2/EXCLK/(SI10 /RxD1)/(TI02)/INTP1	P137/INTP0/SSI00/(TI 03)	P00/ANI17/PCLBUZ1/ TI03/(VCOUT1)/SI10/ RxD1/SDA10/(SDAA1)	P22/ANI2/PGAI/IVCM P0	P23/ANI3/ANO1/PGA GND	4
3	P121/X1/(TI01)/INTP2/ (SI01)	Vdd	EVDD	P33/ANI18/IVCMP1/(I NTP11)/(SCLA1)	P32/ANI19/SO11/(INT P10)/(VCOUT1)/(SDA A1)	3
2	REGC	Vss	P30/ANI21/KR1/TI00/T O01/INTP3/SCK11/SC L11/(TxD0)/PCLBUZ0/ TKBO1/(SDAA0)	P31/ANI20/KR0/TI01/T O00/INTP4/TKBO0/(R xD0)/SI11/SDA11/(SC LA0)	P56/ANI22/KR2/SCK0 0/SCL00/(SO11)/INTP 10/(TO03)/(INTFO)/SC LA1	2
1	P51/KR7/INTP8/(TI02) /(TO02)/SCK01/SCL01 /(TxD0)	P52/KR6/INTP7/SI01/ SDA01/(RxD0)/(SDAA 0)	P53/KR5/INTP6/SO01/ SDAA0	P54/KR4/SO00/TxD0/ TOOLTXD/(TI03)/(TO0 3)/SCLA0	P55/KR3/SI00/RxD0/S DA00/TOOLRXD/TI02/ TO02/INTP11/(VCOUT 0)/SDAA1	1
	A	В	С	D	E	

Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1 μ F).

Remark 1. For pin identification, see 1.4 Pin Identification.

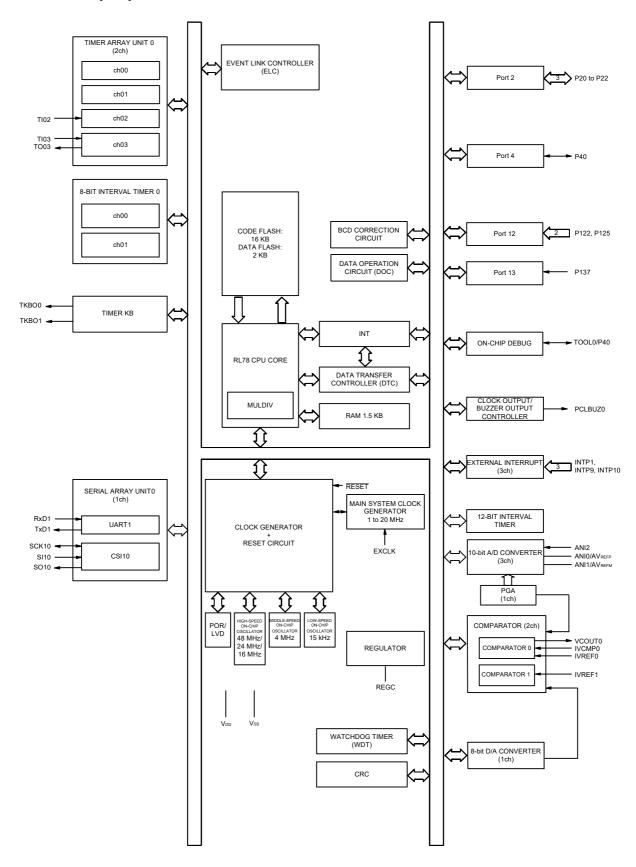
Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0 to 3 (PIOR0 to PIOR3).

1.4 Pin Identification

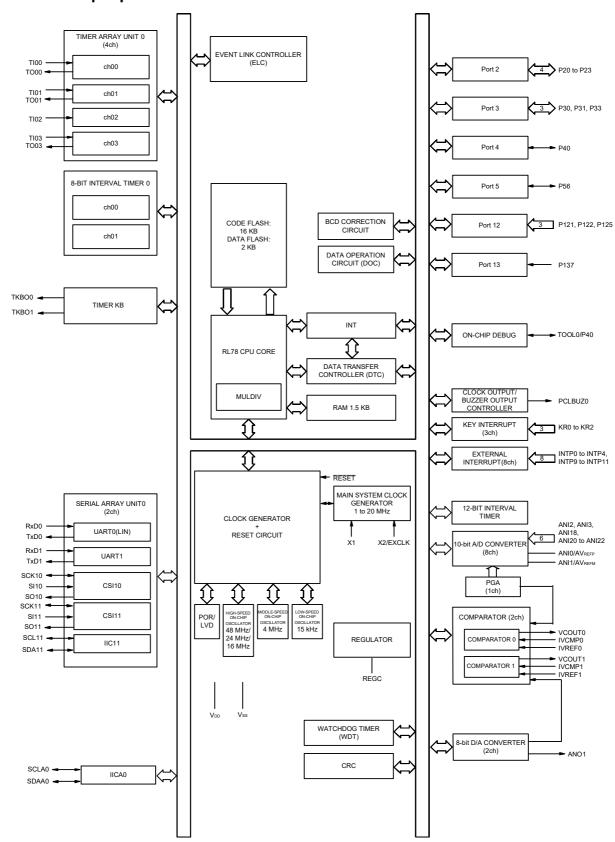
ANI0 to ANI3, PCLBUZ0, PCLBUZ1 : Programmable clock output/buzzer ANI16 to ANI22 : Analog input output ANO1 **REGC** : Regulator capacitance : Analog output **AV**REFM : A/D converter reference RESET : Reset potential (- side) input RxD0, RxD1 : Receive data SCK00, SCK01, **AV**REFP : A/D converter reference potential (+ side) input SCK10, SCK11 : Serial clock input/output EVDD : Power supply SCLA0, SCLA1 : Serial clock input/output **EXCLK** SCL00, SCL01, : External clock input (main system clock) SCL10, SCL11 : Serial clock output INTP0 to INTP11 : External interrupt input SDAA0, SDAA1 : Serial data input/output INTFO : Interrupt Flag output SDA00, SDA01, IVCMP0, IVCMP1 : Comparator input SDA10, SDA11 : Serial data input/output IVREF0, IVREF1 : Comparator reference input SI00, SI01, KR0 to KR7 : Key return SI10, SI11 : Serial data input PGAI, PGAGND : PGA Input SO00, SO01, P00 to P01 : Port 0 SO10, SO11 : Serial data output SSI00 P20 to P23 : Port 2 : Serial interface chip select input P30 to P33 : Port 3 TI00 to TI03 : Timer input P40 : Port 4 TKBO0, TKBO1 : TMKB output P51 to P56 : Port 5 TO00 to TO03 : Timer output P121, P122, P125 : Port 12 TOOL0 : Data input/output for tool P137 : Port 13 TOOLRXD, TOOLTXD : Data input/output for external device TxD0, TxD1 : Transmit data VCOUT0, VCOUT1 : Comparator output VDD : Power supply Vss : Ground X1, X2 : Crystal oscillator (main system clock)

1.5 Block Diagram

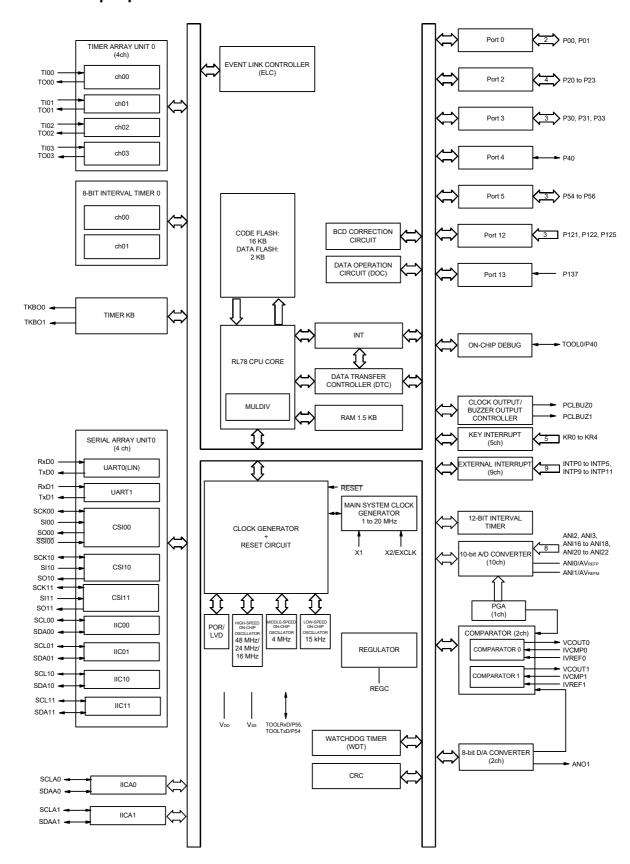
1.5.1 10-pin products



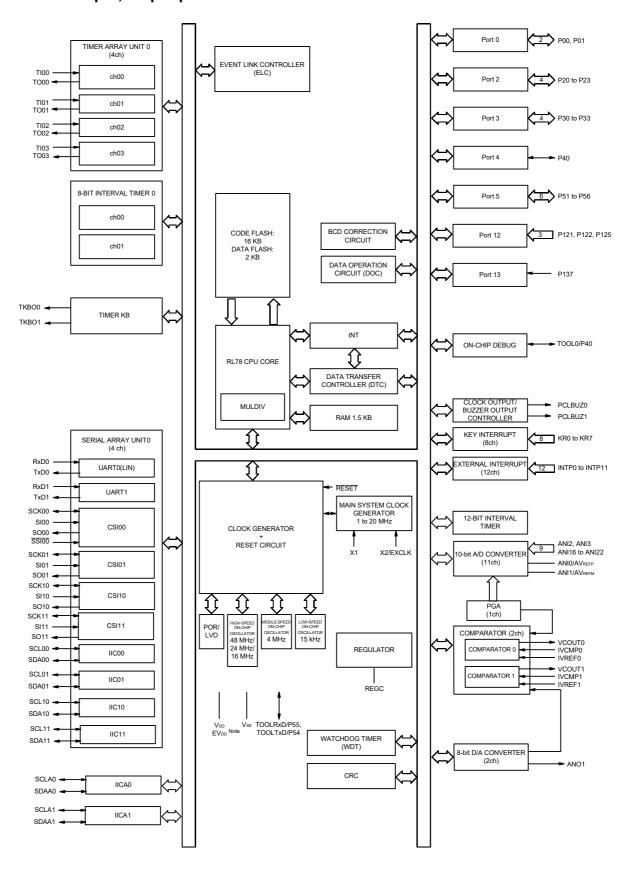
1.5.2 16-pin products



1.5.3 20-pin products



1.5.4 24-pin, 25-pin products



Note 25-pin products

1.6 Outline of Functions

This outline describes the functions at the time when Peripheral I/O redirection register 0 to 3 (PIOR0 to PIOR3) are set to 00H.

(1/2)

	Item	10-pin	16-pin	20-pin	24-pin	25-pin			
		R5F1051A	R5F1054A	R5F1056A	R5F1057A	R5F1058A			
Code flash	memory (KB)	16 Kbytes							
Data flash r	memory (KB)	2 Kbytes							
RAM				1.5 Kbytes					
Address sp	ace	1 Mbytes							
Main system clock	High-speed system clock (fmx)	X1 (crystal/ceramic) oscillation ^{Note} , external main system clock input (EXCLK) 1 to 20 MHz: V _{DD} = 2.7 to 5.5 V 1 to 16 MHz: V _{DD} = 2.4 to 5.5 V 1 to 8 MHz: V _{DD} = 1.8 to 5.5 V							
	High-speed on-chip oscillator clock (fiн) Max: 24 MHz Middle-speed on-chip oscillator clock (fim) Max: 4 MHz								
Subsystem clock	Low-speed on-chip oscillator clock (fiL)	5 kHz (typ.): VDD = 1.6 to 5.5 V							
General-pu	rpose register	8 bits × 32 registers (8 bits × 8 registers × 4 banks)							
Minimum in	struction execution	0.04167 μs (High-speed on-chip oscillator clock: fiн = 24 MHz operation)							
time		0.05 μs (High-speed system clock: f _{MX} = 20 MHz operation)							
Instruction s	set	Data transfer (8/16 bits) Adder and subtractor/logical operation (8/16 bits) Multiplication (8 bits × 8 bits, 16 bits × 16 bits), Division (16 bits ÷ 16 bits, 32 bits ÷ 32 bits) Multiplication and Accumulation (16 bits × 16 bits + 32 bits) Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.							
I/O port	Total	7	13	17	2	1			
	CMOS I/O	4	9	13	1	7			
	CMOS input	3			4				
Timer	16-bit timer	4 channels							
	Watchdog timer	1 channel							
	Timer KB	1 channel							
		1 channel							
	12-bit interval timer								
	8/16-bit interval timer		annel (16 bit)						

Note 16, 20, 24, 25-pin products

Caution The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F105xA (x = 1, 4, 6, 7, 8): Start address FF900H

For the RAM areas used by the flash library, see Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944).

(2/2)

		1		Т		(2		
Iter	n	10-pin	16-pin	20-pin	24-pin	25-pin		
		R5F1051A	R5F1054A	R5F1056A	R5F1057A	R5F1058A		
Clock output/b	ouzzer	(Main system clock: fi	.76 kHz, 1.25 MHz, 2.5 M MAIN = 20 MHz operation) Hz, 938 Hz, 1.875 kHz, 3		2			
10-bit	External	3 channels	8 channels	10 channels	11 channels			
resolution A/D converter	Internal	1 channel	o chaineis	TO CHAIITEIS	TI CII	ailleis		
8-bit D/A conv	erter	1 channel		2 cha	nnels			
Comparator (\ Comparator)	Vindow	1 channel		2 cha	nnels			
PGA		1 channel						
Data Operatio (DOC)	n Circuit	Comparison, addition, a	nd subtraction of 16-bit o	data				
Serial interfac	е	[10-pin products] • Simplified SPI (CSI): 1 channel/UART: 1 channel [16-pin products] • Simplified SPI (CSI): 2 channels/UART: 2 channels/simplified I ² C: 1 channel [20-pin products] • Simplified SPI (CSI): 3 channels/UART: 2 channels/simplified I ² C: 3 channels [24-pin, 25-pin products] • Simplified SPI (CSI): 4 channels/UART: 2 channels/simplified I ² C: 4 channels						
	I ² C bus	None 1 channel 2 channels						
Data transfer (DTC)	controller	13 sources	22 sources	23 sources	24 sources			
Event link con (ELC)	troller	Event input: 11 Event trigger output: 3	Event input: 16 Event trigger output: 4	Event input: 17 Event trigger output: 4	Event input: 18 Event trigger output: 4			
Vectored	Internal	20	24		25			
interrupt sources	External	3	9	10	1	3		
Key interrupt		None	3	5		8		
Reset		Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution Internal reset by RAM parity error Internal reset by illegal-memory access						
Power-on-rese	et circuit	 Power-on-reset: 1.51 ± 0.04V (TA = -40 to +85°C) 1.51 ± 0.06V (TA = +85 to +105°C) Power-down-reset: 1.50 ± 0.04 V (TA = -40 to +85°C) 1.50 ± 0.06V (TA = +85 to +105°C) 						
Voltage	Power on	1.67 V to 4.06 V (14 sta	ges)					
detector	Power down	1.63 V to 3.98 V (14 sta	ges)					
On-chip debu	g function	Provided (Disable to tra	cing)					
Power supply	voltage	V _{DD} = 1.6 to 5.5 V						
Operating am	bient	T _A = -40 to +85°C (Con: T _A = -40 to +105°C (Ind	,					

2. ELECTRICAL SPECIFICATIONS (TA = -40 to +85°C)

This chapter describes the following electrical specifications.

Target products A: Consumer applications (TA = −40 to +85°C)

R5F105xxAxx

G: When the products "G: Industrial applications ($TA = -40 \text{ to } +105^{\circ}\text{C}$)" is used in the range of $TA = -40 \text{ to } +85^{\circ}\text{C}$ R5F105xxGxx

- Caution 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
- Caution 2. The pins mounted depend on the product. Refer to 2.1 Port Functions to 2.2.1 Functions for each product in the RL78/G11 User's Manual.
- Caution 3. The EVDD pin is not present on products with 24 or less pins. Accordingly, replace EVDD with VDD and the voltage condition $1.6 \le \text{EVDD} \le \text{VDD} \le 5.5 \text{ V}$ with $1.6 \le \text{VDD} \le 5.5 \text{ V}$.



2.1 Absolute Maximum Ratings

(1/2)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	VDD		-0.5 to +6.5	V
	EVDD		-0.5 to +6.5	V
	AVREFP		0.3 to V _{DD} + 0.3 Note 2	V
	AVREFM		-0.3 to V _{DD} + 0.3 Note 2 and AVREFM ≤ AVREFP	V
REGC pin input voltage	VIREGC	REGC	-0.3 to +2.8 and -0.3 to V _{DD} + 0.3 ^{Note 1}	V
Input voltage	VI1	P00, P01, P30 to P33, P40, and P51 to P56	51 to -0.3 to EVDD + 0.3 and -0.3 to VDD + 0.3 Note 2	V
	V ₁₂	P20 to P23, P121, P122, P125, P137, EXCLK, RESET	-0.3 to V _{DD} + 0.3 Note 2	V
Output voltage	Vo ₁	P00, P01, P30 to P33, P40, and P51 to P56	-0.3 to EVDD + 0.3 and -0.3 to VDD + 0.3 ^{Note 2}	V
	Vo2	P20 to P23	-0.3 to V _{DD} + 0.3 Note 2	V
Analog input voltage	VAI1	ANI16 to ANI22	-0.3 to EVDD + 0.3 and -0.3 to AVREF(+) + 0.3 Notes 2, 3	V
	VAI2	ANI0 to ANI3	-0.3 to V _{DD} + 0.3 and -0.3 to AV _{REF} (+) + 0.3 Notes 2, 3	V

- Note 1. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
- Note 2. Must be 6.5 V or lower.
- **Note 3.** Do not exceed AVREF (+) + 0.3 V in case of A/D conversion target pin.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter.

That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

- Remark 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
- Remark 2. AVREF (+): + side reference voltage of the A/D converter.
- Remark 3. Vss: Reference voltage

(2/2)

Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Іон1	Per pin		-40	mA
		Total of all pins	P00, P01, P40	-70	mA
		-170 mA	P30 to P33, P51 to P56	-100	mA
	Іон2	Per pin	P20 to P23	-0.5	mA
		Total of all pins		-2	mA
Output current, low lo	IOL1	Per pin		40	mA
		Total of all pins	P00, P01, P40	70	mA
		170 mA	P30 to P33, P51 to P56	100	mA
	lo _{L2}	Per pin	P20 to P23	1	mA
		Total of all pins		4	mA
Operating ambient	ТА	In normal operat	ion mode	-40 to +85	°C
temperature		In flash memory	programming mode		
Storage temperature	Tstg			-65 to +150	°C

Caution

Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark

2.2 Oscillator Characteristics

2.2.1 X1 characteristics

 $(TA = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Resonator	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx) Note	Ceramic resonator/	$2.7 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$	1.0		20.0	MHz
	crystal resonator	2.4 V ≤ VDD < 2.7 V	1.0		16.0	
		1.8 V ≤ VDD < 2.4 V	1.0		8.0	
		1.6 V ≤ VDD < 1.8 V	1.0		4.0	

Note Indicates only permissible oscillator frequency ranges. Refer to 2.4 AC Characteristics for instruction execution time.

Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator, refer to 6.4 System Clock Oscillator in the RL78/G11 User's Manual.

2.2.2 On-chip oscillator characteristics

 $(TA = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Oscillators	Parameters		Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency Notes 1, 2	fıн	2.7 V ≤ VDD ≤ 5.5 V		1		24	MHz
		2.4 V ≤ V _{DD} ≤	5.5 V	1		16	
		1.8 V ≤ V _{DD} ≤	5.5 V	1		8	
		1.6 V ≤ V _{DD} ≤	5.5 V	1		4	
High-speed on-chip oscillator clock frequency accuracy		TA = -20 to	1.8 V ≤ V _{DD} ≤ 5.5 V	-1		1	%
		+85°C	1.6 V ≤ VDD < 1.8 V	-5		5	
		TA = -40 to	1.8 V ≤ V _{DD} ≤ 5.5 V	-1.5		1.5	%
		-20°C	1.6 V ≤ VDD < 1.8 V	- 5.5		5.5	
Middle-speed on-chip oscillator oscillation frequency Note 2	fıм		•	1		4	MHz
Middle-speed on-chip oscillator oscillation frequency accuracy				-12		+12	%
Temperature drift of Middle-speed on-chip oscillator oscillation frequency accuracy	DIMT				0.008		%/°C
Voltage drift of Middle-speed on-chip oscillator oscillation	DIMV	TA = 25°C	2.1 V ≤ V _{DD} ≤ 5.5 V		0.02		%/V
frequency accuracy			2.0 V ≤ V _{DD} < 2.1 V		-12		
			1.6 V ≤ V _{DD} < 2.0 V		10		
Low-speed on-chip oscillator clock frequency Note 2	fiL				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

Note 1. High-speed on-chip oscillator frequency is selected with bits 0 to 3 of the option byte (000C2H) and bits 0 to 2 of the HOCODIV register.

Note 2. This only indicates the oscillator characteristics. Refer to 2.4 AC Characteristics for instruction execution time.



2.3 DC Characteristics

2.3.1 Pin characteristics

$(TA = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le EVDD \le VDD \le 5.5 \text{ V}, Vss = 0 \text{ V})$

(1/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high Note 1	Іон1	Per pin for P00, P01, P30 to P33, P40, and P51 to P56				-10.0 Note 2	mA
		Total of P00, P01, and P40	$4.0 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V}$			-42.0	mA
		(When duty ≤ 70% Note 3)	2.7 V ≤ EV _{DD} < 4.0 V			-10.0	mA
			1.8 V ≤ EV _{DD} < 2.7 V			-5.0	mA
			1.6 V ≤ EV _{DD} < 1.8 V			-2.5	mA
		Total of P30 to P33, and P51 to P56	$4.0 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V}$			-80.0	mA
			2.7 V ≤ EV _{DD} < 4.0 V			-19.0	mA
			1.8 V ≤ EV _{DD} < 2.7 V			-10.0	mA
			1.6 V ≤ EV _{DD} < 1.8 V			-5.0	mA
loi		Total of all pins (When duty ≤ 70% ^{Note 3})				-122.0	mA
	Іон2	Per pin for P20 to P23				-0.1 Note 2	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	1.6 V ≤ VDD ≤ 5.5 V			-0.4	mA

- Note 1. Value of current at which the device operation is guaranteed even if the current flows from the VDD pin to an output pin.
- Note 2. Do not exceed the total current value.
- **Note 3.** Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

```
• Total output current of pins = (IOH \times 0.7)/(n \times 0.01)

<Example> Where n = 80% and IOH = -10.0 mA

Total output current of pins = (-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7 mA
```

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P00, P01, P20, P30 to P33, P40 and P51 to P56 do not output high level in N-ch open-drain mode.

(TA = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(2/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low Note 1	IOL1	Per pin for P00, P01, P30 to P33, P40, and P51 to P56				20.0 Note 2	mA
		Total of P00, P01, and P40	4.0 V ≤ EVDD ≤ 5.5 V			70.0	mA
		(When duty ≤ 70% ^{Note 3})	2.7 V ≤ EV _{DD} < 4.0 V			15.0	mA
			1.8 V ≤ EV _{DD} < 2.7 V			9.0	mA
			1.6 V ≤ EV _{DD} < 1.8 V			4.5	mA
		Total of P30 to P33, and P51 to P56	4.0 V ≤ EV _{DD} ≤ 5.5 V			80.0	mA
		(When duty ≤ 70% Note 3)	2.7 V ≤ EV _{DD} < 4.0 V			35.0	mA
			1.8 V ≤ EV _{DD} < 2.7 V			20.0	mA
			1.6 V ≤ EV _{DD} < 1.8 V			10.0	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})				150.0	mA
	lOL2	Per pin for P20 to P23				0.4 Note 2	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	1.6 V ≤ VDD ≤ 5.5 V			1.6	mA

- Note 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the Vss pin.
- Note 2. Do not exceed the total current value.
- **Note 3.** Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(IoL \times 0.7)/(n \times 0.01)$ <Example> Where n = 80% and IoL = 10.0 mA Total output current of pins = $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

(TA = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(3/5)

Items	Symbol	Conditions	6	MIN.	TYP.	MAX.	Unit
Input voltage, high	VIH1	P00, P01, P30 to P33, P40, and P51 to P56	Normal mode	0.8 EVDD		EVDD	V
	VIH2	P00, P30 to P32, P40, P51 to P56	TTL mode $4.0 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V}$	2.2		EVDD	V
			TTL mode 3.3 V ≤ EV _{DD} < 4.0 V	2.0		EVDD EVDD VDD VDD 0.2 EVDD	V
			TTL mode 1.6 V ≤ EV _{DD} < 3.3 V	1.5			V
	VIH3	P20 to P23 (digital input)	1	0.7 Vdd		VDD	V
	VIH4	P121, P122, P125, P137, EXCLK	K, RESET	0.8 VDD		EVDD EVDD VDD VDD 0.2 EVDD 0.8 0.5	V
Input voltage, low	VIL1	P00, P01, P30 to P33, P40, and P51 to P56	Normal mode	0			V
	VIL2	VIL2 P00, P30 to P32, P40, P51 to P56	TTL mode $4.0 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V}$	0		0.8	V
			TTL mode 3.3 V ≤ EV _{DD} < 4.0 V	0		0.5	V
			TTL mode 1.6 V ≤ EV _{DD} < 3.3 V	0		0.32	V
	VIH3	P20 to P23 (digital input)	•	0		0.3 VDD	V
	VIH4	P121, P122, P125, P137, EXCLK, RESET		0		0.2 VDD	V

Caution The maximum value of VIH of pins P00, P01, P20, P30 to P33, P40 and P51 to P56 is VDD or EVDD, even in the N-ch open-drain mode.

(P20: VDD

P00, P01, P30 to P33, P40, P51 to P56: EVDD)

(Ta = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(4/5)

Items	Symbol	Condi	tions	MIN.	TYP.	MAX.	Unit
Output voltage, high	Voн1	P00, P01, P30 to P33, P40, and P51 to P56	4.0 V ≤ EV _{DD} ≤ 5.5 V, IOH = -10.0 mA	EVDD - 1.5			V
			4.0 V ≤ EVDD ≤ 5.5 V, IOH = -3.0 mA	EVDD - 0.7			V
			2.7 V ≤ EVDD ≤ 5.5 V, IOH = -2.0 mA	EVDD - 0.6			V
			1.8 V ≤ EVDD ≤ 5.5 V IOH = -1.5 mA	EVDD - 0.5			V
			1.6 V ≤ EVDD ≤ 5.5 V, IOH = -1.0 mA	EVDD - 0.5			V
	VOH2	P20 to P23	$1.6~V \le V$ DD $\le 5.5~V$, IOH = -100 μ A	VDD - 0.5			V
Output voltage, low	VOL1	P00, P01, P30 to P33, P40, and P51 to P56	4.0 V ≤ EVDD ≤ 5.5 V, IOL = 20.0 mA			1.3	V
			4.0 V ≤ EVDD ≤ 5.5 V, IOL = 8.5 mA			0.7	V
			2.7 V ≤ EVDD ≤ 5.5 V, IOL = 3.0 mA			0.6	V
			2.7 V ≤ EVDD ≤ 5.5 V, IOL = 1.5 mA			0.4	V
			$1.8 \text{ V} \le \text{EVDD} \le 5.5 \text{ V},$ $\text{IOL} = 0.6 \text{ mA}$			0.4	V
			$1.6 \text{ V} \le \text{EVDD} \le 5.5 \text{ V},$ $\text{IOL} = 0.3 \text{ mA}$			0.4	V
	VOL2	P20 to P23	$1.6~V \leq V_{DD} \leq 5.5~V,$ $I_{OL} = 400~\mu A$			0.4	V

Caution P00, P01, P20, P30 to P33, P40 and P51 to P56 do not output high level in N-ch open-drain mode.

(TA = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(5/5)

Items	Symbol	Cond	itions		MIN.	TYP.	MAX.	Unit
Input leakage current, high	ILIH1	P00, P01, P30 to P33, P40, and P51 to P56	VI = EVDD				1	μА
	ILIH2	P20 to P23, P125, P137, RESET	Vı = V _{DD}				1	μΑ
	Ішнз	P121, P122, X1, X2, EXCLK	VI = VDD	/ı = VDD In input port or external clock input			1	μΑ
				In resonator connection			10	μА
Input leakage current, low	ILIL1	P00, P01, P30 to P33, P40, and P51 to P56	VI = VSS				-1	μА
	ILIL2	P20 to P23, P125, P137, RESET	Vı = Vss				-1	μΑ
	ILIL3	P121, P122, X1, X2, EXCLK	Vı = Vss	In input port or external clock input			-1	μΑ
				In resonator connection			-10	μΑ
On-chip pull-up resistance	Rυ	P00, P01, P30 to P33, P40, P51 to P56, P125	Vı = Vss, In	input port	10	20	100	kΩ

2.3.2 Supply current characteristics

(TA = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(1/4)

Parameter	Symbol				Conditions			MIN.	TYP.	MAX.	Unit
Supply current	I _{DD1}	Operating	Basic	HS (high-speed main)	fHOCO = 48 MHzNote 3	V _{DD} = 5.0 V			1.7		mA
Note 1		mode	operation	mode	f _{IH} = 24 MHz Note 3	V _{DD} = 3.0 V			1.7		
					fHOCO = 24 MHzNote 3	V _{DD} = 5.0 V			1.4		
					f _{IH} = 24 MHz Note 3	V _{DD} = 3.0 V			1.4		
			Normal	HS (high-speed main)	fHOCO = 48 MHzNote 3	V _{DD} = 5.0 V			3.5	6.9	mA
			operation	mode	fiH = 24 MHz Note 3	V _{DD} = 3.0 V			3.5	6.9	
					fHOCO = 24 MHzNote 3	V _{DD} = 5.0 V			3.2	6.3	
				f _{IH} = 24 MHz Note 3	V _{DD} = 3.0 V			3.2	6.3		
					fHOCO = 16 MHzNote 3	V _{DD} = 5.0 V			2.4	4.6	
				fih = 16 MHz Note 3	V _{DD} = 3.0 V			2.4	4.6		
			Normal	LS (low-speed main)	f _{IH} = 8 MHz Note 3	V _{DD} = 3.0 V			1.1	2.0	mA
		operation	mode (MCSEL = 0)		V _{DD} = 2.0 V			1.1	2.0		
			Normal LS (low-speed main)		fiH = 4 MHz Note 3	V _{DD} = 3.0 V			0.72	1.3	mA
			operation	mode		V _{DD} = 2.0 V			0.72	1.3	
				(MCSEL = 1)	f _{IM} = 4 MHz Note 6	V _{DD} = 3.0 V			0.58	1.1	
						V _{DD} = 2.0 V	V _{DD} = 2.0 V		0.58	1.1	
	Normal	LV (low-voltage main)	f _{IH} = 4 MHz Note 3	V _{DD} = 3.0 V			1.2	1.8	mA		
		operation	mode		V _{DD} = 2.0 V			1.2	1.8		
		Normal	LP (low-power main)	f _{IH} = 1 MHz Note 3	V _{DD} = 3.0 V			290	480	μА	
			operation	on mode (MCSEL = 1)		V _{DD} = 2.0 V			290	480	
					f _{IM} = 1 MHz Note 6	V _{DD} = 3.0 V			124	230	
						V _{DD} = 2.0 V			124	230	
			Normal	HS (high-speed main)	f _{MX} = 20 MHz Note 2	V _{DD} = 5.0 V	Square wave input		2.7	5.3	mA
			operation	operation mode			Resonator connection		2.8	5.5	
						V _{DD} = 3.0 V	Square wave input		2.7	5.3	
							Resonator connection		2.8	5.5	
					f _{MX} = 10 MHz Note 2	V _{DD} = 5.0 V	Square wave input		1.8	3.1	
							Resonator connection		1.9	3.2	
						V _{DD} = 3.0 V	Square wave input		1.8	3.1	
							Resonator connection		1.9	3.2	
			Normal	LS (low-speed main)	f _{MX} = 8 MHz Note 2	V _{DD} = 3.0 V	Square wave input		0.9	1.9	mA
			operation	mode (MCSEL = 0)			Resonator connection		1.0	2.0	
			Normal	(WCSEL - U)	f _{MX} = 8 MHz Note 2	V _{DD} = 2.0 V	Square wave input		0.9	1.9	
			operation				Resonator connection		1.0	2.0	
			Normal	LS (low-speed main)	f _{MX} = 4 MHz Note 2	V _{DD} = 3.0 V	Square wave input		0.6	1.1	mA
			operation	mode			Resonator connection		0.6	1.2	
			Normal	(MCSEL = 1)	f _{MX} = 4 MHz Note 2	V _{DD} = 2.0 V	Square wave input		0.6	1.1	
		operation				Resonator connection		0.6	1.2		
			Normal	LP (low-power main)	f _{MX} = 1 MHz Note 2	V _{DD} = 3.0 V	Square wave input		100	190	μА
		operation mod	on mode (MCSEL = 1)			Resonator connection		145	250		
				f _{MX} = 1 MHz Note 2	V _{DD} = 2.0 V	Square wave input		100	190		
		operat					Resonator connection		145	250	

(Notes and Remarks are listed on the next page.)

$(TA = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le EVDD \le VDD \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

(2/4)

Parameter	Symbol		Conditions					MIN.	TYP.	MAX.	Unit
Supply current Note 1	I _{DD1}	Operating mode	Normal operation	clock	f _{IL} = 15 kHz, T _A = -40°C Note 5	Normal operation			1.8	5.9	μА
				operation	f _{IL} = 15 kHz, T _A = +25°C Note 5	Normal operation			1.9	5.9	
					fiL = 15 kHz, T _A = +85°C Note 5	Normal operation			2.3	8.7	

- Note 1. Total current flowing into VDD and EVDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The following points apply in the HS (high-speed main), LS (low-speed main), LV (low-voltage main), and LP (low-power main) modes.
 - The currents in the "TYP." column do not include the operating currents of the peripheral modules.
 - The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the A/D converter, D/A converter, comparator, programmable gain amplifier, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.

In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules.

- Note 2. When the high-speed on-chip oscillator clock, middle-speed on-chip oscillator clock and low-speed on-chip oscillator clock are stopped.
- **Note 3.** When the high-speed system clock, middle-speed on-chip oscillator clock and low-speed on-chip oscillator clock are stopped.
- Note 4. When the high-speed system clock is stopped.
- **Note 5.** When the high-speed system clock, high-speed on-chip oscillator clock and middle-speed on-chip oscillator clock are stopped.
- **Note 6.** When the high-speed system clock, high-speed on-chip oscillator clock and low-speed on-chip oscillator clock are stopped.
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fil: High-speed on-chip oscillator clock frequency (24 MHz max.)
- Remark 3. fim: Middle-speed on-chip oscillator clock frequency (4 MHz max.)
- Remark 4. fil: Low-speed on-chip oscillator clock frequency
- Remark 5. fsub: Subsystem clock frequency (Low-speed on-chip oscillator clock frequency)
- Remark 6. Except subsystem clock operation, temperature condition of the TYP. value is Ta = 25°C

(TA = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(3/4)

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply current	I _{DD2}	HALT	HS (high-speed main) mode	fHOCO = 48 MHzNote 4	$V_{DD} = 5.0 \text{ V}$			0.59	2.43	mA
Note 1	Note 2	mode		f _{IH} = 24 MHz Note 4	$V_{DD} = 3.0 \text{ V}$			0.59	2.43	
				fHOCO = 24 MHzNote 4	V _{DD} = 5.0 V			0.41	1.83	
				f _{IH} = 24 MHz Note 4	$V_{DD} = 3.0 \text{ V}$			0.41	1.83	
				fHOCO = 16 MHzNote 4	V _{DD} = 5.0 V			0.39	1.38	
				fin = 16 MHz Note 4,	V _{DD} = 3.0 V			0.39	1.38	
			LS (low-speed main) mode	f _{IH} = 8 MHz Note 4	V _{DD} = 3.0 V			250	710	μΑ
			(MCSEL = 0)		V _{DD} = 2.0 V			250 710	710	
			LS (low-speed main) mode	f _{IH} = 4 MHz Note 4	f _{IH} = 4 MHz Note 4 V _{DD} = 3.0 V			204	400	μΑ
			(MCSEL = 1)		$V_{DD} = 2.0 \text{ V}$			204	400	
			f _{IM} = 4 MHz Note 6	V _{DD} = 3.0 V			43	250		
					V _{DD} = 2.0 V	V _{DD} = 2.0 V		43	250	
			LV (low-voltage main) mode	f _{IH} = 4 MHz Note 4	V _{DD} = 3.0 V			450	700	μΑ
					V _{DD} = 2.0 V			450	700	
			LP (low-power main) mode	f _{IH} = 1 MHz Note 4	V _{DD} = 3.0 V	V _{DD} = 3.0 V		192	400	μΑ
			(MCSEL = 1)		V _{DD} = 2.0 V			192	400	
			f _{IM} = 1 MHz Note 6	V _{DD} = 3.0 V			28	100		
			V _{DD} = 2.0 V			28	100			
	HS (high-speed main) mode	f _{MX} = 20 MHz Note 3	V _{DD} = 5.0 V	Square wave input		0.20	1.55	mA		
				Resonator connection		0.40	1.74			
					$V_{DD} = 3.0 \text{ V}$	Square wave input		0.20	1.55	
						Resonator connection		0.40	1.74	
				f _{MX} = 10 MHz Note 3	V _{DD} = 5.0 V	Square wave input		0.15	0.86	
						Resonator connection		0.30	0.93	
					V _{DD} = 3.0 V	Square wave input		0.15	0.86	
						Resonator connection		0.30	0.93	
			LS (low-speed main) mode	f _{MX} = 8 MHz Note 3	$V_{DD} = 3.0 \text{ V}$	Square wave input		68	550	μΑ
			(MCSEL = 0)			Resonator connection		125	590	
				f _{MX} = 8 MHz Note 3	$V_{DD} = 2.0 \text{ V}$	Square wave input		68	550	
						Resonator connection		125	590	
			LS (low-speed main) mode	f _{MX} = 4 MHz Note 3	$V_{DD} = 3.0 \text{ V}$	Square wave input		23	128	μΑ
			(MCSEL = 1)			Resonator connection		65	200	
				f _{MX} = 1 MHz Note 3	$V_{DD} = 2.0 \text{ V}$	Square wave input		23	128	
						Resonator connection		65	200	
			LP (low-power main) mode	f _{MX} = 4 MHz Note 3	$V_{DD} = 3.0 \text{ V}$	Square wave input		10	64	μΑ
		(MCSEL = 1)			Resonator connection		59	150		
				f _{MX} = 1 MHz Note 3	$V_{DD} = 2.0 V$	Square wave input		10	64	
						Resonator connection		59	150	
		Subsystem clock operation fil =	fil = 15 kHz, TA = -40°C	Note 5			0.48	1.22	μΑ	
				fil = 15 kHz, TA = +25°C	fil = 15 kHz, T _A = +25°C Note 5 fil = 15 kHz, T _A = +85°C Note 5			0.55	1.22	1
				fil = 15 kHz, TA = +85°C				0.80	3.30	1

(Notes and Remarks are listed on the next page.)

- Note 1. Total current flowing into VDD and EVDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The following points apply in the HS (high-speed main), LS (low-speed main), LV (low-voltage main), and LP (low-power main) modes.
 - The currents in the "TYP." column do not include the operating currents of the peripheral modules.
 - The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the A/D converter, D/A converter, comparator, programmable gain amplifier, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.
 - In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules.
- Note 2. When the HALT instruction is executed in the flash memory.
- **Note 3.** When the high-speed on-chip oscillator clock, middle-speed on-chip oscillator clock, and low-speed on-chip oscillator clock are stopped.
- Note 4. When the high-speed system clock, middle-speed on-chip oscillator clock and low-speed on-chip oscillator clock are stopped.
- **Note 5.** When the high-speed on-chip oscillator clock, middle-speed on-chip oscillator clock and high-speed system clock are stopped.
- **Note 6.** When the high-speed system clock, high-speed on-chip oscillator clock, and low-speed on-chip oscillator clock are stopped.
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fil: High-speed on-chip oscillator clock frequency (24 MHz max.)

 Remark 3. film: Middle-speed on-chip oscillator clock frequency (4 MHz max.)
- Remark 4. fil: Low-speed on-chip oscillator clock frequency
- Remark 5. fsub: Subsystem clock frequency (Low-speed on-chip oscillator clock frequency)

 Remark 6. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

(TA = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(4/4)

Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Supply current	IDD3	STOP mode	TA = -40°C		0.19	0.51	μΑ
Note 1		Note 2	TA = +25°C		0.25	0.51	
			TA = +50°C		0.28	1.10	
		TA = +70°C		0.38	1.90		
			Ta = +85°C		0.60	3.30	

- **Note 1.** Total current flowing into VDD and EVDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. In the STOP mode, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules.
- **Note 2.** For the setting of the current values when operating the subsystem clock in STOP mode, see the current values when operating the subsystem clock in HALT mode.

Peripheral Functions (Common to all products)

(TA = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscillator operating current	I _{FIL} Note 1				0.22		μА
12-bit interval timer operating current	I _{TMKA} Notes 1, 3, 4	f _{IL} = 15 kHz f _{MAIN} stopped (per unit)			0.02		μА
8-bit interval timer operating current	Ітмт	fiL = 15 kHz	8-bit counter mode × 2-channel operation		0.04		μА
Notes 1, 9		fmain stopped (per unit)	16-bit counter mode operation		0.03		μΑ
Watchdog timer operating current	I _{WDT} Notes 1, 3, 5	f _{IL} = 15 kHz f _{MAIN} stopped (per unit)			0.22		μА
A/D converter operating current	I _{ADC} Notes 1, 6	During maximum-speed	Normal mode, AV _{VREFP} = V _{DD} = 5.0 V		1.3	1.7	mA
		conversion	Low voltage mode, AV _{VREFP} = V _{DD} = 3.0 V		0.5	0.7	mA
Internal reference voltage (1.45 V) current Notes 1, 10	IADREF				85.0		μА
Temperature sensor operating current	I _{TMPS} Note 1				85.0		μА
D/A converter operating current	I _{DAC} Notes 1, 14	Per channel				1.5	mA
PGA operating current	I _{PGA} Notes 1, 2				480	700	μА
Comparator operating current	I _{CMP} Note 8	V _{DD} = 5.0 V, Regulator output voltage	Comparator high-speed mode Window mode		12.5		μА
		= 2.1 V	Comparator low-speed mode Window mode		3.0		
			Comparator high-speed mode Standard mode		6.5		
			Comparator low-speed mode Standard mode		1.9		
		V _{DD} = 5.0 V, Regulator output voltage = 1.8 V	Comparator high-speed mode Window mode		8.0		
			Comparator low-speed mode Window mode		2.2		
			Comparator high-speed mode Standard mode	4.0			
			Comparator low-speed mode Standard mode		1.3		
LVD operating current	I _{LVD} Notes 1, 7				0.10		μА
Self-programming operating current	IFSP Notes 1, 12				2.0	12.20	mA
BGO current	IBGO Notes 1, 11				2.0	12.20	mA
SNOOZE operating current	ISNOZ Note 1	ADC operation	Mode transition Note 13		0.50	0.60	mA
		fiH = 24 MHz, AVREFP = VDD = 3.0 V	The A/D conversion operations are performed		1.20	1.44	mA
		Simplified SPI (CSI)/UART	operation fIH = 24 MHz		0.70	0.84	mA
	ISNOZM Note 1	ADC operation	Mode transition Note 13		0.05	0.08	mA
		fim = 4 MHz, AVREFP = VDD = 3.0 V	The A/D conversion operations are performed		0.67	0.78	mA
		Simplified SPI (CSI) operat	ion, fim = 4 MHz		0.06	0.08	mA

(Notes and Remarks are listed on the next page.)



- **Note 1.** Current flowing to VDD.
- Note 2. Operable range is 2.7 to 5.5 V.
- **Note 3.** When the high-speed on-chip oscillator clock, middle-speed on-chip oscillator clock, and high-speed system clock are stopped.
- Note 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.
- Note 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator).

 The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer is in operation.
- **Note 6.** Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
- Note 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.
- Note 8. Current flowing only to the comparator circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2, or IDD3 and ICMP when the comparator circuit is in operation.
- Note 9. Current flowing only to the 8-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 8-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.
- Note 10. Current consumed by generating the internal reference voltage (1.45 V).
- Note 11. Current flowing during programming of the data flash.
- Note 12. Current flowing during self-programming.
- Note 13. For transition time to the SNOOZE mode, see 24.3.3 SNOOZE mode in the RL78/G11 User's Manual.
- **Note 14.** Current flowing only to the D/A converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IDAC when the D/A converter operates in an operation mode or the HALT mode.
- Remark 1. fil: Low-speed on-chip oscillator clock frequency
- Remark 2. fclk: CPU/peripheral hardware clock frequency
- Remark 3. Temperature condition of the TYP. value is TA = 25°C

2.4 AC Characteristics

(TA = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(1/2)

Items	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Instruction cycle	Tcy	Main system clock	HS (high-speed main)	$2.7 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$	0.04167		1	μs
(minimum instruction		(fmain) operation	mode	2.4 V ≤ V _{DD} < 2.7 V	0.0625		1	μs
execution time)			LS (low-speed main) mode	$1.8 \text{ V} \le \text{VDD} \le 5.5 \text{ V}$ PMMC. MCSEL = 0	0.125		1	μs
				1.8 V ≤ VDD ≤ 5.5 V PMMC. MCSEL = 1	0.25		1	
			LP (low-power main) mode	1.8 V ≤ VDD ≤ 5.5 V		1		μs
			LV (low-voltage main) mode	1.6 V ≤ VDD ≤ 5.5 V	0.25		1	μs
		Subsystem clock (fsub) operation	fı∟	1.8 V ≤ VDD ≤ 5.5 V		66.7		μs
		In the self-	HS (high-speed main)	$2.7 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$	0.04167		1	μs
		1, 2	mode	2.4 V ≤ V _{DD} < 2.7 V	0.0625		1	μs
		mode	LS (low-speed main) mode	1.8 V ≤ VDD ≤ 5.5 V	0.125		1	μs
			LV (low-voltage main) mode	1.8 V ≤ VDD ≤ 5.5 V	0.25		1	μs
External system	fEX	$2.7 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$	1		1		20	MHz
clock frequency		2.4 V ≤ V _{DD} < 2.7 \	/		1		16	MHz
		1.8 V ≤ V _{DD} < 2.4 \	1		1		8	MHz
		1.6 V ≤ V _{DD} < 1.8 \	/		1		4	MHz
External system	texH,	$2.7 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$	1		24			ns
clock input high-/low-	texL	2.4 V ≤ VDD < 2.7 V						ns
level width		1.8 V ≤ VDD < 2.4 V						ns
		1.6 V ≤ VDD < 1.8 V			120			ns
TI00 to TI03 input high-/low-level width	ttih, ttil ^{Note}				1/fмск + 10			ns

Note Following conditions must be satisfied on low level interface of EVDD < VDD.

 $1.8 \text{ V} \le \text{EVDD} \le 2.7 \text{ V: MIN. } 125 \text{ ns}$ $1.6 \text{ V} \le \text{EVDD} < 1.8 \text{ V: MIN. } 250 \text{ ns}$

Remark fmck: Timer array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0), n: Channel number (n = 0 to 3))

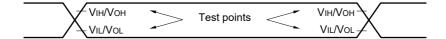
(TA = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(2/2)

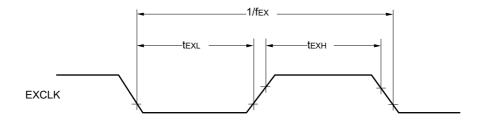
Items	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
TO00 to TO03,	fто	TO00 to TO03,	HS	4.0 V ≤ EVDD ≤ 5.5 V			12	MHz
TKBO0, and TKBO1		TKBO0, and	(high-speed main)	2.7 V ≤ EV _{DD} < 4.0 V			8	
output frequency		TKBO1	mode	1.8 V ≤ EVDD < 2.7 V			4	
Note		(in the case of output from port		1.6 V ≤ EVDD < 1.8 V			2	
		pins other than	LS (low-speed main)	1.8 V ≤ EVDD ≤ 5.5 V			4	
		P20)	mode	1.6 V ≤ EVDD < 1.8 V			2	
			LP (low-power main)	1.8 V ≤ EVDD ≤ 5.5 V			0.5	
			mode					
			LV (low-voltage main) mode	1.6 V ≤ EVDD ≤ 5.5 V			2	
		TKBO1	HS	4.0 V ≤ VDD ≤ 5.5 V			1.5	MHz
		(in the case of output from P20)	(high-speed main)	2.7 V ≤ V _{DD} < 4.0 V			1.2	
			mode	2.4 V ≤ V _{DD} < 2.7 V			1	
			LS (low-speed main)	4.0 V ≤ VDD ≤ 5.5 V			1.5	-
			mode	2.7 V ≤ V _{DD} < 4.0 V			1.2	
				2.4 V ≤ V _{DD} < 2.7 V			1	
				1.8 V ≤ V _{DD} < 2.4 V			0.75	
			LP (low-power main) mode	1.8 V ≤ VDD ≤ 5.5 V			0.5	
			LV (low-voltage main) mode	$4.0 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$			1.5	
				2.7 V ≤ V _{DD} < 4.0 V			1.2	
				2.4 V ≤ V _{DD} < 2.7 V			1	
				1.8 V ≤ V _{DD} < 2.4 V			0.75	
				1.6 V ≤ VDD < 1.8 V			0.5	
PCLBUZ0,	fPCL	HS (high-speed ma	ain) mode	4.0 V ≤ EVDD ≤ 5.5 V			16	MHz
PCLBUZ1				2.7 V ≤ EV _{DD} < 4.0 V			8	
output frequency				1.8 V ≤ EV _{DD} < 2.7 V			4	
				1.6 V ≤ EV _{DD} < 1.8 V			2	
		LS (low-speed mai	n) mode	1.8 V ≤ EVDD ≤ 5.5 V			4	
				1.6 V ≤ EV _{DD} < 1.8 V			2	
		LP (low-power mai	n) mode	1.6 V ≤ EVDD ≤ 5.5 V			1	
		LV (low-voltage ma	nin) mode	1.8 V ≤ EVDD ≤ 5.5 V			4	
				1.6 V ≤ EVDD < 1.8 V			2	1
Interrupt input high-/	tinth,	INTP0 to INTP2, IN	NTP9	1.6 V ≤ VDD ≤ 5.5 V	1			μs
low-level width	tintl	INTP3 to INTP8, IN	NTP10, INTP11	1.6 V ≤ EVDD ≤ 5.5 V	1			
Key interrupt input	tkr	KR0 to KR7		1.8 V ≤ EVDD ≤ 5.5 V	250			ns
low-level width				1.6 V ≤ EVDD < 1.8 V	1			μs
RESET low-level width	trsL				10			μs

Note When duty is 50%.

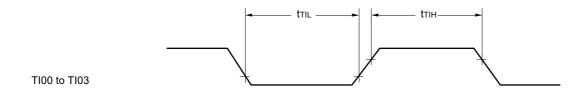
AC Timing Test Points

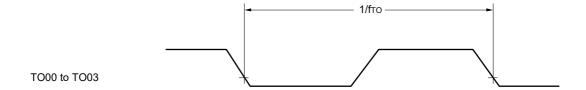


External System Clock Timing

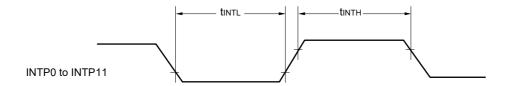


TI/TO Timing

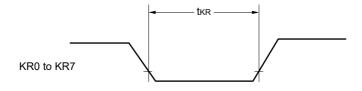




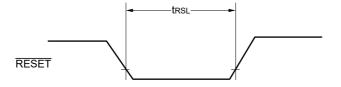
Interrupt Request Input Timing



Key Interrupt Input Timing

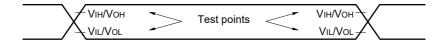


RESET Input Timing



2.5 Peripheral Functions Characteristics

AC Timing Test Points



2.5.1 Serial array unit

(1) During communication at same potential (UART mode)

When P01, P30, P31 and P54 are used as TxDq pins

(TA = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, VSS = 0 V)

Parameter	Symbol	Conditions	, ,	peed main) ode	` .	peed main) ode	` .	ower main) ode	LV (low-vol	,	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		2.7 V ≤ EVDD ≤ 5.5V		fмск/6		fмск/6		fмск/6		fмск/6	bps
Note 1, 2		Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		4.0		1.3		0.1		0.6	Mbps
		1.8 V ≤ EVDD ≤ 5.5 V		fмск/6		fмск/6		fмск/6		fмск/6	bps
		Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		4.0		1.3		0.1		0.6	Mbps
		1.7 V ≤ EVDD ≤ 5.5 V		fмск/6		fмск/6		fмск/6		fмск/6	bps
		Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		4.0		1.3		0.1		0.6	Mbps
		1.6 V ≤ EVDD ≤ 5.5 V	-	_		fмск/6		fмск/6		fмск/6	bps
		Theoretical value of the maximum transfer rate fMCK = fCLK Note 3	-	_		1.3		0.1		0.6	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

Note 2. Following conditions must be satisfied on low level interface of EVDD < VDD.

 $2.4 \text{ V} \le \text{EVDD} < 2.7 \text{ V: MAX.2.6 Mbps}$ $1.8 \text{ V} \le \text{EVDD} < 2.4 \text{ V: MAX.1.3 Mbps}$ $1.6 \text{ V} \le \text{EVDD} < 1.8 \text{ V: MAX.0.6 Mbps}$

Note 3. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: 24 MHz (2.7 V \leq EVDD \leq 5.5 V) 16 MHz (2.4 V \leq EVDD \leq 5.5 V)

LS (low-speed main) mode: 8 MHz (1.8 V \leq EVDD \leq 5.5 V) LP (low-power main) mode: 1 MHz (1.8 V \leq EVDD \leq 5.5 V) LV (low-voltage main) mode: 4 MHz (1.6 V \leq EVDD \leq 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

When P20 is used as TxD1 pin

(TA = -40 to +85°C, 1.6 V \leq EVDD = VDD \leq 5.5 V, VSS = 0 V)

Parameter	Sym bol	Conditions	, ,	h-speed) Mode		peed main) ode	LP (Low-po	ower main) ode	,	ltage main) ode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		4.0 V ≤ V _{DD} ≤ 5.5 V		fMCK/6 Notes 1, 2,		fMCK/6 Notes 1, 2		fMCK/6 Notes 1, 2		fMCK/6 Notes 1, 2	bps
		Theoretical value of the maximum transfer rate fMCK = fCLKNotes 1, 3		1.5		1.3		0.1		0.6	Mbps
		2.7 V ≤ V _{DD} ≤ 5.5 V		fMCK/6 Notes 1, 2,		fMCK/6 Notes 1, 2		fMCK/6 Notes 1, 2		fMCK/6 Notes 1, 2	bps
		Theoretical value of the maximum transfer rate fMCK = fCLKNotes 1, 3		1.2		1.2		0.1		0.6	Mbps
		2.4 V ≤ V _{DD} ≤ 5.5 V		fMCK/6 Notes 1, 2,		fMCK/6 Notes 1, 2		fMCK/6 Notes 1, 2		fMCK/6 Notes 1, 2	bps
		Theoretical value of the maximum transfer rate fMCK = fCLKNotes 1, 3		1.0		1.0		0.1		0.6	Mbps
		1.8 V ≤ VDD ≤ 5.5 V				fMCK/6 Notes 1, 2		fMCK/6 Notes 1, 2		fMCK/6 Notes 1, 2	bps
		Theoretical value of the maximum transfer rate fmck = fclkNotes 1, 3		-		0.6		0.1		0.6	Mbps
		1.7 V ≤ VDD ≤ 5.5 V								fMCK/6 Notes 1, 2	bps
		Theoretical value of the maximum transfer rate fmck = fclkNotes 1, 3		Using prohibited		Using		Using		0.5	Mbps
		1.6 V ≤ VDD ≤ 5.5 V				prohibited		prohibited		fmck/6 Notes 1, 2	bps
		Theoretical value of the maximum transfer rate fMCK = fCLKNotes 1, 3								0.5	Mbps

Note 1. fmck is a frequency selected by setting the CKS bit in the SPS and SMR registers.

Note 2. The transfer rate of 4800 bps is only supported in the SNOOZE mode.

Note that the SNOOZE mode is not supported when fHOCO is 48 MHz.

Note 3. fclk in each operating mode is as follows.:

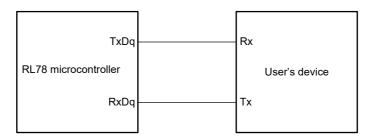
HS (high-speed main) mode: 24 MHz (2.7 V \leq VDD \leq 5.5 V)

16 MHz (2.4 V \leq VDD \leq 5.5 V)

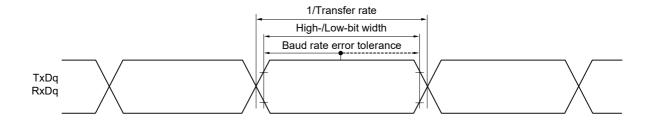
LS (low-speed main) mode: 8 MHz (1.8 V \leq VDD \leq 5.5 V) LP (low-power main) mode: 1 MHz (1.8 V \leq VDD \leq 5.5 V) LV (low-voltage main) mode: 4 MHz (1.6 V \leq VDD \leq 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remark 1. q: UART number (q = 0 and 1), g: PIM and POM number (g = 0, 2, 3 and 5)

Remark 2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03))

(2) During communication at same potential (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

 $(TA = -40 \text{ to } +85^{\circ}C, 2.7 \text{ V} \le EVDD \le VDD \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (high-s	peed main) ode	LS (low-sp Mo	eed main) ode	LP (Low-po	ower main) ode	LV (low-vol	tage main) ode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 2/fcLk	83.3		250		2000		500		ns
SCKp high-/low-level width	tKL1	4.0 V ≤ EVDD ≤ 5.5 V	tксү1/2 - 7		tксү1/2 - 50		tксү1/2 - 50		tксү1/2 - 50		ns
		2.7 V ≤ EVDD ≤ 5.5 V	tксү1/2 - 10								ns
SIp setup time (to SCKp↑)	tsıĸ1	4.0 V ≤ EVDD ≤ 5.5 V	23		110		110		110		ns
		2.7 V ≤ EVDD ≤ 5.5 V	33								ns
SIp hold time (from SCKp↑) Note 2	tksi1		10		10		10		10		ns
Delay time from SCKp↓ to SOp output Note 3	tkso1	C = 20 pF Note 4		10		20		20		20	ns

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **Note 4.** C is the load capacitance of the SCKp and SOp output lines.
- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- Remark 1. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM numbers (g = 5)
- Remark 2. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))

(3) During communication at same potential (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

When P01, P32, P53, P54 and P56 are used as SOmn pins $\,$

 $(TA = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le EVDD \le VDD \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	C	conditions	HS (high-sր Mo	,	,	/-speed Mode	LP (Low main)	v-power mode	LV (low- main)	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle	tkcy1	tkcy1 ≥ 4/fclk	$2.7 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V}$	167		500		4000		1000		ns
time			$2.4 \text{ V} \le \text{EV}_{\text{DD}} \le 5.5 \text{ V}$	250								
			1.8 V ≤ EV _{DD} ≤ 5.5 V	500								
			$1.7 \text{ V} \le \text{EV}_{\text{DD}} \le 5.5 \text{ V}$	1000		1000						
			1.6 V ≤ EVDD ≤ 5.5 V	Using prohibited								
SCKp high-/	t кн1,	4.0 V ≤ EV _{DD} s	≤ 5.5 V	tkcy1/2- 12		tксү1/2		tkcy1/2		tkcy1/2		ns
low-level width	tKL1	2.7 V ≤ EVDD 5	≤ 5.5 V	tксү1/2- 18		- 50		- 50		- 50		
Width		2.4 V ≤ EVDD 5	≤ 5.5 V	tkcy1/2-38								
		1.8 V ≤ EV _{DD} ≤	≤ 5.5 V	tkcy1/2-50								
		1.7 V ≤ EVDD 5	≤ 5.5 V	tkcy1/2- 100		tксу1/2		tkcy1/2		tkcy1/2		
		1.6 V ≤ EV _{DD} s	≤ 5.5 V	Using prohibited		- 100		- 100		- 100		
SIp setup	tsıĸ1	4.0 V ≤ EV _{DD} ≤	≤ 5.5 V	44		110		110		110		ns
time (to SCKp↑)		2.7 V ≤ EV _{DD} s	≤ 5.5 V									
Note 1		2.4 V ≤ EVDD 5	≤ 5.5 V	75								
		1.8 V ≤ EV _{DD} ≤	≤ 5.5 V	110								
		1.7 V ≤ EV _{DD} s	≤ 5.5 V	220		220		220		220		
		1.6 V ≤ EVDD :	≤ 5.5 V	Using prohibited								
SIp hold	tksi1	1.7 V ≤ EVDD 5	≤ 5.5 V	19		19		19		19		ns
time (from SCKp↑) Note 2		1.6 V ≤ EVDD 5	≤ 5.5 V	Using prohibited								
Delay time	tkso1	C = 30 pF	1.7 V ≤ EVDD ≤ 5.5 V		33.4		33.4		33.4		33.4	ns
from SCKp↓ to SOp output Note 3		Note 4	1.6 V ≤ EVDD ≤ 5.5 V		Using prohibited							

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **Note 4.** C is the load capacitance of the SCKp and SOp output lines.
- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- Remark 1. p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)
- Remark 2. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 n: Channel number (mn = 00 to 03))



When P20 is used as SO10 pin

(TA = -40 to +85°C, 1.6 V \leq EVDD = VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	С	conditions	٠. ٠	h-speed Mode		v-speed Mode		v-power mode		-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle	tkcy1	tkcy1 ≥ 4/fclk	$4.0 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	600		600		4000		1000		ns
time			$2.7~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$	850		850	1					
			$2.4 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	1000		1000						
			$1.8 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	_		1500	1			1500		
			$1.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	_		_		_		2000		
			$1.6 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$	_		_		_		1		
SCKp high-/ low-level	tkH1, tkL1	4.0 V ≤ V _{DD} ≤	5.5 V	tксү1/2 - 12		tксү1/2 - 50		tксу1/2 - 50		tксү1/2 - 50		ns
width		2.7 V ≤ V _{DD} ≤	5.5 V	tkcy1/2 - 18								
		2.4 V ≤ V _{DD} ≤	5.5 V	tkcy1/2 - 38								
		1.8 V ≤ V _{DD} ≤	5.5 V	_								
		1.7 V ≤ V _{DD} ≤	5.5 V	_		_		_		tkcy1/2		
		1.6 V ≤ V _{DD} ≤	5.5 V	_		_		_		- 100		
SIp setup	tsıĸ1	4.0 V ≤ V _{DD} ≤	5.5 V	44		110		110		110		ns
time (to SCKp↑)		2.7 V ≤ V _{DD} ≤	5.5 V			1						
Note 1		2.4 V ≤ V _{DD} ≤	5.5 V	75		1						
		1.8 V ≤ V _{DD} ≤	5.5 V	_								
		1.7 V ≤ V _{DD} ≤	5.5 V	_		_		_		220		
		1.6 V ≤ V _{DD} ≤	5.5 V	_		_		_				
SIp hold	tksi1	2.4 V ≤ V _{DD} ≤	5.5 V	19		19		19		19		ns
time (from SCKp↑)		1.8 V ≤ V _{DD} ≤	5.5 V	_		1						
Note 2		1.6 V ≤ V _{DD} ≤	5.5 V	_		_		_				
Delay time	tkso1	C = 30 pF	2.4 V ≤ V _{DD} ≤ 5.5 V		150		250		250		300	ns
from SCKp↓		Note 4	1.8 V ≤ V _{DD} ≤ 5.5 V		_	1						
to SOp output Note 3			1.6 V ≤ V _{DD} ≤ 5.5 V		_		_		_			

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **Note 4.** C is the load capacitance of the SCKp and SOp output lines.
- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- Remark 1. p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 4 and 12)
- Remark 2. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 n: Channel number (mn = 00 to 03))



(4) During communication at same potential (Simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)

When P01, P32, P53, P54 and P56 are used as SOmn pins

 $(TA = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le EVDD \le VDD \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

(1/2)

Parameter	Symbol	Condi	tions		peed main) ode	LS (low-sp Mo	,		v-power mode	LV (low- main)	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy2	4.0 V ≤ EV _{DD} ≤ 5.5 V	fmck > 20 MHz	8/fмск		_		_		_		ns
Note 3			fмcк ≤ 20 MHz	6/ƒмск		6/fмск		6/fмск		6/fмск		
		2.7 V ≤ EV _{DD} ≤ 5.5 V	fмск > 16 MHz	8/fмск		_		_		_	_	
			fмcк ≤ 16 MHz	6/fмск		6/fмск		6/fмск		6/fмск		
		2.4 V ≤ EV _{DD} ≤ 5.5 V		6/fмск and 500								
		1.8 V ≤ EV _{DD} ≤ 5.5 V		6/fмск and 750								
		1.7 V ≤ EV _{DD} ≤ 5.5V		6/fмск and 1500		6/fмск and 1500						
		1.6 V ≤ EV _{DD} ≤ 5.5 V		_								
SCKp high-/ low-level width	tkH2, tkL2	4.0 V ≤ EV _{DD} ≤ 5.5 V		tkcy2/2 -		tксу2/2 - 7		tксү2/2 - 7		tксу2/2 - 7		ns
		2.7 V ≤ EV _{DD} ≤ 5.5 V		tkcy2/2 -		tксу2/2 - 8		tkcy2/2 -		tксү2/2 - 8		
		1.8 V ≤ EV _{DD} ≤ 5.5 V		tксү2/2 - 18		tксу2/2 - 18		tксү2/2 - 18		tксү2/2 - 18		
		1.7 V ≤ EV _{DD} ≤ 5.5 V		tkcy2/2 - 66		tксү2/2 - 66		tксү2/2 - 66		tксү2/2 - 66		
		$1.6 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V}$		_								
SIp setup time (to SCKp†)	tsıĸ2	2.7 V ≤ EV _{DD} ≤ 5.5 V		1/fмск + 20		1/fмск + 30		1/fмcк + 30		1/fмск + 30		ns
Note 1		1.8 V ≤ EV _{DD} ≤ 5.5 V		1/fмcк + 30		1/fмск + 30		1/fмcк + 30		1/fмск + 30		
		1.7 V ≤ EV _{DD} ≤ 5.5 V		1/fмcк + 40		1/fмск + 40		1/fмск + 40		1/fмск + 40		
		1.6 V ≤ EV _{DD} ≤ 5.5 V		_								
SIp hold time (from SCKp↑)	tksi2	1.8 V ≤ EV _{DD} ≤ 5.5 V		1/fмск + 31		1/fмск + 31		1/fмcк + 31		1/fмск + 31		ns
Note 2		1.7 V ≤ EV _{DD} ≤ 5.5 V		1/fмcк + 250		1/fмск + 250		1/fмск + 250		1/fмск + 250		
		1.6 V ≤ EV _{DD} ≤ 5.5 V		_						1		

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **Note 3.** The maximum transfer rate when using the SNOOZE mode is 1 Mbps.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- Remark 1. p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)
- Remark 2. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 n: Channel number (mn = 00 to 03))



(TA = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(2/2)

Parameter	Symbol		Conditions		peed main) ode		peed main) ode		ower main) ode	,	ltage main) ode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Delay time from SCKp↓ to SOp output	tkso2	C = 30 pF Note 2	2.7 V ≤ EV _{DD} ≤ 5.5 V		2/fмск + 44		2/fмск + 110		2/fмск + 110		2/fмск + 110	ns
Note 1			2.4 V ≤ EV _{DD} ≤ 5.5 V		2/fмск + 75							
			1.8 V ≤ EV _{DD} ≤ 5.5 V		2/fмск + 110							
			1.7 V ≤ EV _{DD} ≤ 5.5 V		2/fмск + 220		2/fмск + 220		2/fмск + 220		2/fмск + 220	
			1.6 V ≤ EV _{DD} ≤ 5.5 V		_				1			
SSI00 setup time	tssik	DAPmn = 0	2.7 V ≤ V _{DD} ≤ 5.5 V	120		120		120		120		ns
			1.8 V ≤ V _{DD} < 2.7 V	200		200		200		200		
			1.7 V ≤ V _{DD} < 1.8 V	400		400		400		400		
			1.6 V ≤ V _{DD} < 1.7 V	_								
		DAPmn = 1	2.7 V ≤ V _{DD} ≤ 5.5 V	1/fмск + 120		1/fмск + 120		1/fмск + 120		1/fмск + 120		ns
			1.8 V ≤ V _{DD} < 2.7 V	1/fмск + 200		1/fмск + 200		1/fмcк + 200		1/fмcк + 200		
			1.7 V ≤ V _{DD} < 1.8 V	1/fмск + 400		1/fмск + 400		1/fмск + 400		1/fмcк + 400		
			1.6 V ≤ V _{DD} < 1.7 V	_								
SSI00 hold time	tkssi	DAPmn = 0	$2.7 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$	1/fмск + 120		1/fмск + 120		1/fмск + 120		1/fмск + 120		ns
			1.8 V ≤ V _{DD} < 2.7 V	1/fмск + 200		1/fмск + 200		1/fмск + 200		1/fмcк + 200		
			1.7 V ≤ V _{DD} < 1.8 V	1/fмск + 400		1/fмск + 400		1/fмск + 400		1/fмск + 400		
			1.6 V ≤ V _{DD} < 1.7 V	_								
		DAPmn = 1	2.7 V ≤ V _{DD} ≤ 5.5 V	120		120		120		120		ns
			1.8 V ≤ V _{DD} < 2.7 V	200		200		200		200		
			1.7 V ≤ V _{DD} < 1.8 V	400		400		400		400		
			1.6 V ≤ V _{DD} < 1.7 V	_		1		1		1		

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. C is the load capacitance of the SOp output lines.
- Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- Remark 1. p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)
- Remark 2. fmck: Serial array unit operation clock frequency

 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

 n: Channel number (mn = 00 to 03))

When P20 is used as SO10 pin

(TA = -40 to +85°C, 1.6 V \leq EVDD = VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Cond	ditions	HS (high-s Mo			peed main) ode		v-power mode		-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy2	$4.0~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$	fмск > 20 MHz	14/fмck		_		_		_		ns
Note 5			fмcк ≤ 20 MHz	12/fмск		12/fмск		12/fmck		12/fмск		
		2.7 V ≤ V _{DD} ≤ 5.5 V	fмск > 16 MHz	14/fмск and 850		_		_		_		
			fmck ≤ 16 MHz	12/fмск and 850		12/fмск		12/fмск		12/fмск		
		2.4 V ≤ V _{DD} ≤ 5.5 V		12/fмск and 1000		12/fмск		12/ƒмск		12/fмск		
		$1.8~V \leq V_{DD} \leq 5.5~V$		_		12/fмск		12/fмск		12/fмск		
		$1.7~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5\text{V}$		_		_		_		12/fмск		
		$1.6~V \leq V_{DD} \leq 5.5~V$		_		_		-				
SCKp high-/ low-level width	tкн2, tкL2	$4.0~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$		tксу2/2 - 7		tксу2/2 - 7		tkcy2/2 - 7		tксү2/2 - 7		ns
		$2.7~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$		tkcy2/2 -		tксү2/2 - 8		tксу2/2 - 8		tксү2/2 - 8		
		1.8 V ≤ V _{DD} ≤ 5.5 V		_		tксу2/2 - 18		tkcy2/2 - 18		tксу2/2 - 18		
		1.7 V ≤ V _{DD} ≤ 5.5 V		_		_		_		tксү2/2 -		
		1.6 V ≤ V _{DD} ≤ 5.5 V		_		_		_		66		
SIp setup time (to SCKp↑)	tsık2	2.7 V ≤ V _{DD} ≤ 5.5 V		1/fмcк + 20		1/fMCK + 30		1/fMCK + 30		1/fMCK + 30		ns
Note 1		2.4 V ≤ V _{DD} ≤ 5.5 V		1/fмcк + 30								
		1.8 V ≤ V _{DD} ≤ 5.5 V		_								
		1.7 V ≤ V _{DD} ≤ 5.5 V		_		_		_		1/fMCK		
		1.6 V ≤ V _{DD} ≤ 5.5 V		_		_		_		+ 40		
SIp hold time (from SCKp↑)	tksi2	$2.4~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$		1/fмск + 31		1/fмcк + 31		1/fмск + 31		1/fмcк + 31		ns
Note 2		1.8 V ≤ V _{DD} ≤ 5.5 V		_		1/fмск + 31		1/fмск + 31		1/fмск + 31		
		1.7 V ≤ V _{DD} ≤ 5.5 V		_		_		_		1/fмcк		
		1.6 V ≤ V _{DD} ≤ 5.5 V		_		_		_		+ 250		
Delay time from SCKp↓ to SOp	tkso2	C = 30 pF Note 4	2.7 V ≤ V _{DD} ≤ 5.5 V		2/fмск + 160		2/fMCK + 260		2/fMCK + 260		2/fмск + 260	ns
output Note 3			$2.4~\textrm{V} \leq \textrm{V}_\textrm{DD} \leq 5.5~\textrm{V}$		2/fмcк + 190							
			1.8 V ≤ V _{DD} ≤ 5.5 V		_	1						
			1.7 V ≤ V _{DD} ≤ 5.5 V		_		_		_		2/fmck	1
			1.6 V ≤ V _{DD} ≤ 5.5 V		_		_		_]	+ 320	

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. C is the load capacitance of the SOp output lines.
- Note 5. The maximum transfer rate when using the SNOOZE mode is 1 Mbps.
- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark 1. p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM



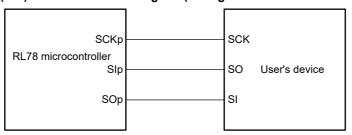
numbers (g = 0, 4 and 12)

Remark 2. fmck: Serial array unit operation clock frequency

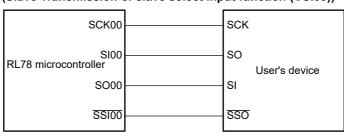
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03))

Simplified SPI (CSI) mode connection diagram (during communication at same potential)

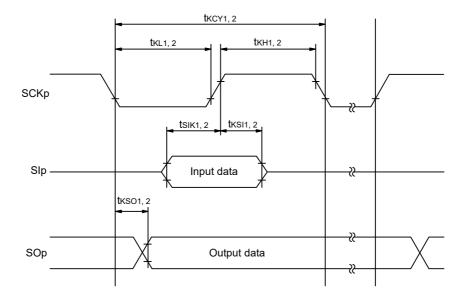


Simplified SPI (CSI) mode connection diagram (during communication at same potential) (Slave Transmission of slave select input function (CSI00))

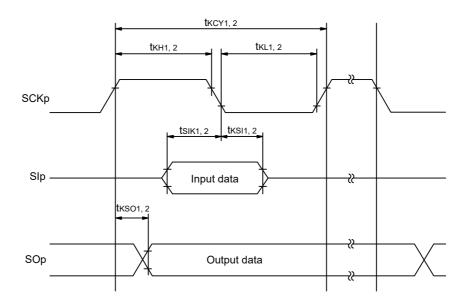


Remark p: CSI number (p = 00, 01, 10 and 11)

Simplified SPI (CSI) mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark 1. p: CSI number (p = 00, 01, 10 and 11)

Remark 2. m: Unit number, n: Channel number (mn = 00 to 03)

(5) During communication at same potential (simplified I²C mode)

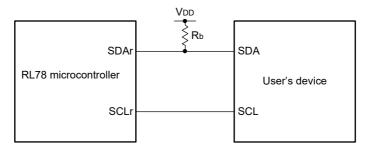
(TA = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions		peed main) ode		peed main) ode	-	w-power mode	1	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	fscL	$2.7~V \leq EV_{DD} \leq 5.5~V,$ $C_b = 50~pF,~R_b = 2.7~k\Omega$		1000 Note 1		400 Note 1		250 Note 1		400 Note 1	kHz
		$1.8~V \le EV_{DD} \le 5.5~V,$ $C_b = 100~pF,~R_b = 3~k\Omega$		400 Note 1							
		1.8 V ≤ EV _{DD} < 2.7 V,		300		300		250		300	
		C_b = 100 pF, R_b = 5 k Ω		Note 1		Note 1		Note 1		Note 1	
		1.7 V \leq EV _{DD} $<$ 1.8 V, C _b = 100 pF, R _b = 5 kΩ		250 Note 1		250 Note 1		250 Note 1		250 Note 1	
		$1.6~V \leq EV_{DD} < 1.8~V,$ $C_b = 100~pF,~R_b = 5~k\Omega$		_				-			
Hold time when SCLr = "L"	tLOW	$2.7~V \leq EV_{DD} \leq 5.5~V,$ $C_b = 50~pF,~R_b = 2.7~k\Omega$	475		1150		1150		1150		ns
		$1.8~V \le EV_{DD} \le 5.5~V,$ $C_b = 100~pF,~R_b = 3~k\Omega$	1150								
		1.8 V \leq EV _{DD} $<$ 2.7 V, C _b = 100 pF, R _b = 5 kΩ	1550		1550		1550		1550		
		$1.7~V \leq EV_{DD} < 1.8~V,$ $C_b = 100~pF,~R_b = 5~k\Omega$	1850		1850		1850		1850		
		$1.6~V \leq EV_{DD} < 1.8~V,$ $C_b = 100~pF,~R_b = 5~k\Omega$									
Hold time when SCLr = "H"	tнідн	$2.7~V \leq \text{EV}_{\text{DD}} \leq 5.5~V,$ $C_{\text{b}} = 50~\text{pF},~R_{\text{b}} = 2.7~\text{k}\Omega$	475		1150		1150		1150		ns
		$1.8~V \leq EV_{DD} \leq 5.5~V,$ $C_b = 100~pF,~R_b = 3~k\Omega$	1150								
		$1.8~V \leq EV_{DD} < 2.7~V,$ $C_b = 100~pF,~R_b = 5~k\Omega$	1550		1550		1550		1550		
		$1.7~V \leq EV_{DD} < 1.8~V,$ $C_b = 100~pF,~R_b = 5~k\Omega$	1850		1850		1850		1850		
		$1.6~V \leq EV_{DD} < 1.8~V,$ $C_b = 100~pF,~R_b = 5~k\Omega$	_								
Data setup time	tsu: dat	$2.7 \text{ V} \le \text{EV}_{\text{DD}} \le 5.5 \text{ V},$	1/fмск		1/fмск		1/fмск		1/fмск		ns
(reception)		$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	+ 85 Note 2		+ 145 Note 2		+ 145 Note 2		+ 145 Note 2		
		$1.8~V \leq EV_{DD} \leq 5.5~V,$ $C_b = 100~pF,~R_b = 3~k\Omega$	1/fмск + 145 Note 2								
		1.8 V ≤ EV _{DD} < 2.7 V,	1/fмск		1/fмск		1/fмск		1/fмск		
		C_b = 100 pF, R_b = 5 k Ω	+ 230 Note 2		+ 230 Note 2		+ 230 Note 2		+ 230 Note 2		
		$1.7~V \leq EV_{DD} < 1.8~V,$ $C_b = 100~pF,~R_b = 5~k\Omega$	1/fмск + 290 Note 2		1/fмск + 290 Note 2		1/fмск + 290 Note 2		1/fмск + 290 Note 2		
		1.6 V \leq EV _{DD} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	_								
Data hold time (transmission)	thd: dat	$2.7~V \leq \text{EV}_{\text{DD}} \leq 5.5~V,$ $C_b = 50~\text{pF},~R_b = 2.7~\text{k}\Omega$	0	305	0	305	0	305	0	305	ns
		1.8 V \leq EV _{DD} \leq 5.5 V, C _b = 100 pF, R _b = 3 kΩ		355		355		355		355	
		1.8 V \leq EV _{DD} $<$ 2.7 V, C _b = 100 pF, R _b = 5 kΩ		405		405		405		405	
		1.7 V \leq EV _{DD} $<$ 1.8 V, C _b = 100 pF, R _b = 5 kΩ									
		1.6 V \leq EV _{DD} $<$ 1.8 V, C _b = 100 pF, R _b = 5 kΩ	_	_	1						

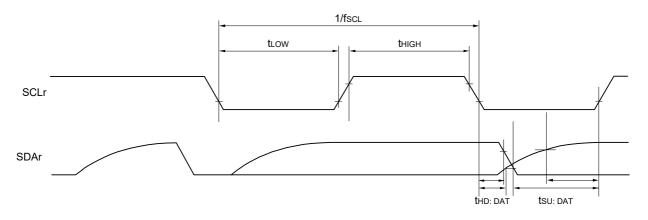
- **Note 1.** The value must be equal to or less than fMCK/4.
- Note 2. Set the fмcκ value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the normal input buffer and the N-ch open drain output (EVDD tolerance) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

Simplified I²C mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



- **Remark 1.** Rb[Ω]: Communication line (SDAr) pull-up resistance, Cb[F]: Communication line (SDAr, SCLr) load capacitance r: IIC number (r = 00, 01, 10 and 11), g: PIM number (g = 0, 3 and 5), h: POM number (h = 0, 3 and 5)
- Remark 2. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0),
 n: Channel number (n = 0 to 3), mn = 00 to 03)

(6) Communication at different potential (1.8 V, 2.5 V, 3.0 V) (UART mode) (dedicated baud rate generator output)

(TA = -40 to +85°C, 1.8 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(1/2)

Parameter	Symbol		Conditions	,	gh-speed) Mode	,	w-speed) Mode	,	w-power) mode	,	ow-voltage in) Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		reception	$4.0 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{b} \le 4.0 \text{ V}$		fмск/6 Note 1		fMCK/6 Note 1		fMCK/6 Note 1		fMCK/6 Note 1	bps
			Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		4.0		1.3		0.1		0.6	Mbps
			2.7 V ≤ EV _{DD} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V		fмск/6 Note 1		fMCK/6 Note 1		fMCK/6 Note 1		fмск/6 Note 1	bps
			Theoretical value of the maximum transfer rate fmck = fclk Note 3		4.0		1.3		0.1		0.6	Mbps
			$1.8 \text{ V} \le \text{EV}_{DD} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{b} \le 2.0 \text{ V}$		fMCK/6 Notes 1, 2,		fMCK/6 Notes 1, 2		fMCK/6 Notes 1, 2		fMCK/6 Notes 1, 2	bps
			Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		4.0		1.3		0.1		0.6	Mbps

- Note 1. Transfer rate in the SNOOZE mode is 4,800 bps only.
- Note 2. Use it with $EVDD \ge Vb$.
- Note 3. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: 24 MHz (2.7 V \leq VDD \leq 5.5 V)

16 MHz (2.4 V \leq VDD \leq 5.5 V)

LS (low-speed main) mode: 8 MHz (1.8 V \leq VDD \leq 5.5 V) LP (low-power main) mode: 1 MHz (1.8 V \leq VDD \leq 5.5 V) LV (low-voltage main) mode: 4 MHz (1.6 V \leq VDD \leq 5.5 V)

Note 4. The following conditions are required for low voltage interface when EVDD < VDD

2.4 V ≤ EVDD < 2.7 V: MAX. 2.6 Mbps 1.8 V ≤ EVDD < 2.4 V: MAX. 1.3 Mbps

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (EVDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

- Remark 1. Vb[V]: Communication line voltage
- Remark 2. q: UART number (q = 0 and 1), g: PIM and POM number (g = 0, 2, 3, 5 and 12)
- Remark 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03))

$(TA = -40 \text{ to } +85^{\circ}C, 1.8 \text{ V} \le EVDD \le VDD \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

(2/2)

Parameter	Symbol		Conditions	,	gh-speed) Mode	,	w-speed) Mode	,	w-power) mode	,	v-voltage) Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		Transmission	$4.0 \text{ V} \le \text{EVDD} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{Vb} \le 4.0 \text{ V}$		Note 1		Note 1		Note 1		Note 1	bps
			Theoretical value of the maximum transfer rate $C_b = 50$ pF, $R_b = 1.4$ k Ω , $V_b = 2.7$ V		2.8 Note 2		2.8 Note 2		2.8 Note 2		2.8 Note 2	Mbps
			$2.7 \text{ V} \le \text{EV}_{DD} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V}$		Note 3		Note 3		Note 3		Note 3	bps
			Theoretical value of the maximum transfer rate $C_b = 50$ pF, $R_b = 2.7$ k Ω , $V_b = 2.3$ V		1.2 Note 4		1.2 Note 4		1.2 Note 4		1.2 Note 4	Mbps
			1.8 V \leq EV _{DD} $<$ 3.3 V, 1.6 V \leq V _b \leq 2.0 V		Notes 5, 6		Notes 5, 6		Notes 5, 6		Notes 5, 6	bps
			Theoretical value of the maximum transfer rate $C_b = 50$ pF, $R_b = 5.5$ k Ω , $V_b = 1.6$ V		0.43 Note 7		0.43 Note 7		0.43 Note 7		0.43 Note 7	Mbps

Note 1. The smaller maximum transfer rate derived by using fMck/6 or the following expression is the valid maximum transfer rate. Expression for calculating the transfer rate when $4.0 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V}$ and $2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V}$

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln \left(1 - \frac{2.2}{V_b}\right)\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}}$$

- **Note 2.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.
- Note 3. The smaller maximum transfer rate derived by using fMcK/6 or the following expression is the valid maximum transfer rate. Expression for calculating the transfer rate when $2.7 \text{ V} \le \text{EV}_{DD} \le 4.0 \text{ V}$ and $2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V}$

$$\begin{aligned} \text{Maximum transfer rate} &= \frac{}{\left\{ -\text{Cb} \times \text{Rb} \times \text{ln} \left(1 - \frac{2.0}{V_b} \right) \right\} \times 3} \\ &= \frac{1}{\text{Transfer rate} \times 2} - \left\{ -\text{Cb} \times \text{Rb} \times \text{ln} \left(1 - \frac{2.0}{V_b} \right) \right\} \\ &= \frac{1}{\text{Transfer rate} \times 2} \times 100 \, [\%] \end{aligned}$$
 Baud rate error (theoretical value) =
$$\frac{1}{\left(\frac{1}{\text{Transfer rate}} \right) \times \text{Number of transferred bits} }$$

Note 4. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.

Note 5. Use it with $EVDD \ge Vb$.



^{*} This value is the theoretical value of the relative difference between the transmission and reception sides

^{*} This value is the theoretical value of the relative difference between the transmission and reception sides

Note 6. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate. Expression for calculating the transfer rate when 1.8 V \leq EVDD < 3.3 V and 1.6 V \leq Vb \leq 2.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln \left(1 - \frac{1.5}{V_b}\right)\} \times 3}$$
 [bps]

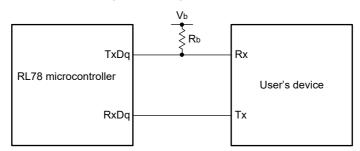
Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-\text{Cb} \times \text{Rb} \times \text{In } (1 - \frac{1.5}{\text{Vb}})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}}$$

- **Note 7.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 6 above to calculate the maximum transfer rate under conditions of the customer.
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (EVDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

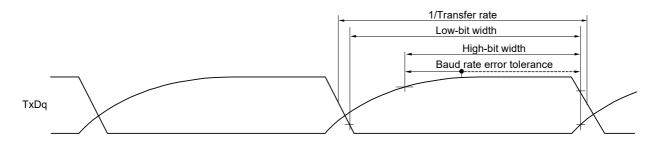


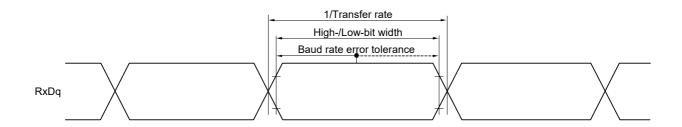
^{*} This value is the theoretical value of the relative difference between the transmission and reception sides

UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)





- **Remark 1.** Rb[Ω]: Communication line (TxDq) pull-up resistance, Cb[F]: Communication line (TxDq) load capacitance, Vb[V]: Communication line voltage
- Remark 2. q: UART number (q = 0 and 1), g: PIM and POM number (g = 0, 2, 3, 5 and 12)
- Remark 3. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03))

(7) Communication at different potential (1.8 V, 2.5 V, 3.0 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

(TA = -40 to +85°C, 2.7 V \leq EVDD \leq VDD \leq 5.5 V, VSS = 0 V)

(1/2)

Parameter	Sym bol		Conditions	, ,	h-speed Mode	LS (low main)	/-speed Mode		v-power mode	LV (low- main)	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 2/fclk	$\begin{split} 4.0 \ V &\leq EV_{DD} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 20 \ pF, \ R_b = 1.4 \ k\Omega \end{split}$			1150		1150		1150		ns
		tkcy1 ≥ 2/fcLk	$\label{eq:substitute} \begin{split} 2.7 \ V &\leq E V_{DD} < 4.0 \ V, \\ 2.3 \ V &\leq V_{b} \leq 2.7 \ V, \\ C_{b} &= 20 \ pF, \ R_{b} = 2.7 \ k\Omega \end{split}$	300								ns
SCKp high-level width	t кн1	$4.0 \text{ V} \leq \text{EV}_{DD} \leq 2.7 \text{ V} \leq \text{V}_{b} \leq 4.0 \text{ C}_{b} = 20 \text{ pF, Rb}$	0 V,	tkcy1/2 - 50		tксү1/2 - 50		tксү1/2 - 50		tксү1/2 - 50		ns
		$2.7 \text{ V} \le \text{EV}_{DD} \le 2.3 \text{ V} \le \text{V}_{b} \le 2.$ C _b = 20 pF, R _b	7 V,	tксү1/2 - 120		tксу1/2 - 120		tксу1/2 - 120		tксу1/2 - 120		ns
SCKp low-level width	tKL1	$4.0 \text{ V} \le \text{EV}_{DD} \le$ $2.7 \text{ V} \le \text{V}_b \le 4.$ $C_b = 20 \text{ pF, Rb}$ $2.7 \text{ V} \le \text{EV}_{DD} \le$	0 V, = 1.4 kΩ	tксү1/2 - 7 tксү1/2		tксу1/2 - 50		tксү1/2 - 50		tксү1/2 - 50		ns
		$2.3 \text{ V} \le \text{Vb} \le 2.$ Cb = 20 pF, Rb	,	- 10								
SIp setup time (to SCKp↑) Note 1	tsik1	$4.0 \text{ V} \leq \text{EV}_{DD} \leq$ $2.7 \text{ V} \leq \text{V}_{b} \leq 4.0 \text{ C}_{b} = 20 \text{ pF, Rb}$	0 V,	58		479		479		479		ns
		$ 2.7 \text{ V} \leq \text{EV}_{DD} \leq \\ 2.3 \text{ V} \leq \text{V}_{b} \leq 2. \\ C_{b} = 20 \text{ pF, Rb} $	7 V,	121								
SIp hold time (from SCKp↑) Note 1	tksii	$4.0 \text{ V} \leq \text{EV}_{DD} \leq$ $2.7 \text{ V} \leq \text{V}_{b} \leq 4.0$ $C_{b} = 20 \text{ pF, Rb}$	0 V,	10		10		10		10		ns
		$2.7 \text{ V} \leq \text{EV}_{DD} \leq$ $2.3 \text{ V} \leq \text{V}_{b} \leq 2.$ $C_{b} = 20 \text{ pF, Rb}$	7 V,									
Delay time from SCKp↓ to SOp output ^{Note 1}	tkso1	$4.0 \text{ V} \leq \text{EV}_{DD} \leq$ $2.7 \text{ V} \leq \text{V}_{b} \leq 4.0$ $C_{b} = 20 \text{ pF, Rb}$	0 V,		60		60		60		60	ns
		$2.7 \text{ V} \leq \text{EV}_{DD} \leq$ $2.3 \text{ V} \leq \text{V}_{b} \leq 2.$ $C_{b} = 20 \text{ pF, Rb}$	7 V,		130		130		130		130	
SIp setup time (to SCKp↓) Note 2	tsıĸ1	$4.0 \text{ V} \leq \text{EV}_{DD} \leq$ $2.7 \text{ V} \leq \text{V}_{b} \leq 4.0$ $C_{b} = 20 \text{ pF, Rb}$	0 V,	23		110		110		110		ns
		$2.7 \text{ V} \leq \text{EV}_{DD} \leq 2.3 \text{ V} \leq \text{V}_{b} \leq 2.3 \text{ C}_{b} = 20 \text{ pF, Rb}$	7 V,	33								
SIp hold time (from SCKp↓) Note 2	tksii	4.0 V ≤ EVDD ≤ 2.7 V ≤ Vb ≤ 4.1 Cb = 20 pF, Rb	0 V, = 1.4 kΩ	10		10		10		10		ns
		$2.7 \text{ V} \leq \text{EV}_{DD} < 2.3 \text{ V} \leq \text{V}_{b} \leq 2.$ $C_{b} = 20 \text{ pF}, \text{ Rb}$	7 V,									

$(TA = -40 \text{ to } +85^{\circ}C, 2.7 \text{ V} \le EVDD \le VDD \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

(2/2)

Parameter	Sym bol	Conditions		h-speed Mode	,	/-speed Mode	,	v-power mode	,	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Delay time from SCKp↑ to SOp output Note 2	tkso1	$ 4.0 \text{ V} \leq \text{EVdd} \leq 5.5 \text{ V}, \\ 2.7 \text{ V} \leq \text{V}_b \leq 4.0 \text{ V}, \\ \text{C}_b = 20 \text{ pF}, \text{R}_b = 1.4 \text{ k}\Omega $		10		10		10		10	ns
		$2.7 \text{ V} \leq \text{EV}_{DD} < 4.0 \text{ V},$ $2.3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V},$ $C_{b} = 20 \text{ pF}, R_{b} = 2.7 \text{ k}\Omega$									

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.
- Note 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (EVDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.
- Remark 1. $R_b[\Omega]$: Communication line (SCKp, SOp) pull-up resistance, $C_b[F]$: Communication line (SCKp, SOp) load capacitance, $V_b[V]$: Communication line voltage
- Remark 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM number (g = 5)
- Remark 3. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 n: Channel number (mn = 00))

(8) Communication at different potential (1.8 V, 2.5 V, 3.0 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

(TA = -40 to +85°C, 1.8 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(1/2)

Parameter	Sym		Conditions		h-speed Mode	LS (low main)	/-speed Mode	,	v-power mode	LV (low- main)	•	Unit
	DOI			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$ \begin{array}{lll} \text{4.1 } \geq 4/\text{fclk} & 4.0 \text{ V} \leq \text{EVdd} \leq 5.5 \text{ V}, \\ 2.7 \text{ V} \leq \text{V}_b \leq 4.0 \text{ V}, \\ \text{C}_b = 30 \text{ pF}, \text{R}_b = 1.4 \text{ k}\Omega \\ \end{array} $			1150		1150		1150		ns
			$\begin{aligned} 2.7 \ V &\leq EV_{DD} < 4.0 \ V, \\ 2.3 \ V &\leq V_{b} \leq 2.7 \ V, \\ C_{b} &= 30 \ pF, \ R_{b} = 2.7 \ k\Omega \end{aligned}$			-						ns
			$\begin{split} &1.8 \; \text{V} \leq \text{EV}_{\text{DD}} < 3.3 \; \text{V}, \\ &1.6 \; \text{V} \leq \text{V}_{b} \leq 2.0 \; \text{V} \; \text{Note}, \\ &\text{C}_{b} = 30 \; \text{pF}, \; \text{R}_{b} = 5.5 \; \text{k}\Omega \end{split}$	1150								ns
SCKp high- level width	tĸн1	4.0 V ≤ EV _{DD} ≤ C _b = 30 pF, R _b	$5.5 \text{ V}, 2.7 \text{ V} \le \text{Vb} \le 4.0 \text{ V},$ = 1.4 kΩ	tксү1/2 - 75		tkcy1/2 - 75		tксү1/2 - 75		tксү1/2 - 75		ns
		2.7 V ≤ EV _{DD} < C _b = 30 pF, R _b	$< 4.0 \text{ V}, 2.3 \text{ V} \le \text{Vb} \le 2.7 \text{ V},$ = 2.7 kΩ	tксү1/2 - 170		tксү1/2 - 170		tксү1/2 - 170		tксү1/2 - 170		ns
		1.8 V ≤ EV _{DD} < Note, C _b = 30 pF, R _b		tkcy1/2 - 458		tксү1/2 - 458		tксү1/2 - 458		tксү1/2 - 458		ns
SCKp low-level width	t _{KL1}	4.0 V ≤ EV _{DD} ≤ C _b = 30 pF, R _b	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{Vb} \leq 4.0 \text{ V},$ = 1.4 kΩ	tксү1/2 - 12		tkcy1/2 - 50		tксү1/2 - 50		tксү1/2 - 50		ns
			$V \le EV_{DD} < 4.0 \text{ V}, 2.3 \text{ V} \le V_b \le 2.7 \text{ V},$ = 30 pF, $R_b = 2.7 \text{ k}Ω$									
		Note,	$3~V \le EV_{DD} < 3.3~V, \ 1.6~V \le V_b \le 2.0~V$ te, $_0 = 30~pF, \ R_b = 5.5~k\Omega$									ns

Note Use it with $EVDD \ge Vb$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (EVDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)

(8) Communication at different potential (1.8 V, 2.5 V, 3.0 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

(TA = -40 to +85°C, 1.8 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(2/2)

Parameter	Sym	Conditions	, ,	h-speed Mode	,	v-speed Mode	,	v-power mode	,	-voltage Mode	Unit
	boi		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Slp setup time	tsıĸ1	$ 4.0 \text{ V} \leq \text{EV}_{DD} \leq 5.5 \text{ V}, \ 2.7 \text{ V} \leq \text{V}_b \leq 4.0 \text{ V}, $ $C_b = 30 \text{ pF}, \ R_b = 1.4 \text{ k}\Omega $	81		479		479		479		ns
(to SCKp↑) Note 1		$ 2.7 \text{ V} \leq \text{EV}_{DD} < 4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_b \leq 2.7 \text{ V}, \\ C_b = 30 \text{ pF}, \ R_b = 2.7 \text{ k}\Omega $	177								
			479								
SIp hold time (from SCKp↑)	tksi1	$ 4.0 \text{ V} \leq \text{EV}_{DD} \leq 5.5 \text{ V}, \ 2.7 \text{ V} \leq \text{V}_b \leq 4.0 \text{ V}, $ $C_b = 30 \text{ pF}, \ R_b = 1.4 \text{ k}\Omega $	19		19		19		19		ns
Note 1		$ 2.7 \text{ V} \leq \text{EV}_{DD} < 4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_b \leq 2.7 \text{ V}, \\ C_b = 30 \text{ pF}, \ R_b = 2.7 \text{ k}\Omega $									
		$\begin{array}{c} 1.8 \text{ V} \leq \text{EV}_{\text{DD}} \leq 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V} \ \text{Note 3}, \\ C_{\text{b}} = 30 \text{ pF}, \ R_{\text{b}} = 5.5 \text{ k}\Omega \end{array}$									
Delay time from SCKp↓	tkso1	$ 4.0 \text{ V} \leq \text{EV}_{DD} \leq 5.5 \text{ V}, \ 2.7 \text{ V} \leq \text{V}_b \leq 4.0 \text{ V}, $ $C_b = 30 \text{ pF}, \ R_b = 1.4 \text{ k}\Omega $		100		100		100		100	ns
to SOp output Note 1		$ 2.7 \text{ V} \leq \text{EV}_{DD} < 4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_b \leq 2.7 \text{ V}, \\ C_b = 30 \text{ pF}, \ R_b = 2.7 \text{ k}\Omega $		195		195		195		195	ns
		$\begin{array}{l} 1.8 \; \text{V} \leq \text{EV}_{\text{DD}} \leq 3.3 \; \text{V}, 1.6 \; \text{V} \leq \text{V}_{\text{b}} \leq 2.0 \; \text{V} \; ^{\text{Note } 3}, \\ \text{C}_{\text{b}} = 30 \; \text{pF}, \; \text{R}_{\text{b}} = 5.5 \; \text{k} \Omega \end{array}$		483		483		483		483	ns
SIp setup time	tsık1	$ 4.0 \text{ V} \leq \text{EV}_{DD} \leq 5.5 \text{ V}, \ 2.7 \text{ V} \leq \text{V}_b \leq 4.0 \text{ V}, $ $C_b = 30 \text{ pF}, \ R_b = 1.4 \text{ k}\Omega $	44		110		110		110		ns
(to SCKp↓) Note 2		$ 2.7 \text{ V} \leq \text{EV}_{DD} < 4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_b \leq 2.7 \text{ V}, $ $ C_b = 30 \text{ pF}, \ R_b = 2.7 \text{ k} \Omega $									
			110								
SIp hold time (from SCKp↓)	tksi1	$ 4.0 \text{ V} \leq \text{EV}_{DD} \leq 5.5 \text{ V}, \ 2.7 \text{ V} \leq \text{V}_b \leq 4.0 \text{ V}, $ $C_b = 30 \text{ pF}, \ R_b = 1.4 \text{ k}\Omega $	19		19		19		19		ns
Note 2		$ 2.7 \text{ V} \leq \text{EV}_{DD} < 4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_b \leq 2.7 \text{ V}, \\ C_b = 30 \text{ pF}, \ R_b = 2.7 \text{ k}\Omega $									
		$\begin{array}{c} 1.8 \text{ V} \leq \text{EV}_{DD} \leq 3.3 \text{ V}, 1.6 \text{ V} \leq \text{V}_{b} \leq 2.0 \text{ V} \text{ Note } 3, \\ C_{b} = 30 \text{ pF}, \text{ R}_{b} = 5.5 \text{ k}\Omega \end{array}$									
Delay time from SCKp↑	tkso1	$4.0~V \leq EV_{DD} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ $C_b = 30~pF,~R_b = 1.4~k\Omega$		25		25		25		25	ns
to SOp output Note 2		$2.7 \text{ V} \leq \text{EV}_{DD} < 4.0 \text{ V}, 2.3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V},$ $C_{b} = 30 \text{ pF}, R_{b} = 2.7 \text{ k}\Omega$									
		$\begin{array}{c} 1.8 \; \text{V} \leq \text{EV}_{\text{DD}} \leq 3.3 \; \text{V}, 1.6 \; \text{V} \leq \text{V}_{\text{b}} \leq 2.0 \; \text{V} \; \text{Note 3}, \\ C_{\text{b}} = 30 \; \text{pF}, \; R_{\text{b}} = 5.5 \; \text{k}\Omega \end{array}$									

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (EVDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

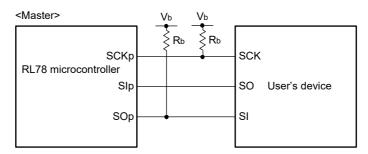
(Remarks are listed on the next page.)



Note 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

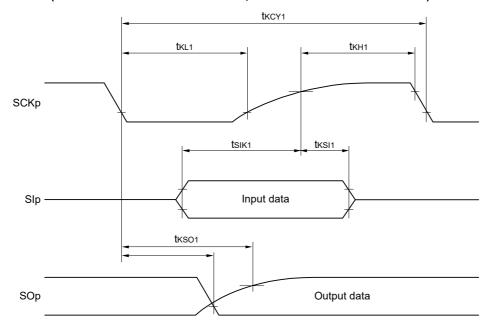
Note 3. Use it with $EVDD \ge Vb$.

Simplified SPI (CSI) mode connection diagram (during communication at different potential)

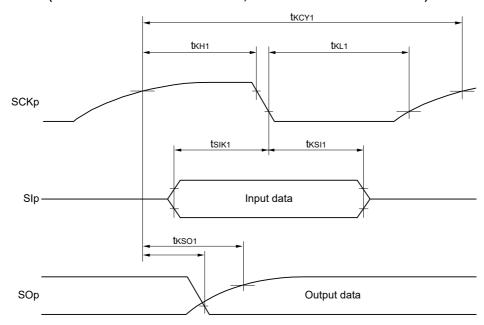


- Remark 1. $Rb[\Omega]$: Communication line (SCKp, SOp) pull-up resistance, Cb[F]: Communication line (SCKp, SOp) load capacitance, Vb[V]: Communication line voltage
- Remark 2. p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)
- Remark 3. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 n: Channel number (mn = 00 to 03))

Simplified SPI (CSI) mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)

(9) Communication at different potential (1.8 V, 2.5 V, 3.0 V) (Simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)

(TA = -40 to 85°C, 1.8 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

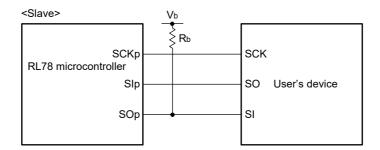
Parameter	Symb	C	conditions	, ,	h-speed Mode		/-speed Mode	,	v-power mode	,	-voltage Mode	Unit
	Oi			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	•
SCKp cycle	tkcy2	$4.0 \text{ V} \leq \text{EV}_{DD} \leq 5.5 \text{ V},$	20 MHz < f _{MCK} ≤ 24 MHz	12/fмск		_		_		_		ns
time Note 1		$2.7~V \leq Vb \leq 4.0~V$	8 MHz < fмcк ≤ 20 MHz	10/fмск		-		_		_		ns
			4 MHz < f _{MCK} ≤ 8 MHz	8/fмск		16/fмск		_		_		ns
			fMCK ≤ 4 MHz	6/fмск		10/fмск		10/fмск		10/fмск		ns
		2.7 V ≤ EV _{DD} < 4.0 V,	20 MHz < f _{MCK} ≤ 24 MHz	16/fмск		-		_		_		ns
		$2.3 \text{ V} \le \text{Vb} \le 2.7 \text{ V}$	16 MHz < fмcк ≤ 20 MHz	14/fмск		_		_		_		ns
			8 MHz < fмcк ≤ 16 MHz	12/fмск		_		_		_		ns
			4 MHz < f _{MCK} ≤ 8 MHz	8/fмск		16/fмск		_		_		ns
			fMCK ≤ 4 MHz	6/fмск		10/fмск		10/fмск		10/fмск		ns
		1.8 V ≤ EV _{DD} < 2.7 V,	20 MHz < f _{MCK} ≤ 24 MHz	36/fмск		_		_		_		ns
		1.6 V ≤ Vb ≤ 2.0 V Note 2	16 MHz < fмcк ≤ 20 MHz	32/fмск		_		_		_		ns
		Note 2	8 MHz < fмcк ≤ 16 MHz	26/fмск		_		_		_		ns
			4 MHz < f _{MCK} ≤ 8 MHz	16/fмск		16/fмск		_		_		ns
			fmck ≤ 4 MHz	10/fмск		10/fмск		10/fмск		10/fмск		ns
SCKp high-/ low-level	tkH2, tkL2	4.0 V ≤ EV _{DD} ≤ 5.5 V, 2.7	7 V ≤ Vb ≤ 4.0 V	tксу2/2 - 12		tксү2/2 - 50		tксү2/2 - 50		tксү2/2 - 50		ns
width		$2.7 \text{ V} \le \text{EV}_{DD} < 4.0 \text{ V}, 2.3$	3 V ≤ Vb ≤ 2.7 V	tксу2/2 - 18		tксу2/2 - 50		tксу2/2 - 50		tксү2/2 - 50		ns
		1.8 V ≤ EV _{DD} < 3.3 V, 1.6	6 V ≤ Vb ≤ 2.0 V Note 2	tксу2/2 - 50		tксү2/2 - 50		tксү2/2 - 50		tксү2/2 - 50		ns
SIp setup time (to	tsıĸ2	4.0 V ≤ EV _{DD} ≤ 5.5 V, 2.7	$7 \text{ V} \le \text{Vb} \le 4.0 \text{ V}$	1/fмск + 20		1/fмск + 30		1/fмск + 30		1/fмск + 30		ns
SCKp↑) Note 3		2.7 V ≤ EV _{DD} < 4.0 V, 2.3	3 V ≤ Vb ≤ 2.7 V	1/fмск + 20		1/fмск + 30		1/fмcк + 30		1/fmck + 30		ns
		1.8 V ≤ EV _{DD} < 3.3 V, 1.6	3 V ≤ Vb ≤ 2.0 V Note 2	1/fмск + 30		1/fмск + 30		1/fмcк + 30		1/fmck + 30		ns
SIp hold time (from SCKp†) Note 3	tksı2			1/fмск + 31		1/fмск + 31		1/fмск + 31		1/fмск + 31		ns
Delay time from SCKp↓	tkso2	$4.0 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V}, 2.7$ $C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$	$7 \text{ V} \le \text{Vb} \le 4.0 \text{ V},$		2/fмск + 120		2/fмск + 573		2/fмск + 573		2/fмск + 573	ns
to SOp output Note 4		$2.7 \text{ V} \le \text{EV}_{DD} < 4.0 \text{ V}, 2.3 $ $C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	$3 \text{ V} \le \text{Vb} \le 2.7 \text{ V},$		2/fмск + 214		2/fмск + 573		2/fмск + 573		2/fмск + 573	ns
		$1.8 \text{ V} \leq \text{EV}_{DD} < 3.3 \text{ V}, \ 1.6 \\ C_b = 30 \text{ pF}, \ R_b = 5.5 \text{ k}\Omega$	$6 \text{ V} \le \text{Vb} \le 2.0 \text{ V} \text{ Note 2},$		2/fмск + 573		2/fмск + 573		2/fмск + 573		2/fмск + 573	ns

(Notes, Caution and Remarks are listed on the next page.)

- Note 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
- Note 2. Use it with $EVDD \ge V_b$.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" and the SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

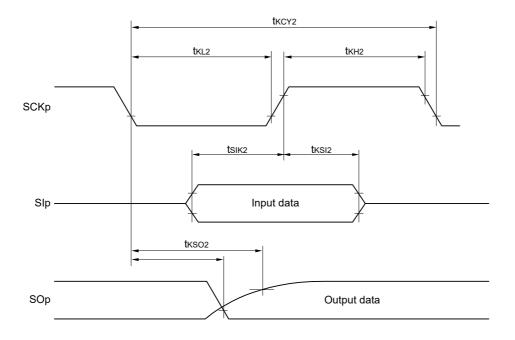
Caution Select the TTL input buffer for the SIp pin and SCKp pin and the N-ch open drain output (EVDD tolerance) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

Simplified SPI (CSI) mode connection diagram (during communication at different potential)

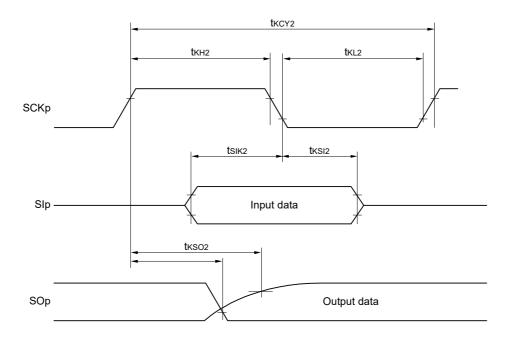


- **Remark 1.** Rb[Ω]: Communication line (SOp) pull-up resistance, Cb[F]: Communication line (SOp) load capacitance, Vb[V]: Communication line voltage
- Remark 2. p: CSI number (p = 00 to 03), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)
- Remark 3. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03))

Simplified SPI (CSI) mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)

(10) Communication at different potential (1.8 V, 2.5 V, 3.0 V) (simplified I²C mode)

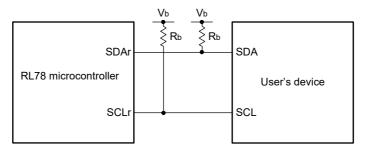
(TA = -40 to 85°C, 1.8 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Sym	Conditions		h-speed Mode	,	/-speed Mode	LP (Lov main)	•	,	-voltage Mode	Unit
	DOI		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	fscL	$ 4.0 \text{ V} \leq \text{EV}_{DD} \leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_b \leq 4.0 \text{ V}, $ $C_b = 50 \text{ pF}, \ R_b = 2.7 \text{ k}\Omega $		1000 Note 1		300 Note 1		250 Note 1		300 Note 1	kHz
		$ 2.7 \text{ V} \leq \text{EV}_{DD} < 4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_b \leq 2.7 \text{ V}, \\ C_b = 50 \text{ pF}, \ R_b = 2.7 \text{ k}\Omega $		1000 Note 1		300 Note 1		250 Note 1		300 Note 1	kHz
		$4.0~V \leq EV_{DD} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ $C_b = 100~pF,~R_b = 2.8~k\Omega$		400 Note 1		300 Note 1		250 Note 1		300 Note 1	kHz
		$2.7 \text{ V} \le \text{EV}_{DD} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V},$ $C_{b} = 100 \text{ pF}, R_{b} = 2.7 \text{ k}\Omega$		400 Note 1		300 Note 1		250 Note 1		300 Note 1	kHz
		$1.8 \text{ V} \leq \text{EV}_{DD} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_b \leq 2.0 \text{ V} \text{ Note 2}, \\ C_b = 100 \text{ pF}, R_b = 5.5 \text{ k}\Omega$		300 Note 1		300 Note 1		250 Note 1		300 Note 1	kHz
Hold time when SCLr	tLow	$4.0 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{b} \le 4.0 \text{ V},$ $C_{b} = 50 \text{ pF}, R_{b} = 2.7 \text{ k}\Omega$	475		1550		1550		1550		ns
= "L"		$2.7 \text{ V} \le \text{EV}_{DD} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V},$ $C_{b} = 50 \text{ pF}, R_{b} = 2.7 \text{ k}\Omega$	475		1550		1550		1550		ns
		$4.0~V \leq EV_{DD} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ $C_b = 100~pF,~R_b = 2.8~k\Omega$	1150		1550		1550		1550		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD}} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	1150		1550		1550		1550		ns
		$\begin{array}{c} 1.8 \text{ V} \leq \text{EV}_{\text{DD}} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V} \ \text{Note 2}, \\ C_{\text{b}} = 100 \text{ pF}, \ R_{\text{b}} = 5.5 \text{ k}\Omega \end{array}$	1550		1550		1550		1550		ns
Hold time when SCLr	tніgн	$ 4.0 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, $ $ C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega $	245		610		610		610		ns
= "H"		$2.7 \text{ V} \leq \text{EV}_{DD} < 4.0 \text{ V}, 2.3 \text{ V} \leq \text{V}_b \leq 2.7 \text{ V}, \\ C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	200		610		610		610		ns
		$ \begin{aligned} &4.0 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ &C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 2.8 \text{ k}\Omega \end{aligned} $	675		610		610		610		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD}} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	600		610		610		610		ns
		$ \begin{array}{c} 1.8 \text{ V} \leq \text{EV}_{\text{DD}} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V} \text{ Note 2}, \\ C_{\text{b}} = 100 \text{ pF}, \ R_{\text{b}} = 5.5 \text{ k}\Omega \end{array} $	610		610		610		610		ns
Data setup time (reception)	tsu: DAT	$ \begin{aligned} &4.0 \text{ V} \leq \text{EV}_{DD} \leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_b \leq 4.0 \text{ V}, \\ &C_b = 50 \text{ pF}, \text{ R}_b = 2.7 \text{ k}\Omega \end{aligned} $	1/fмск + 135 Note 3		1/fмск + 190 Note 2		1/fмск + 190 Note 3		1/fмск + 190 Note 3		ns
		$2.7 \text{ V} \le \text{EV}_{DD} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	1/fмск + 135 Note 3		1/fмск + 190 Note 2		1/fмск + 190 Note 3		1/fмcк + 190 Note 3		ns
		$ 4.0 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V}, $ $ C_b = 100 \text{ pF}, R_b = 2.8 \text{ k}\Omega $	1/fмск + 190 Note 3		1/fмск + 190 Note 3		1/fмск + 190 Note 3		1/fмск + 190 Note 3		ns
		$2.7 \text{ V} \le \text{EV}_{DD} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $C_b = 100 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	1/fмcк + 190 Note 3		1/fмск + 190 Note 3		1/fмск + 190 Note 3		1/fмск + 190 Note 3		ns
		$\begin{array}{l} 1.8 \text{ V} \leq \text{EV}_{\text{DD}} < 4.0 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_{b} \leq 2.0 \text{ V} \ \text{Note 2}, \\ C_{b} = 100 \text{ pF}, \ R_{b} = 5.5 \text{ k}\Omega \end{array}$	1/fмcк + 190 Note 3		1/fмск + 190 Note 3		1/fмск + 190 Note 3		1/fмск + 190 Note 3		ns
Data hold time (transmission)	thd:	$ 4.0 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, $ $ C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k} \Omega $	0	305	0	305	0	305	0	305	ns
		$2.7 \text{ V} \leq \text{EV}_{\text{DD}} < 4.0 \text{V}, \ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, \ R_{\text{b}} = 2.7 \text{ k}\Omega$	0	305	0	305	0	305	0	305	ns
		$ \begin{aligned} &4.0 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ &C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 2.8 \text{ k}\Omega \end{aligned} $	0	355	0	355	0	355	0	355	ns
		$2.7 \text{ V} \leq \text{EV}_{\text{DD}} < 4.0 \text{ V}, 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	0	355	0	355	0	355	0	355	ns
		$ 1.8 \text{ V} \leq \text{EV}_{DD} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_b \leq 2.0 \text{ V} \text{ Note 2}, $	0	405	0	405	0	405	0	405	ns

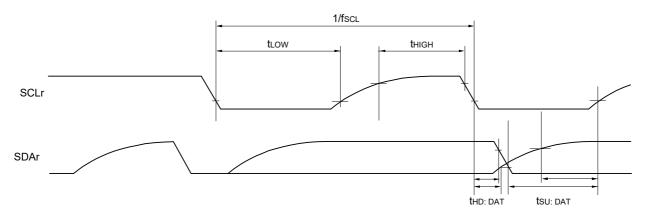
- Note 1. The value must be equal to or less than fMCK/4.
- Note 2. Use it with $EVDD \ge Vb$.
- Note 3. Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the TTL input buffer and the N-ch open drain output (EVDD tolerance) mode for the SDAr pin and the N-ch open drain output (EVDD tolerance) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



- **Remark 1.** Rb[Ω]: Communication line (SDAr, SCLr) pull-up resistance, Cb[F]: Communication line (SDAr, SCLr) load capacitance, Vb[V]: Communication line voltage
- **Remark 2.** r: IIC number (r = 00, 01, 10 and 11), g: PIM, POM number (g = 0, 3 and 5)
- Remark 3. fmck: Serial array unit operation clock frequency

 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0),

 n: Channel number (n = 0 to 3), mn = 00 to 03)

2.5.2 Serial interface IICA

(1) I²C standard mode

(TA = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	C	Conditions		h-speed) mode	,	v-speed mode	,	v-power mode		-voltage mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock	fscL	Standard mode:	$2.7 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V}$	0	100	0	100	0	100	0	100	kHz
frequency		fclk ≥ 1 MHz	1.8 V ≤ EVDD ≤ 5.5 V	0	100	0	100	0	100	0	100	kHz
			1.7 V ≤ EVDD ≤ 5.5 V	0	100	0	100	0	100	0	100	kHz
			1.6 V ≤ EVDD ≤ 5.5 V	-		0	100	0	100	0	100	kHz
Setup time of	tsu: sta	2.7 V ≤ EV _{DD} ≤ 5	5 V	4.7		4.7		4.7		4.7		μs
restart condition		1.8 V ≤ EV _{DD} ≤ 5	5 V	4.7		4.7		4.7		4.7		μs
		1.7 V ≤ EV _{DD} ≤ 5	5 V	4.7		4.7		4.7		4.7		μs
		1.6 V ≤ EV _{DD} ≤ 5	5 V	-	_	4.7		4.7		4.7		μs
Hold time Note 1	thd: STA	2.7 V ≤ EV _{DD} ≤ 5	.5 V	4.0		4.0		4.0		4.0		μs
		1.8 V ≤ EV _{DD} ≤ 5	.5 V	4.0		4.0		4.0		4.0		μs
		1.7 V ≤ EV _{DD} ≤ 5	.5 V	4.0		4.0		4.0		4.0		μs
		1.6 V ≤ EV _{DD} ≤ 5.	5 V	-	_	4.0		4.0		4.0		μs
Hold time when	tLOW	2.7 V ≤ EV _{DD} ≤ 5	5 V	4.7		4.7		4.7		4.7		μs
SCLA0 = "L"		1.8 V ≤ EV _{DD} ≤ 5	5 V	4.7		4.7		4.7		4.7		μs
		1.7 V ≤ EV _{DD} ≤ 5	.5 V	4.7		4.7		4.7		4.7		μs
		1.6 V ≤ EV _{DD} ≤ 5	5 V	-	_	4.7		4.7		4.7		μs
Hold time when	thigh	2.7 V ≤ EV _{DD} ≤ 5	.5 V	4.0		4.0		4.0		4.0		μs
SCLA0 = "H"		1.8 V ≤ EV _{DD} ≤ 5	.5 V	4.0		4.0		4.0		4.0		μs
		1.7 V ≤ EV _{DD} ≤ 5	.5 V	4.0		4.0		4.0		4.0		μs
		1.6 V ≤ EV _{DD} ≤ 5	5 V		_	4.0		4.0		4.0		μs
Data setup time	tsu: dat	2.7 V ≤ EV _{DD} ≤ 5	.5 V	250		250		250		250		ns
(reception)		1.8 V ≤ EV _{DD} ≤ 5	.5 V	250		250		250		250		ns
		1.7 V ≤ EV _{DD} ≤ 5	.5 V	250		250		250		250		ns
		1.6 V ≤ EV _{DD} ≤ 5	5 V	-	_	250		250		250		ns
Data hold time	thd: dat	2.7 V ≤ EV _{DD} ≤ 5	.5 V	0	3.45	0	3.45	0	3.45	0	3.45	μs
(transmission) Note 2		1.8 V ≤ EV _{DD} ≤ 5	5 V	0	3.45	0	3.45	0	3.45	0	3.45	μs
Note 2		1.7 V ≤ EV _{DD} ≤ 5	5 V	0	3.45	0	3.45	0	3.45	0	3.45	μs
		1.6 V ≤ EV _{DD} ≤ 5	.5 V		_	0	3.45	0	3.45	0	3.45	μs
Setup time of	tsu: sto	2.7 V ≤ EV _{DD} ≤ 5	.5 V	4.0		4.0		4.0		4.0		μs
stop condition		1.8 V ≤ EV _{DD} ≤ 5	5 V	4.0		4.0		4.0		4.0		μs
		1.7 V ≤ EV _{DD} ≤ 5	.5 V	4.0		4.0		4.0		4.0		μs
		1.6 V ≤ EV _{DD} ≤ 5	.5 V		_	4.0		4.0		4.0		μs
Bus-free time	tbur	2.7 V ≤ EV _{DD} ≤ 5	5 V	4.7		4.7		4.7		4.7		μs
		1.8 V ≤ EV _{DD} ≤ 5	.5 V	4.7		4.7		4.7		4.7		μs
		1.7 V ≤ EV _{DD} ≤ 5	.5 V	4.7		4.7		4.7		4.7		μs
		1.6 V ≤ EV _{DD} ≤ 5	.5 V	-	_	4.7		4.7		4.7		μs

Note 1. The first clock pulse is generated after this period when the start/restart condition is detected.

Note 2. The maximum value (MAX.) of this during normal transfer and a clock stretch state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR02) in the peripheral I/O redirection register 0 (PIOR0) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.



Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: C_b = 400 pF, R_b = 2.7 $k\Omega$



(2) I2C fast mode

(TA = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol			speed	high- I main) ode	speed	(low- main) ode	power	Low- main) ode	volt	low- age mode	Unit
			1		MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode:	$2.7 \text{ V} \leq \text{EV}_{DD} \leq 5.5 \text{ V}$	0	400	0	400	0	400	0	400	kHz
		fclk ≥ 3.5 MHz	1.8 V ≤ EV _{DD} ≤ 5.5 V	0	400	0	400	0	400	0	400	kHz
Setup time of restart	tsu: sta	2.7 V ≤ EV _{DD} ≤ 5	.5 V	0.6		0.6		0.6		0.6		μs
condition		1.8 V ≤ EV _{DD} ≤ 5	.5 V	0.6		0.6		0.6		0.6		μs
Hold time Note 1	thd: sta	2.7 V ≤ EV _{DD} ≤ 5	.5 V	0.6		0.6		0.6		0.6		μs
		1.8 V ≤ EV _{DD} ≤ 5	.5 V	0.6		0.6		0.6		0.6		μs
Hold time when SCLA0 = "L"	tLOW	2.7 V ≤ EV _{DD} ≤ 5	.5 V	1.3		1.3		1.3		1.3		μs
		1.8 V ≤ EV _{DD} ≤ 5	.5 V	1.3		1.3		1.3		1.3		μs
Hold time when SCLA0 = "H"	tніgн	2.7 V ≤ EV _{DD} ≤ 5	.5 V	0.6		0.6		0.6		0.6		μs
		1.8 V ≤ EV _{DD} ≤ 5	.5 V	0.6		0.6		0.6		0.6		μs
Data setup time (reception)	tsu: DAT	2.7 V ≤ EV _{DD} ≤ 5	.5 V	100		100		100		100		ns
		1.8 V ≤ EV _{DD} ≤ 5	.5 V	100		100		100		100		ns
Data hold time (transmission)	thd: dat	2.7 V ≤ EV _{DD} ≤ 5	.5 V	0	0.9	0	0.9	0	0.9	0	0.9	μs
Note 2		1.8 V ≤ EV _{DD} ≤ 5	.5 V	0	0.9	0	0.9	0	0.9	0	0.9	μs
Setup time of stop condition	tsu: sto	2.7 V ≤ EVDD ≤ 5	.5 V	0.6		0.6		0.6		0.6		μs
		1.8 V ≤ EVDD ≤ 5	.5 V	0.6		0.6		0.6		0.6		μs
Bus-free time	tBUF	2.7 V ≤ EV _{DD} ≤ 5	.5 V	1.3		1.3		1.3		1.3		μs
		1.8 V ≤ EVDD ≤ 5	.5 V	1.3		1.3		1.3		1.3		μs

Note 1. The first clock pulse is generated after this period when the start/restart condition is detected.

Note 2. The maximum value (MAX.) of this during normal transfer and a clock stretch state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR02) in the peripheral I/O redirection register 0 (PIOR0) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode: Cb = 320 pF, Rb = 1.1 k Ω

(3) I²C fast mode plus

(Ta = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Cor	Conditions		high- l main) ode	LS (low- speed main) mode		LP (Low- power main) mode		LV (low- voltage main) mode		Unit
			1		MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode plus: fclk ≥ 10 MHz	2.7 V ≤ EVDD ≤ 5.5 V	0	1000	_		-	_	-	_	kHz
Setup time of restart condition	tsu: sta	2.7 V ≤ EV _{DD} ≤ 5.	5 V	0.26		-	-	-	-	-	_	μs
Hold time Note 1	thd: STA	$2.7 \text{ V} \leq \text{EV}_{DD} \leq 5.$	5 V	0.26		_		_	_	_		μs
Hold time when SCLA0 = "L"	tLOW	$2.7 \text{ V} \leq \text{EV}_{DD} \leq 5.$	5 V	0.5		_		-	_	-	_	μs
Hold time when SCLA0 = "H"	tніgн	$2.7 \text{ V} \leq \text{EV}_{DD} \leq 5.$	5 V	0.26		_			_	_	_	μs
Data setup time (reception)	tsu: DAT	$2.7 \text{ V} \leq \text{EV}_{DD} \leq 5.$	5 V	50		-	_			-	_	ns
Data hold time (transmission) Note 2	thd: dat	2.7 V ≤ EV _{DD} ≤ 5.	7 V ≤ EV _{DD} ≤ 5.5 V		0.45	-	-	=	_	-	_	μs
Setup time of stop condition	tsu: sto	$2.7 \text{ V} \leq \text{EV}_{DD} \leq 5.$	5 V	0.26		_	_	_	_	_	_	μs
Bus-free time	t BUF	$2.7 \text{ V} \leq \text{EV}_{DD} \leq 5.$.7 V ≤ EVDD ≤ 5.5 V			_		_				μs

Note 1. The first clock pulse is generated after this period when the start/restart condition is detected.

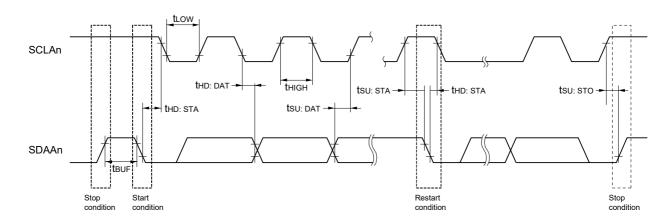
Note 2. The maximum value (MAX.) of thd: DAT is during normal transfer and a clock stretch state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR02) in the peripheral I/O redirection register 0 (PIOR0) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode plus: C_b = 120 pF, R_b = 1.1 k Ω

IICA serial transfer timing



Remark n = 0, 1

2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Reference Voltage Input channel	Reference voltage (+) = AVREFP Reference voltage (-) = AVREFM	Reference voltage (+) = VDD Reference voltage (-) = VSS	Reference voltage (+) = V _{BGR} Reference voltage (-)= AV _{REFM}
ANI0 to ANI3	Refer to 2.6.1 (1).	Refer to 2.6.1 (3).	Refer to 2.6.1 (4).
ANI16 to ANI22	Refer to 2.6.1 (2).		
Internal reference voltage Temperature sensor output voltage	Refer to 2.6.1 (1) .		_

(1) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI2 and ANI3, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +85°C, 1.6 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Condition	ns	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution	1.8 V ≤ AVREFP ≤ 5.5 V		1.2	±3.5	LSB
		AVREFP = V _{DD} Note 3	1.6 V ≤ AVREFP ≤ 5.5 V Note 4		1.2	±7.0	LSB
Conversion time	tconv	10-bit resolution	3.6 V ≤ VDD ≤ 5.5 V	2.125		39	μs
		Target pin: ANI2 and ANI3	2.7 V ≤ VDD ≤ 5.5 V	3.1875		39	μs
			1.8 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
			1.6 V ≤ VDD ≤ 5.5 V	57		95	μs
		10-bit resolution	3.6 V ≤ VDD ≤ 5.5 V	2.375		39	μs
		Target pin: Internal reference voltage,	2.7 V ≤ VDD ≤ 5.5 V	3.5625		39	μs
		and temperature sensor output voltage	1.8 V ≤ VDD ≤ 5.5 V	17		39	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution	1.8 V ≤ AVREFP ≤ 5.5 V			±0.25	%FSR
		AVREFP = VDD Note 3	1.6 V ≤ AVREFP ≤ 5.5 V Note 4			±0.50	%FSR
Full-scale error Notes 1, 2	Ers	10-bit resolution	1.8 V ≤ AVREFP ≤ 5.5 V			±0.25	%FSR
		AVREFP = VDD Note 3	1.6 V ≤ AVREFP ≤ 5.5 V Note 4			±0.50	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	1.8 V ≤ AVREFP ≤ 5.5 V			±2.5	LSB
		AV _{REFP} = V _{DD} Note 3	1.6 V ≤ AVREFP ≤ 5.5 V Note 4			±5.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	1.8 V ≤ AVREFP ≤ 5.5 V			±1.5	LSB
		AV _{REFP} = V _{DD} Note 3	1.6 V ≤ AVREFP ≤ 5.5 V Note 4			±2.0	LSB
Analog input voltage	Vain	ANI2 and ANI3		0		AVREFP	V
		Internal reference voltage (1.8 V ≤ V _{DD} ≤ 5.5 V)			/ _{BGR} Note	5	V
		Temperature sensor output voltage (1.8 V ≤ V _{DD} ≤ 5.5 V)		Vī	MPS25 Not	te 5	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

Note 3. When AVREFP < VDD, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when AVREFP = VDD. Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AVREFP = VDD. Integral linearity error/ Differential linearity error: Add ± 0.5 LSB to the MAX. value when AVREFP = VDD.

Note 4. Values when the conversion time is set to 57 μ s (min.) and 95 μ s (max.).

Note 5. Refer to 2.6.2 Temperature sensor characteristics/internal reference voltage characteristic.



(2) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI16 to ANI22

(Ta = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, 1.6 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Cond	litions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution	1.8 V ≤ AVREFP ≤ 5.5 V		1.2	±5.0	LSB
		EV _{DD} ≤ AV _{REFP} = V _{DD} Notes 3, 4	1.6 V ≤ AVREFP ≤ 5.5 V Note 5		1.2	±8.5	LSB
Conversion time	tconv	10-bit resolution	3.6 V ≤ VDD ≤ 5.5 V	2.125		39	μs
		Target ANI pin: ANI16 to ANI22	2.7 V ≤ VDD ≤ 5.5 V	3.1875		39	μs
			1.8 V ≤ VDD ≤ 5.5 V	17		39	μs
			1.6 V ≤ VDD ≤ 5.5 V	57		95	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution	1.8 V ≤ AVREFP ≤ 5.5 V			±0.35	%FSR
		EV _{DD} ≤ AV _{REFP} = V _{DD} Notes 3, 4	1.6 V ≤ AVREFP ≤ 5.5 V Note 5			±0.60	%FSR
Full-scale error Notes 1, 2	Ers	10-bit resolution	1.8 V ≤ AVREFP ≤ 5.5 V			±0.35	%FSR
		EV _{DD} ≤ AV _{REFP} = V _{DD} Notes 3, 4	1.6 V ≤ AVREFP ≤ 5.5 V Note 5			±0.60	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	1.8 V ≤ AVREFP ≤ 5.5 V			±3.5	LSB
		EV _{DD} ≤ AV _{REFP} = V _{DD} Notes 3, 4	1.6 V ≤ AVREFP ≤ 5.5 V Note 5			±6.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	1.8 V ≤ AVREFP ≤ 5.5 V			±2.0	LSB
		EV _{DD} ≤ AV _{REFP} = V _{DD} Notes 3, 4	1.6 V ≤ AVREFP ≤ 5.5 V Note 5			±2.5	LSB
Analog input voltage	VAIN	ANI16 to ANI22		0		AVREFP and EVDD	V

- Note 1. Excludes quantization error (±1/2 LSB).
- Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- **Note 3.** When $EVDD \le AVREFP < VDD$, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when AVREFP = VDD. Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AVREFP = VDD. Integral linearity error/ Differential linearity error: Add ± 0.5 LSB to the MAX. value when AVREFP = VDD.

Note 4. When AVREFP \leq EVDD \leq VDD, the MAX. values are as follows.

Overall error: Add ± 4.0 LSB to the MAX. value when AVREFP = VDD. Zero-scale error/Full-scale error: Add $\pm 0.20\%$ FSR to the MAX. value when AVREFP = VDD. Integral linearity error/ Differential linearity error: Add ± 2.0 LSB to the MAX. value when AVREFP = VDD.

Note 5. When the conversion time is set to 57 μs (min.) and 95 μs (max.).

(3) When reference voltage (+) = VDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = Vss (ADREFM = 0), target pin: ANI0 to ANI3, ANI16 to ANI22, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = VDD, Reference voltage (-) = Vss)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V		1.2	±7.0	LSB
			1.6 V ≤ V _{DD} ≤ 5.5 V Note 3		1.2	±10.5	LSB
Conversion time	tconv	10-bit resolution	3.6 V ≤ VDD ≤ 5.5 V	2.125		39	μs
		Target pin: ANI0 to ANI3, ANI16 to ANI22	2.7 V ≤ V _{DD} ≤ 5.5 V	3.1875		39	μs
			1.8 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
			1.6 V ≤ V _{DD} ≤ 5.5 V	57		95	μs
		10-bit resolution	3.6 V ≤ V _{DD} ≤ 5.5 V	2.375		39	μs
		Target pin: internal reference voltage, and temperature sensor output voltage	$2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	3.5625		39	μs
		temperature sensor output voltage	1.8 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V			±0.60	%FSR
			1.6 V ≤ V _{DD} ≤ 5.5 V Note 3			±0.85	%FSR
Full-scale error Notes 1, 2	Ers	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V			±0.60	%FSR
			1.6 V ≤ V _{DD} ≤ 5.5 V Note 3			±0.85	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V			±4.0	LSB
			1.6 V ≤ V _{DD} ≤ 5.5 V Note 3			±6.5	LSB
Differential linearity error	DLE	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V			±2.0	LSB
Note 1			1.6 V ≤ V _{DD} ≤ 5.5 V Note 3			±2.5	LSB
Analog input voltage	Vain	ANI0 to ANI3	•	0		VDD	V
		ANI16 to ANI22		0		EV _{DD}	V
		Internal reference voltage (1.8 V ≤ V _{DD} ≤ 5.5 V)		\	/ _{BGR} Note	4	V
		Temperature sensor output voltage (1.8 V ≤ V _{DD} ≤ 5.5 V)		Vı	rmps25 Not	te 4	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

Note 3. When the conversion time is set to 57 μ s (min.) and 95 μ s (max.).

Note 4. Refer to 2.6.2 Temperature sensor characteristics/internal reference voltage characteristic.

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI0, ANI2 and ANI3, ANI16 to ANI22

(TA = -40 to +85°C, 1.8 V \leq VDD \leq 5.5 V, 1.6 V \leq EVDD \leq VDD, Vss = 0 V, Reference voltage (+) = VBGR Note 3, Reference voltage (-) = AVREFM = 0 V Note 4)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		bit
Conversion time	tconv		17		39	μs
Zero-scale error Notes 1, 2	Ezs				±0.60	% FSR
Integral linearity error Note 1	ILE				±2.0	LSB
Differential linearity error Note 1	DLE				±1.0	LSB
Analog input voltage	Vain		0		V _{BGR} Note 3	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

Note 3. Refer to 2.6.2 Temperature sensor characteristics/internal reference voltage characteristic.

Note 4. When reference voltage (-) = Vss, the MAX. values are as follows.

Zero-scale error: Add $\pm 0.35\%$ FSR to the MAX. value when reference voltage (-) = AVREFM. Integral linearity error: Add ± 0.5 LSB to the MAX. value when reference voltage (-) = AVREFM. Differential linearity error: Add ± 0.2 LSB to the MAX. value when reference voltage (-) = AVREFM.

2.6.2 Temperature sensor characteristics/internal reference voltage characteristic

 $(TA = -40 \text{ to } +85^{\circ}C, 1.8 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	VTMPS25	Setting ADS register = 80H, T _A = +25°C		1.05		V
Internal reference voltage	VBGR	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	FVTMPS	Temperature sensor that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tamp	$2.4 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$	5			μs
		1.8 V ≤ VDD < 2.4 V	10			μs

2.6.3 D/A converter (channel 1)

(Ta = -40 to +85°C, 1.6 V \leq EVss \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Cor	MIN.	TYP.	MAX.	Unit	
Resolution	RES				8	bit	
Overall error	AINL	Rload = 4 MΩ	1.8 V ≤ V _{DD} ≤ 5.5 V			±2.5	LSB
		Rload = 8 MΩ	$1.8 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$			±2.5	LSB
Settling time	tset	Cload = 20 pF	$2.7 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$			3	μs
			1.6 V ≤ V _{DD} < 2.7 V			6	μs

2.6.4 Comparator

(Comparator 0: Ta = -40 to +85°C, 2.7 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V) (Comparator 1: Ta = -40 to +85°C, 1.6 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Cor	nditions	MIN.	TYP.	MAX.	Unit
Input voltage range	VIREF0	IVREF0 pin		0		V _{DD} - 1.4 Note 1	V
	VIREF1	IVREF1 pin		1.4 Note 1		VDD	V
	VICMP	IVCMP0 pin		-0.3		V _{DD} + 0.3	V
		IVCMP1 pin		-0.3		EV _{DD} + 0.3	V
Output delay td VDD = 3.0 V Input slew rate > 50 m	V _{DD} = 3.0 V Input slew rate > 50 mV/μs	Comparator high-speed mode, standard mode			1.2	μs	
			Comparator high-speed mode, window mode			2.0	μs
			Comparator low-speed mode, standard mode		3		μs
			Comparator low-speed mode, window mode		4		μs
Operation stabilization wait time	tсмр			100			μs
Reference voltage declination in channel 0 of internal DAC Note 2	∆VIDAC					± 2.5	LSB

Note 1. In window mode, make sure that $VREF1 - VREF0 \ge 0.2 \text{ V}$.

Note 2. Only in CMP0

2.6.5 PGA

(TA = -40 to +85°C, 2.7 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Cor	nditions	MIN.	TYP.	MAX.	Unit
Input offset voltage	VIOPGA					±10	mV
Input voltage range	VIPGA			0		0.9 × V _{DD} /Gain	V
Output voltage range	VIOHPGA			$0.93 \times V_{DD}$			V
	VIOLPGA					$0.07 \times V_{DD}$	V
Gain error		x4, x8				±1	%
		x16				±1.5	%
		x32			±2	%	
Slew rate	SRRPGA	Rising When VIN = 0.1Vpb/gain to 0.9Vpb/gain. 10 to 90% of output voltage amplitude	4.0 V ≤ V _{DD} ≤ 5.5 V (Other than x32)	3.5			V/µs
			4.0 V ≤ V _{DD} ≤ 5.5 V (x32)	3.0			
			2.7 V ≤ V _{DD} ≤ 4.0V	0.5			
SRF	SR _{FPGA}	Falling When VIN= 0.1Vpb/gain to 0.9Vpb/gain.	4.0 V ≤ V _{DD} ≤ 5.5 V (Other than x32)	3.5			
		90 to 10% of output	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} (x32)$	3.0			
		voltage amplitude	$2.7 \text{ V} \leq \text{V}_{DD} \leq 4.0 \text{V}$	0.5			
Reference voltage	t PGA	x4, x8				5	μs
stabilization wait time ^{Note} x16, x32					10	μs	

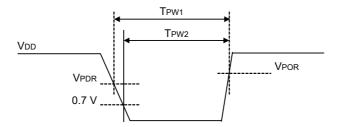
Note Time required until a state is entered where the DC and AC specifications of the PGA are satisfied after the PGA operation has been enabled (PGAEN = 1).

2.6.6 POR circuit characteristics

(TA = -40 to +85°C, Vss = 0 V)

Parameter	Symbol	Conditions		TYP.	MAX.	Unit
Detection voltage	VPOR	The power supply voltage is rising.	1.47	1.51	1.55	V
	VPDR	The power supply voltage is falling. Note 1	1.46	1.50	1.54	V
Minimum pulse width Note 2	TpW1	Other than STOP/SUB HALT/SUB RUN	300			μs
	TPW2	STOP/SUB HALT/SUB RUN	300			μs

- **Note 1.** However, when the operating voltage falls while the LVD is off, enter STOP mode, or enable the reset status using the external reset pin before the voltage falls below the operating voltage range shown in 2.4 AC Characteristics.
- Note 2. Minimum time required for a POR reset when VDD exceeds below VPDR. This is also the minimum time required for a POR reset from when VDD exceeds below 0.7 V to when VDD exceeds VPOR while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



2.6.7 LVD circuit characteristics

(1) LVD Detection Voltage of Reset Mode and Interrupt Mode

(TA = -40 to +85°C, VPDR \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Pa	rameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	Supply voltage level	VLVD0	The power supply voltage is rising.	3.98	4.06	4.14	V
			The power supply voltage is falling.	3.90	3.98	4.06	V
		VLVD1	The power supply voltage is rising.	3.68	3.75	3.82	V
			The power supply voltage is falling.	3.60	3.67	3.74	V
		VLVD2	The power supply voltage is rising.	3.07	3.13	3.19	V
			The power supply voltage is falling.	3.00	3.06	3.12	V
		VLVD3	The power supply voltage is rising.	2.96	3.02	3.08	V
			The power supply voltage is falling.	2.90	2.96	3.02	V
		VLVD4	The power supply voltage is rising.	2.86	2.92	2.97	V
			The power supply voltage is falling.	2.80	2.86	2.91	V
		VLVD5	The power supply voltage is rising.	2.76	2.81	2.87	V
			The power supply voltage is falling.	2.70	2.75	2.81	V
		VLVD6	The power supply voltage is rising.	2.66	2.71	2.76	V
			The power supply voltage is falling.	2.60	2.65	2.70	V
		VLVD7	The power supply voltage is rising.	2.56	2.61	2.66	V
			The power supply voltage is falling.	2.50	2.55	2.60	V
		VLVD8	The power supply voltage is rising.	2.45	2.50	2.55	V
			The power supply voltage is falling.	2.40	2.45	2.50	V
		VLVD9	The power supply voltage is rising.	2.05	2.09	2.13	V
			The power supply voltage is falling.	2.00	2.04	2.08	V
		VLVD10	The power supply voltage is rising.	1.94	1.98	2.02	V
			The power supply voltage is falling.	1.90	1.94	1.98	V
		VLVD11	The power supply voltage is rising.	1.84	1.88	1.91	V
			The power supply voltage is falling.	1.80	1.84	1.87	V
		VLVD12	The power supply voltage is rising.	1.74	1.77	1.81	V
			The power supply voltage is falling.	1.70	1.73	1.77	V
		VLVD13	The power supply voltage is rising.	1.64	1.67	1.70	V
			The power supply voltage is falling.	1.60	1.63	1.66	V
Minimum pulse wid	Minimum pulse width			300			μs
Detection delay time	е					300	μs

(2) LVD Detection Voltage of Interrupt & Reset Mode

(TA = -40 to +85°C, VPDR \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conc	ditions	MIN.	TYP.	MAX.	Unit
Interrupt and	VLVDA0	VPOC0, VPOC1, VPOC2 = 0, 0, 0, fa	illing reset voltage	1.60	1.63	1.66	V
reset mode	VLVDA1	LVIS0, LVIS1 = 1, 0	Rising release reset voltage	1.74	1.77	1.81	V
			Falling interrupt voltage	1.70	1.73	1.77	V
	VLVDA2	LVIS0, LVIS1 = 0, 1	Rising release reset voltage	1.84	1.88	1.91	V
			Falling interrupt voltage	1.80	1.84	1.87	V
	VLVDA3	LVIS0, LVIS1 = 0, 0	Rising release reset voltage	2.86	2.92	2.97	V
			Falling interrupt voltage	2.80	2.86	2.91	V
	VLVDB0	VPOC0, VPOC1, VPOC2 = 0, 0, 1, fa	1.80	1.84	1.87	V	
	VLVDB1	LVIS0, LVIS1 = 1, 0	Rising release reset voltage	1.94	1.98	2.02	V
VLVDB2			Falling interrupt voltage	1.90	1.94	1.98	V
	VLVDB2	LVIS0, LVIS1 = 0, 1	Rising release reset voltage	2.05	2.09	2.13	V
			Falling interrupt voltage	2.00	2.04	2.08	V
	VLVDB3	LVIS0, LVIS1 = 0, 0	Rising release reset voltage	3.07	3.13	3.19	V
			Falling interrupt voltage	3.00	3.06	3.12	V
	VLVDC0	VPOC0, VPOC1, VPOC2 = 0, 1, 0, fa	VPOC0, VPOC1, VPOC2 = 0, 1, 0, falling reset voltage				V
	VLVDC1	LVIS0, LVIS1 = 1, 0	Rising release reset voltage	2.56	2.61	2.66	V
			Falling interrupt voltage	2.50	2.55	2.60	V
	VLVDC2	LVIS0, LVIS1 = 0, 1	Rising release reset voltage	2.66	2.71	2.76	V
			Falling interrupt voltage	2.60	2.65	2.70	V
	VLVDC3	LVIS0, LVIS1 = 0, 0	Rising release reset voltage	3.68	3.75	3.82	V
			Falling interrupt voltage	3.60	3.67	3.74	V
	VLVDD0	VPOC0, VPOC1, VPOC2 = 0, 1, 1, fa	Illing reset voltage	2.70	2.75	2.81	V
	VLVDD1	LVIS0, LVIS1 = 1, 0	Rising release reset voltage	2.86	2.92	2.97	V
VLV			Falling interrupt voltage	2.80	2.86	2.91	V
	VLVDD2	LVIS0, LVIS1 = 0, 1	Rising release reset voltage	2.96	3.02	3.08	V
			Falling interrupt voltage	2.90	2.96	3.02	V
	VLVDD3	LVIS0, LVIS1 = 0, 0	Rising release reset voltage	3.98	4.06	4.14	V
			Falling interrupt voltage	3.90	3.98	4.06	V

2.6.8 Power supply voltage rising slope characteristics

$(TA = -40 \text{ to } +85^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

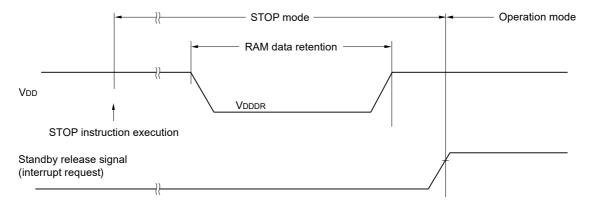
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until VDD reaches the operating voltage range shown in 2.4 AC Characteristics.

2.7 RAM Data Retention Characteristics

(TA = -40 to +85°C, 1.8 V \leq EVDD \leq VDD \leq 5.5 V, VSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.46 Note		5.5	V

Note The value depends on the POR detection voltage. When the voltage drops, the RAM data is retained before a POR reset is effected, but RAM data is not retained when a POR reset is effected.



2.8 Flash Memory Programming Characteristics

 $(TA = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EVDD} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditi	MIN.	TYP.	MAX.	Unit	
System clock frequency	fclk	1.8 V ≤ VDD ≤ 5.5 V	1		24	MHz	
Number of code flash rewrites Notes 1, 2, 3	Cerwr	Retained for 20 years T _A = 85°C		1,000			Times
Number of data flash rewrites		Retained for 1 year	TA = 25°C		1,000,000		
Notes 1, 2, 3		Retained for 5 years	Ta = 85°C	100,000			
		Retained for 20 years	Ta = 85°C	10,000			

- Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.
- Note 2. When using flash memory programmer and Renesas Electronics self-programming library
- **Note 3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

2.9 Dedicated Flash Memory Programmer Communication (UART)

$(TA = -40 \text{ to } +85^{\circ}C, 1.8 \text{ V} \le EVDD \le VDD \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

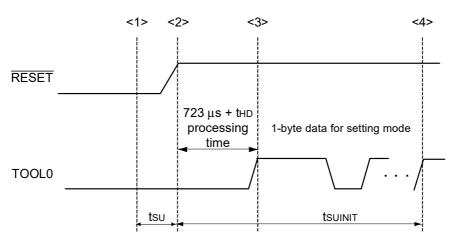
2.10 Timing of Entry to Flash Memory Programming Modes

$(TA = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EVDD} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified Note 1	tsuinit	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends Note 1	tsu	POR and LVD reset must end before the external reset ends.	10			μs
How long the TOOL0 pin must be kept at the low level after an external reset ends (excluding the processing time of the firmware to control the flash memory) Notes 1, 2	thD	POR and LVD reset must end before the external reset ends.	1			ms

Note 1. Deassertion of the POR and LVD reset signals must precede deassertion of the pin reset signal.

Note 2. This excludes the flash firmware processing time (723 μ s).



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset ends (POR and LVD reset must end before the external reset ends).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark tsuinit: The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the external resets end.

tsu: How long from when the TOOL0 pin is placed at the low level until a pin reset ends
thd: How long to keep the TOOL0 pin at the low level from when the external resets end
(excluding the processing time of the firmware to control the flash memory)

3. ELECTRICAL SPECIFICATIONS (TA = -40 to +105°C)

This chapter describes the following electrical specifications. Target products G: Industrial applications (TA = -40 to +105°C) R5F105xxGxx

- Caution 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
- Caution 2. The pins mounted depend on the product. Refer to 2.1 Port Functions to 2.2.1 Functions for each product in the RL78/G11 User's Manual.
- Caution 3. Please contact Renesas Electronics sales office for derating of operation under TA = +85 to +105°C.

 Derating is the systematic reduction of load for the sake of improved reliability.
- Caution 4. When operating temperature exceeds 85°C, only HS (high-speed main) mode can be used as the flash operation mode. Regulator mode should be used with the normal setting (MCSEL = 0).
- Caution 5. The EVDD pin is not present on products with 24 or less pins. Accordingly, replace EVDD with VDD and the voltage condition 1.6 ≤ EVDD ≤ VDD ≤ 5.5 V with 1.6 ≤ VDD ≤ 5.5 V.
- Remark When the products "G: Industrial applications" is used in the range of TA = -40 to +85°C, see 2. ELECTRICAL SPECIFICATIONS (TA = -40 to +85°C).

Fields of application	A: Consumer applications	G: Industrial applications
Operating ambient temperature	TA = -40 to +85°C	TA = -40 to +105°C
Operating mode Operating Voltage Range	HS (High-speed main) mode: $2.7 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V} \textcircled{m} \text{ 1 MHz to 24 MHz}$ $2.4 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V} \textcircled{m} \text{ 1 MHz to 16 MHz}$ $LS \text{ (Low-speed main) mode:}$ $1.8 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V} \textcircled{m} \text{ 1 MHz to 8 MHz}$ $LV \text{ (Low-voltage main) mode:}$ $1.8 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V} \textcircled{m} \text{ 1 MHz to 4 MHz}$	Only in HS (High-speed main) mode: 2.7 V \leq VDD \leq 5.5 V @ 1 MHz to 24 MHz 2.4 V \leq VDD \leq 5.5 V @ 1 MHz to 16 MHz
High-speed on-chip oscillator clock to an accuracy	1.8 V ≤ VDD ≤ 5.5 V: ±1.0% @ TA = -20 to +85°C ±1.5% @ TA = -40 to -20°C 1.6 V ≤ VDD < 1.8 V: ±5.0% @ TA = -20 to +85°C ±5.5% @ TA = -40 to -20°C	2.4 V ≤ VDD ≤ 5.5 V: ±2.0% @ TA = +85 to +105°C ±1.0% @ TA = -20 to +85°C ±1.5% @ TA = -40 to -20°C
Serial array unit	UART Simplified SPI (CSI): fcLk/2 (12 Mbps are supported), fcLk/4 Simplified I ² C	UART Simplified SPI (CSI): fclk/4 Simplified I ² C
IICA	Standard mode Fast mode Fast mode plus	Standard mode Fast mode
Voltage Detector	• Rising: 1.67 V to 4.06 V (14 levels) • Falling: 1.63 V to 3.98 V (14 levels)	• Rising: 2.61 V to 4.06 V (8 levels) • Falling: 2.55 V to 3.98 V (8 levels)

Remark The electrical characteristics for "G: Industrial applications" differ from those for "A: Consumer applications" when the product is in use in an ambient temperature over 85°C. For details, see **3.1** to **3.10** in the following pages.

3.1 Absolute Maximum Ratings

(1/2)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	VDD		-0.5 to +6.5	V
	EVDD		-0.5 to +6.5	V
	AVREFP		0.3 to V _{DD} + 0.3 Note 2	V
	AVREFM		-0.3 to V _{DD} + 0.3 Note 2 and AVREFM ≤ AVREFP	V
REGC pin input voltage	VIREGC	REGC	-0.3 to +2.8 and -0.3 to V _{DD} + 0.3 ^{Note 1}	V
Input voltage	VI1	P00, P01, P30 to P33, P40, and P51 to P56	-0.3 to EVDD + 0.3 and -0.3 to VDD + 0.3 Note 2	V
	VI2	P20 to P23, P121, P122, P125, P137, EXCLK, RESET	-0.3 to V _{DD} + 0.3 Note 2	V
Output voltage	Vo ₁	P00, P01, P30 to P33, P40, and P51 to P56	-0.3 to EVDD + 0.3 and -0.3 to VDD + 0.3 ^{Note 2}	V
	Vo2	P20 to P23	-0.3 to V _{DD} + 0.3 Note 2	V
Analog input voltage	VAI1	ANI16 to ANI22	-0.3 to EVDD + 0.3 and -0.3 to AVREF(+) + 0.3 Notes 2, 3	V
	VAI2	ANI0 to ANI3	-0.3 to V _{DD} + 0.3 and -0.3 to AV _{REF} (+) + 0.3 Notes 2, 3	V

- Note 1. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
- Note 2. Must be 6.5 V or lower.
- **Note 3.** Do not exceed AVREF (+) + 0.3 V in case of A/D conversion target pin.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

- Remark 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
- Remark 2. AVREF (+): + side reference voltage of the A/D converter.
- Remark 3. Vss: Reference voltage

(2/2)

Parameter	Symbols		Conditions	Ratings	Unit		
Output current, high	Іон1	Per pin	P00, P01, P30 to P33, P40, P51 to P56	-40	mA		
		Total of all pins	P00, P01, P40	-70	mA		
		-170 mA	P30 to P33, P51 to P56	-100	mA		
	Іон2	Per pin	P20 to P23	-0.5	mA		
		Total of all pins		-2	mA		
Output current, low	IOL1	Per pin	P00, P01, P30 to P33, P40, P51 to P56	40	mA		
,				Total of all pins	P00, P01, P40	70	mA
		170 mA	P30 to P33, P51 to P56	100	mA		
	IOL2	Per pin	P20 to P23	1	mA		
		Total of all pins		4	mA		
Operating ambient	TA	In normal operat	ion mode	-40 to +105	°C		
temperature		In flash memory	1				
Storage temperature	Tstg			-65 to +150	°C		

Caution

Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

3.2 Oscillator Characteristics

3.2.1 X1 characteristics

$(TA = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Resonator	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx) Note	Ceramic resonator/	$2.7 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$	1.0		20.0	MHz
	crystal resonator	$2.4 \text{ V} \leq \text{VDD} < 2.7 \text{ V}$	1.0		16.0	

Note Indicates only permissible oscillator frequency ranges. Refer to 3.4 AC Characteristics for instruction execution time.

Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator

characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock

oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator, refer to 6.4 System Clock Oscillator in the RL78/G11 User's Manual.

3.2.2 On-chip oscillator characteristics

(TA = -40 to +105°C, 2.4 V \leq VDD \leq 5.5 V, Vss = 0 V)

Oscillators	Parameters	Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency Notes 1, 2	fıн	2.7 V ≤ V _{DD} ≤ 5.5 V	1		24	MHz
		2.4 V ≤ V _{DD} ≤ 5.5 V	1		16	
High-speed on-chip oscillator clock frequency accuracy		T _A = +85°C to +105°C	-2		2	%
		TA = -20°C to +85°C	-1		1	%
		TA = -40°C to -20°C	-1.5		1.5	%
Middle-speed on-chip oscillator oscillation frequency Note 2	fім		1		4	MHz
Middle-speed on-chip oscillator oscillation frequency accuracy			-12		+12	%
Temperature drift of Middle-speed on-chip oscillator oscillation frequency accuracy	DIMT			0.008		%/°C
Voltage drift of Middle-speed on-chip oscillator oscillation frequency accuracy	Diм∨	TA = 25°C		0.02		%/V
Low-speed on-chip oscillator clock frequency Note 2	fiL			15		kHz
Low-speed on-chip oscillator clock frequency accuracy			-15		+15	%

Note 1. High-speed on-chip oscillator frequency is selected with bits 0 to 3 of the option byte (000C2H) and bits 0 to 2 of the HOCODIV register.

Note 2. This only indicates the oscillator characteristics. Refer to 3.4 AC Characteristics for instruction execution time.



3.3 DC Characteristics

3.3.1 Pin characteristics

$(TA = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EVDD} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

(1/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high Note 1	Іон1	Per pin for P00, P01, P30 to P33, P40, and P51 to P56				-3.0 Note 2	mA
		Total of P00, P01, and P40	4.0 V ≤ EVDD ≤ 5.5 V			-12.5	mA
		(When duty ≤ 70% Note 3)	2.7 V ≤ EV _{DD} < 4.0 V			-10.0	mA
			2.4 V ≤ EV _{DD} < 2.7 V			-5.0	mA
		Total of P30 to P33, and P51 to P56	$4.0 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V}$			-30.0	mA
		(When duty ≤ 70% Note 3)	2.7 V ≤ EV _{DD} < 4.0 V			-19.0	mA
			2.4 V ≤ EV _{DD} < 2.7 V			-10.0	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})				-42.5	mA
	Іон2	Per pin for P20 to P23				-0.1 Note 2	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	2.4 V ≤ VDD ≤ 5.5 V			-0.4	mA

- Note 1. Value of current at which the device operation is guaranteed even if the current flows from the VDD pin to an output pin.
- Note 2. Do not exceed the total current value.
- **Note 3.** Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = (IoH \times 0.7)/(n \times 0.01) <Example> Where n = 80% and IoH = -10.0 mA Total output current of pins = (-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P00, P01, P20, P30 to P33, P40 and P51 to P56 do not output high level in N-ch open-drain mode.

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(2/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low Note 1	lo _{L1}	Per pin for P00, P01, P30 to P33, P40, and P51 to P56				8.5 Note 2	mA
		Total of P00, P01, and P40	4.0 V ≤ EV _{DD} ≤ 5.5 V			36.0	mA
		(When duty ≤ 70% ^{Note 3})	2.7 V ≤ EV _{DD} < 4.0 V			15.0	mA
			2.4 V ≤ EV _{DD} < 2.7 V			9.0	mA
		Total of P30 to P33, and P51 to P56	$4.0 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V}$			40.0	mA
		(When duty ≤ 70% ^{Note 3})	2.7 V ≤ EV _{DD} < 4.0 V			35.0	mA
			2.4 V ≤ EVDD < 2.7 V			20.0	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})				76.0	mA
	IOL2	Per pin for P20 to P23				0.4 Note 2	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	2.4 V ≤ VDD ≤ 5.5 V			1.6	mA

- Note 1. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the Vss pin.
- Note 2. Do not exceed the total current value.
- **Note 3.** Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(IoL \times 0.7)/(n \times 0.01)$ <Example> Where n = 80% and IoL = 10.0 mA Total output current of pins = $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

(Ta = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(3/5)

Items	Symbol	Conditions	3	MIN.	TYP.	MAX.	Unit
Input voltage, high	ViH1	P00, P01, P30 to P33, P40, and P51 to P56	Normal mode	0.8 EVDD		EVDD	V
	VIH2	P00, P30 to P32, P40, P51 to P56	TTL mode $4.0 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V}$	2.2		EVDD	V
			TTL mode 3.3 V ≤ EV _{DD} < 4.0 V	2.0		EVDD	V
			TTL mode 2.4 V ≤ EV _{DD} < 3.3 V	1.5		EVDD	V
	VIH3	P20 to P23 (digital input)	0.7 Vdd		VDD	V	
	VIH4	P121, P122, P125, P137, EXCLK	0.8 VDD		VDD	V	
Input voltage, low	VIL1	P00, P01, P30 to P33, P40, and P51 to P56		0		0.2 EVDD	V
	VIL2	P00, P30 to P32, P40, P51 to P56	TTL mode $4.0 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V}$	0		0.8	V
			TTL mode 3.3 V ≤ EV _{DD} < 4.0 V	0		0.5	V
			TTL mode 2.4 V ≤ EV _{DD} < 3.3 V	0		0.32	V
	VIH3	P20 to P23 (digital input)		0		0.3 VDD	V
	VIH4	P121, P122, P125, P137, EXCLK	K, RESET	0		0.2 VDD	V

Caution The maximum value of VIH of pins P00, P01, P20, P30 to P33, P40 and P51 to P56 is VDD or EVDD, even in the N-ch open-drain mode.

(P20: VDD

P00, P01, P30 to P33, P40, P51 to P56: EVDD)

(Ta = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(4/5)

•	-	·	•				•
Items	Symbol	Cond	itions	MIN.	TYP.	MAX.	Unit
Output voltage, high	Vон1	P00, P01, P30 to P33, P40, and P51 to P56	4.0 V ≤ EVDD ≤ 5.5 V, IOH = -3.0 mA	EVDD - 0.7			V
			$2.7 \text{ V} \le \text{EVDD} \le 5.5 \text{ V},$ IOH = -2.0 mA	EVDD - 0.6			٧
			2.4 V ≤ EVDD ≤ 5.5 V IOH = -1.5 mA	EVDD - 0.5			V
	VOH2	P20 to P23	$2.4~V \le V_{DD} \le 5.5~V,$ IOH = -100 μA	VDD - 0.5			V
Output voltage, low	VOL1	P00, P01, P30 to P33, P40, and P51 to P56	$4.0 \text{ V} \le \text{EVDD} \le 5.5 \text{ V},$ $\text{IOL} = 8.5 \text{ mA}$			0.7	٧
			$2.7 \text{ V} \le \text{EVDD} \le 5.5 \text{ V},$ IOL = 3.0 mA			0.6	٧
			$2.7 \text{ V} \le \text{EVDD} \le 5.5 \text{ V},$ $\text{IOL} = 1.5 \text{ mA}$			0.4	٧
			$2.4 \text{ V} \le \text{EVDD} \le 5.5 \text{ V},$ IoL = 0.6 mA			0.4	V
	VOL2	P20 to P23	$2.4~V \le V_{DD} \le 5.5~V$, $I_{OL} = 400~\mu A$			0.4	V

Caution P00, P01, P20, P30 to P33, P40 and P51 to P56 do not output high level in N-ch open-drain mode.

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(5/5)

Items	Symbol	Cond	itions		MIN.	TYP.	MAX.	Unit
Input leakage current, high	ILIH1	P00, P01, P30 to P33, P40, and P51 to P56	VI = EVDD				1	μΑ
	ILIH2	P20 to P23, P125, P137, RESET	Vı = V _{DD}				1	μΑ
	Ішнз	P121, P122, X1, X2, EXCLK	VI = VDD	In input port or external clock input			1	μΑ
				In resonator connection			10	μА
Input leakage current, low	ILIL1	P00, P01, P30 to P33, P40, and P51 to P56	Vı = Vss				-1	μА
	ILIL2	P20 to P23, P125, P137, RESET	Vı = Vss				-1	μΑ
	ILIL3	P121, P122, X1, X2, EXCLK	Vı = Vss	In input port or external clock input			-1	μА
				In resonator connection			-10	μΑ
On-chip pull-up resistance	Rυ	P00, P01, P30 to P33, P40, P51 to P56, P125	Vı = Vss, In	input port	10	20	100	kΩ

3.3.2 Supply current characteristics

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(1/3)

Parameter	Symbol				Conditions			MIN.	TYP.	MAX.	Unit
Supply current	I _{DD1}	Operating	Basic	HS (high-speed main)	fHOCO = 48 MHzNote 3	V _{DD} = 5.0 V			1.7		mA
Note 1		mode	operation	mode	f _{IH} = 24 MHz Note 3	V _{DD} = 3.0 V			1.7		
					fHOCO = 24 MHzNote 3	V _{DD} = 5.0 V			1.4		
					f _{IH} = 24 MHz Note 3	V _{DD} = 3.0 V			1.4		
			Normal	HS (high-speed main)	fHOCO = 48 MHzNote 3	V _{DD} = 5.0 V			3.5	7.3	mA
			operation	mode	f _{IH} = 24 MHz Note 3	V _{DD} = 3.0 V			3.5	7.3	
					fHOCO = 24 MHzNote 3	V _{DD} = 5.0 V			3.2	6.7	
					f _{IH} = 24 MHz Note 3	V _{DD} = 3.0 V			3.2	6.7	
					fHOCO = 16 MHzNote 3	V _{DD} = 5.0 V			2.4	4.9	
					f _{IH} = 16 MHz Note 3	V _{DD} = 3.0 V			2.4	4.9	
			Normal	HS (high-speed main)	f _{MX} = 20 MHz Note 2	V _{DD} = 5.0 V	Square wave input		2.7	5.7	mA
	operation mode		Resonator connection		2.8	5.8					
					V _{DD} = 3.0 V	Square wave input		2.7	5.7		
							Resonator connection		2.8	5.8	
					f _{MX} = 10 MHz Note 2	V _{DD} = 5.0 V	Square wave input		1.8	3.4	
							Resonator connection		1.9	3.5	
						V _{DD} = 3.0 V	Square wave input		1.8	3.4	
							Resonator connection		1.9	3.5	
			Normal operation	Subsystem clock operation	fil = 15 kHz, TA = - 40°C Note 4				1.8	5.9	μА
		fil = 15 kHz, Ta = +25°C Note 4				1.9	5.9				
			fil = 15 kHz, T _A = +85°C Note 4				2.3	8.7			
					f _{IL} = 15 kHz, T _A = +105°C Note 4				3.0	20.9	

- **Note 1.** Total current flowing into VDD and EVDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The following points apply in the HS (high-speed main) modes.
 - The currents in the "TYP." column do not include the operating currents of the peripheral modules.
 - The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the A/D converter, D/A converter, comparator, programmable gain amplifier, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.

In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules.

- **Note 2.** When the high-speed on-chip oscillator clock, middle-speed on-chip oscillator clock and low-speed on-chip oscillator clock are stopped.
- **Note 3.** When the high-speed system clock, middle-speed on-chip oscillator clock and low-speed on-chip oscillator clock are stopped.
- **Note 4.** When the high-speed system clock, high-speed on-chip oscillator clock and middle-speed on-chip oscillator clock are stopped.
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fil: High-speed on-chip oscillator clock frequency (24 MHz max.)
- Remark 3. fim: Middle-speed on-chip oscillator clock frequency (4 MHz max.)
- Remark 4. fil: Low-speed on-chip oscillator clock frequency
- Remark 5. fsub: Subsystem clock frequency (Low-speed on-chip oscillator clock frequency)
- **Remark 6.** Except subsystem clock operation, temperature condition of the TYP. value is $T_A = 25^{\circ}C$

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(2/3)

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply current	I _{DD2}	HALT	HS (high-speed main) mode	fHOCO = 48 MHz Note 3	$V_{DD} = 5.0 \text{ V}$			0.59	3.45	mA
Note 1	Note 2	mode		f _{IH} = 24 MHz Note 4	$V_{DD} = 3.0 \text{ V}$			0.59	3.45	
				fHOCO = 24 MHz Note 3	V _{DD} = 5.0 V			0.41	2.85	
				fin = 16 MHz Note 4	V _{DD} = 3.0 V			0.41	2.85	
				fHOCO = 16 MHz Note 3	V _{DD} = 5.0 V			0.39	2.08	
				f _{IH} = 16 MHz Note 4	V _{DD} = 3.0 V			0.39	2.08	
			HS (high-speed main) mode	f _{MX} = 20 MHz Note 3	V _{DD} = 5.0 V	Square wave input		0.20	2.45	mA
						Resonator connection		0.40	2.57	
					V _{DD} = 3.0 V	Square wave input		0.20	2.45	
						Resonator connection		0.40	2.57	
				f _{MX} = 10 MHz Note 3	V _{DD} = 5.0 V	Square wave input		0.15	1.28	
						Resonator connection		0.30	1.36	
					$V_{DD} = 3.0 \text{ V}$	Square wave input		0.15	1.28	
						Resonator connection		0.30	1.36	
			Subsystem clock operation	fil = 15 kHz, TA = -40°C	Note 5			0.48	1.22	μΑ
				fil = 15 kHz, TA = +25°C	Note 5			0.55	1.22	
				fil = 15 kHz, T _A = +85°C	Note 5			0.80	3.30	
				fil = 15 kHz, T _A = +105°	C Note 5			2.00	17.3	

- **Note 1.** Total current flowing into VDD and EVDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The following points apply in the HS (high-speed main) modes.
 - The currents in the "TYP." column do not include the operating currents of the peripheral modules.
 - The currents in the "MAX." column include the operating currents of the peripheral modules, except for those flowing into the A/D converter, D/A converter, comparator, programmable gain amplifier, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors, and those flowing while the data flash memory is being rewritten.

In the subsystem clock operation, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules.

- Note 2. When the HALT instruction is executed in the flash memory.
- **Note 3.** When the high-speed on-chip oscillator clock, middle-speed on-chip oscillator clock, and low-speed on-chip oscillator clock are stopped.
- Note 4. When the high-speed system clock, middle-speed on-chip oscillator clock and low-speed on-chip oscillator clock are stopped.
- **Note 5.** When the high-speed on-chip oscillator clock, middle-speed on-chip oscillator clock and high-speed system clock are stopped.
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fin: High-speed on-chip oscillator clock frequency (24 MHz max.)
- Remark 3. flm: Middle-speed on-chip oscillator clock frequency (4 MHz max.)
- Remark 4. fil: Low-speed on-chip oscillator clock frequency
- Remark 5. fsub: Subsystem clock frequency (Low-speed on-chip oscillator clock frequency)
- Remark 6. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(3/3)

Parameter	Symbol		MIN.	TYP.	MAX.	Unit	
Supply current	IDD3	STOP mode	TA = -40°C		0.19	0.51	μΑ
Note 1		Note 2	TA = +25°C		0.25	0.51	
			TA = +50°C		0.28	1.10	
			TA = +70°C		0.38	1.90	
		TA = +85°C		0.60	3.30		
			TA = +105°C		1.5	17.0	

- **Note 1.** Total current flowing into VDD and EVDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. In the STOP mode, the currents in both the "TYP." and "MAX." columns do not include the operating currents of the peripheral modules.
- **Note 2.** For the setting of the current values when operating the subsystem clock in STOP mode, see the current values when operating the subsystem clock in HALT mode.

Peripheral Functions (Common to all products)

(TA = -40 to +105°C, 2.4 V \leq EVDD $\leq~$ VDD $\leq~$ 5.5 V, Vss = 0 V)

Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscillator operating current	I _{FIL} Note 1				0.22		μА
12-bit interval timer operating current	I _{TMKA} Notes 1, 3, 4	fil = 15 kHz fmain stopped (per unit)			0.02		μА
8-bit interval timer operating current	Ітмт	fıL = 15 kHz	8-bit counter mode × 2-channel operation		0.04		μА
Notes 1, 9		fmain stopped (per unit)	16-bit counter mode operation		0.03		μА
Watchdog timer operating current	I _{WDT} Notes 1, 3, 5	fil = 15 kHz fmain stopped (per unit)			0.22		μА
A/D converter operating current	I _{ADC} Notes 1, 6	During maximum-speed	Normal mode, AV _{VREFP} = V _{DD} = 5.0 V		1.3	1.7	mA
		conversion	Low voltage mode, AV _{VREFP} = V _{DD} = 3.0 V		0.5	0.7	mA
Internal reference voltage (1.45 V) current Notes 1, 10	ladref				85.0		μА
Temperature sensor operating current	I _{TMPS} Note 1				85.0		μА
D/A converter operating current	I _{DAC} Note 1	Per channel				1.5	mA
PGA operating current	I _{PGA} Notes 1, 2				480	700	μА
Comparator operating current	I _{CMP} Note 8	V _{DD} = 5.0 V, Regulator output voltage	Comparator high-speed mode Window mode		12.5		μА
	V _{DD} = Regul	VDD = 5.0 V, Regulator output voltage = 1.8 V	Comparator low-speed mode Window mode		3.0		
			Comparator high-speed mode Standard mode		6.5		
			Comparator low-speed mode Standard mode		1.9		
			Comparator high-speed mode Window mode		8.0		
			Comparator low-speed mode Window mode		2.2		
			Comparator high-speed mode Standard mode		4.0		
			Comparator low-speed mode Standard mode		1.3		
LVD operating current	I _{LVD} Notes 1, 7				0.10		μА
Self-programming operating current	IFSP Notes 1, 12				2.0	12.20	mA
BGO current	IBGO Notes 1, 11				2.0	12.20	mA
SNOOZE operating current	ISNOZ Note 1	ADC operation	Mode transition Note 13		0.50	1.10	mA
		fih = 24 MHz, AVREFP = V _{DD} = 3.0 V	The A/D conversion operations are performed		1.20	2.04	mA
		Simplified SPI (CSI)/UART	operation fiн = 24 MHz		0.70	1.54	mA
	ISNOZM Note 1	ADC operation	Mode transition Note 13		0.05	0.13	mA
		fim = 4 MHz, AVREFP = V _{DD} = 3.0 V	The A/D conversion operations are performed		0.67	0.84	mA
		Simplified SPI (CSI) operate	tion, fIM = 4 MHz		0.06	0.15	mA

(Notes and Remarks are listed on the next page.)

- Note 1. Current flowing to VDD.
- Note 2. Operable range is 2.7 to 5.5 V.
- **Note 3.** When the high-speed on-chip oscillator clock, middle-speed on-chip oscillator clock, and high-speed system clock are stopped.
- Note 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.
- Note 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator).

 The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer is in operation.
- **Note 6.** Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
- Note 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.
- Note 8. Current flowing only to the comparator circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2, or IDD3 and ICMP when the comparator circuit is in operation.
- Note 9. Current flowing only to the 8-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 8-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.
- Note 10. Current consumed by generating the internal reference voltage (1.45 V).
- Note 11. Current flowing during programming of the data flash.
- **Note 12.** Current flowing during self-programming.
- Note 13. For transition time to the SNOOZE mode, see 24.3.3 SNOOZE mode in the RL78/G11 User's Manual.
- Remark 1. flL: Low-speed on-chip oscillator clock frequency
- Remark 2. fclk: CPU/peripheral hardware clock frequency
- **Remark 3.** Temperature condition of the TYP. value is $TA = 25^{\circ}C$

3.4 AC Characteristics

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Items	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Instruction cycle	Tcy	Main system clock	HS (high-speed main)	$2.7 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$	0.04167		1	μs
(minimum instruction		(fmain) operation	mode	2.4 V ≤ V _{DD} < 2.7 V	0.0625		1	μs
execution time)		Subsystem clock (fsub) operation	fiL	2.4 V ≤ VDD ≤ 5.5 V		66.7		μs
		In the self-	HS (high-speed main)	$2.7 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$	0.04167		1	μs
		programming mode	mode	2.4 V ≤ VDD < 2.7 V	0.0625		1	μs
External system	fex	2.7 V ≤ VDD ≤ 5.5 V	1		1		20	MHz
clock frequency		2.4 V ≤ V _{DD} < 2.7 \	/		1		16	MHz
External system	texH,	$2.7 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$	/		24			ns
clock input high-/low- level width	texL	2.4 V ≤ V _{DD} < 2.7 \	/		30			ns
TI00 to TI03 input high-/low-level width	tTIH, tTILNote 1				1/fмск + 10			ns
TO00 to TO03,	fто	TO00 to TO03,	HS (high-speed main)	$4.0 \text{ V} \le \text{EVDD} \le 5.5 \text{ V}$			12	MHz
TKBO0, and TKBO1		TKBO0, and	mode	2.7 V ≤ EV _{DD} < 4.0 V			8	
output frequency Note 2		TKBO1		2.4 V ≤ EV _{DD} < 2.7 V			4	
		(in the case of						
		output from port						
		pins other than						
		P20)						
		TKBO1	HS (high-speed main)	4.0 V ≤ V _{DD} ≤ 5.5 V			1.5	MHz
		(in the case of	mode	2.7 V ≤ V _{DD} < 4.0 V			1.2	
		output from P20)		2.4 V ≤ V _{DD} < 2.7 V			1	
PCLBUZ0, PCLBUZ1	fPCL	HS (high-speed ma	ain) mode	4.0 V ≤ EV _{DD} ≤ 5.5 V			16	MHz
output frequency				2.7 V ≤ EV _{DD} < 4.0 V			8	
				2.4 V ≤ EV _{DD} < 2.7 V			4	
Interrupt input high-	tinth,	INTP0 to INTP2, IN	ITP9	$2.4 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$	1			μs
/low-level width	tintl	INTP3 to INTP8, IN	ITP10, INTP11	2.4 V ≤ EVDD ≤ 5.5 V	1			
Key interrupt input low-level width	tkr	KR0 to KR7		$2.4 \text{ V} \le \text{EVdd} \le 5.5 \text{ V}$	250			ns
RESET low-level width	trsL				10			μs

Note 1. Following conditions must be satisfied on low level interface of EVDD < VDD.

 $2.4~V \le EV_{DD} \le 2.7~V$: MIN.125 ns

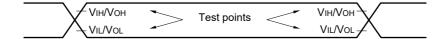
Note 2. When duty is 50%.

Remark fMCK: Timer array unit operation clock frequency

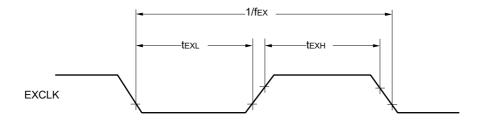
(Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0), n: Channel number (n = 0 to 3))

RENESAS

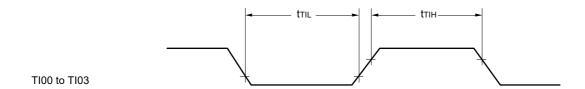
AC Timing Test Points

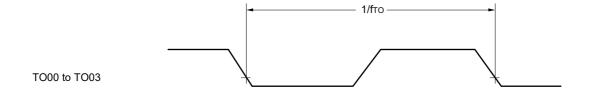


External System Clock Timing

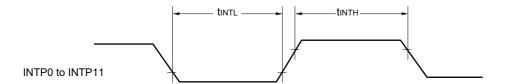


TI/TO Timing

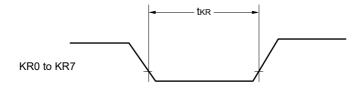




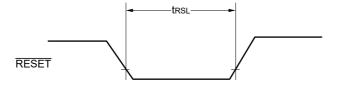
Interrupt Request Input Timing



Key Interrupt Input Timing

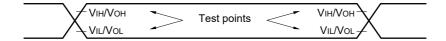


RESET Input Timing



3.5 Peripheral Functions Characteristics

AC Timing Test Points



3.5.1 Serial array unit

(1) during communication at same potential (UART mode) When P01, P30, P31 and P54 are used as TxDq pin

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	HS (high-sp	eed main) Mode	Unit
Farameter	Symbol	Conditions	MIN.	MAX.	Offic
Transfer rate		Theoretical value of the maximum transfer		fMCK/12Notes 1, 2	bps
		rate fmck = fclk = 24 MHz		2.0	Mbps

Note 1. Transfer rate in the SNOOZE mode is 4800 bps only.

Note 2. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode:

 $2.4 \text{ V} \leq \text{EV}_{DD} \leq 2.7 \text{ V: MAX. } 1.3 \text{ Mbps}$

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

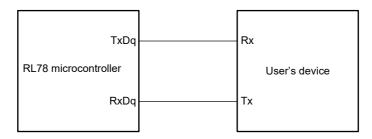
When P20 is used as TxD1 pin

(TA = -40 to +105°C, 2.4 V \leq EVDD = VDD \leq 5.5 V, Vss = 0 V)

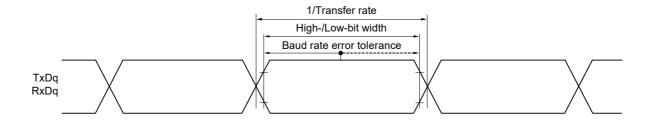
Parameter	Symbol	Conditions	HS (high-spee	Unit	
Farameter	Symbol	Conditions	MIN.	MAX.	Offic
Transfer rate		4.0 V ≤ VDD ≤ 5.5 V		fмск/16 ^{Note}	bps
		Theoretical value of the maximum transfer rate fMCK = fCLK = 24 MHz		1.5	Mbps
		2.7 V ≤ VDD ≤ 5.5 V		fмск/20 ^{Note}	bps
		Theoretical value of the maximum transfer rate fmck = fclk = 24 MHz		1.2	Mbps
		2.4 V ≤ VDD ≤ 5.5 V		fмск/16 ^{Note}	bps
		Theoretical value of the maximum transfer rate fmck = fclk = 16 MHz		1.0	Mbps

Note Transfer rate in the SNOOZE mode is 4800 bps only. When fHoco = 48 MHz, SNOOZE mode is not supported.

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remark 1. q: UART number (q = 0 and 1), g: PIM and POM number (g = 0, 2, 3 and 5)

Remark 2. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03)

(2) During communication at same potential (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

When P01, P32, P53, P54 and P56 are used as SOmn pins

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	_	Conditions		HS (high-speed main) Mode		
Falametei	Symbol		onditions	MIN.	MAX.	Unit	
SCKp cycle time	tkcy1	$t_{\text{KCY1}} \ge 4/f_{\text{CLK}} \qquad \frac{2.7 \text{ V} \le \text{EV}_{\text{DD}} \le 5.5 \text{ V}}{2.4 \text{ V} \le \text{EV}_{\text{DD}} \le 5.5 \text{ V}}$ $4.0 \text{ V} \le \text{EV}_{\text{DD}} \le 5.5 \text{ V}$		250		ns	
			$2.4 \text{ V} \leq \text{EV}_{DD} \leq 5.5 \text{ V}$	500 tkcy1/2 - 24	ns		
SCKp high-/low-level width	tkH1, tkL1	4.0 V ≤ EVDD ≤ 5.5 V		tkcy1/2 - 24		ns	
		2.7 V ≤ EV _{DD} ≤ 5.5 V		tkcy1/2 - 36		ns	
		2.4 V ≤ EV _{DD} ≤ 5	5.5 V	tkcy1/2 - 76		ns	
SIp setup time (to SCKp↑) Note 1	tsık1	4.0 V ≤ EV _{DD} ≤ 5	i.5 V	66		ns	
		2.7 V ≤ EV _{DD} ≤ 5	i.5 V			ns	
		2.4 V ≤ EV _{DD} ≤ 5	5.5 V	133		ns	
SIp hold time (from SCKp↑) Note 2	tksıı			38		ns	
Delay time from SCKp↓ to SOp output Note 3	tkso1	C = 30 pF Note 4			50	ns	

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **Note 4.** C is the load capacitance of the SCKp and SOp output lines.
- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- **Remark 1.** p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)
- Remark 2. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 n: Channel number (mn = 00 to 03))

When P20 is used as SO10 pin

(TA = -40 to +105°C, 2.4 V \leq EVDD = VDD \leq 5.5 V, VSS = 0 V)

Parameter	Symbol	Symbol Conditions		HS (high-spee	Unit	
Falaniciei	Symbol		oriditions	MIN.	MAX.	Offic
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$2.7 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$	1000		ns
			2.4 V ≤ V _{DD} ≤ 5.5 V	1200		ns
SCKp high-/low-level width	tkh1, tkL1			tkcy1/2 - 24		ns
				tkcy1/2 - 36		ns
		2.4 V ≤ V _{DD} ≤ 5.5	5 V			ns
SIp setup time (to SCKp↑) Note 1	tsıĸ1	2.7 V ≤ V _{DD} ≤ 5.5	5 V	66		ns
		2.4 V ≤ V _{DD} ≤ 5.5	5 V	133		ns
SIp hold time (from SCKp↑) Note 2	tksi1			38		ns
Delay time from SCKp↓ to SOp output Note 3	tkso1	C = 30 pF Note 4			180	ns

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. C is the load capacitance of the SCKp and SOp output lines.
- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- Remark 1. p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)
- Remark 2. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 n: Channel number (mn = 00 to 03))

(3) During communication at same potential (Simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)

When P01, P32, P53, P54 and P56 are used as SOmn pins

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(1/2)

Development	Oh - I	0	!!!	HS (high-speed	main) Mode	11
Parameter	Symbol	Cond	itions	MIN.	MAX.	Unit
SCKp cycle time Note 4	tkcy2	4.0 V ≤ EV _{DD} ≤ 5.5 V	fмск > 20 MHz	16/ƒмск		ns
			fмcк ≤ 20 MHz	12/fмск		ns
		2.7 V ≤ EV _{DD} < 4.0 V	fмск > 16 MHz	16/fмск		ns
			fмск ≤ 16 MHz	12/fмск		ns
		2.4 V ≤ EVDD < 2.7 V		12/fмск and 1000		ns
SCKp high-/low-level width	tkH2, tkL2	4.0 V ≤ EV _{DD} ≤ 5.5 V		tксү2/2 - 14		ns
	tkH2, tkL2	2.7 V ≤ EVDD < 4.0 V		tксү2/2 - 16		ns
		2.4 V ≤ EVDD < 2.7 V		tkcy2/2 - 36		ns
SIp setup time (to SCKp↑) Note 1	tsık2	$2.7 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V}$		1/fмск + 40		ns
		2.4 V ≤ EVDD < 2.7 V		1/fмск + 60		ns
SIp hold time (from SCKp↑) Note 1	tksi2			1/fмск + 62		ns
Delay time from SCKp↓ to SOp output Note 2	tkso2	C = 30 pF Note 3	$2.7 \text{ V} \leq \text{EV}_{DD} \leq 5.5 \text{ V}$		2/fмск + 66	ns
			2.4 V ≤ EVDD < 2.7 V		2/fмск + 113	ns

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" and the SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. C is the load capacitance of the SOp output lines.
- **Note 4.** The maximum transfer rate when using the SNOOZE mode is 1 Mbps.
- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- Remark 1. p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)
- Remark 2. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 n: Channel number (mn = 00 to 03))

(Ta = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(2/2)

Parameter	Symbol		Conditions	HS (high-spee	ed main) Mode	Unit
Farameter	Symbol		Conditions	MIN.	MAX.	Offic
SSI00 setup time	tssıĸ	DAPmn = 0	$2.7 \text{ V} \leq \text{V}_{DD} \leq 3.6 \text{ V}$	240		ns
			2.4 V ≤ V _{DD} < 2.7 V	400		ns
		DAPmn = 1	$2.7 \text{ V} \le \text{Vdd} \le 3.6 \text{ V}$	1/fмск + 240		ns
			2.4 V ≤ V _{DD} < 2.7 V	1/fмск + 400		ns
SSI00 hold time	tkssi	DAPmn = 0	$2.7 \text{ V} \leq \text{V}_{DD} \leq 3.6 \text{ V}$	1/fмск + 240		ns
			2.4 V ≤ V _{DD} < 2.7 V	1/fмск + 400		ns
		DAPmn = 1	$2.7 \text{ V} \leq \text{V}_{DD} \leq 3.6 \text{ V}$	240		ns
			2.4 V ≤ V _{DD} < 2.7 V	400		ns

Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remark p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5, 12)

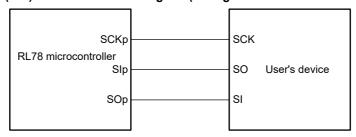
When P20 is used as SO10 pin

(TA = -40 to +105°C, 2.4 V \leq EVDD = VDD \leq 5.5 V, Vss = 0 V)

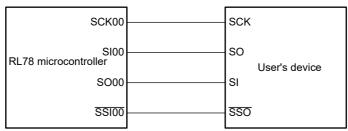
Parameter	Cumphal	Cond	Conditions		HS (high-speed main) Mode		
Parameter	Symbol	Cond	itions	MIN.	MAX.	Unit	
SCKp cycle time Note 4	tkcy2	4.0 V ≤ V _{DD} ≤ 5.5 V	fмск > 20 MHz	20/fмск		ns	
			fмcκ ≤ 20 MHz	18/fмск		ns	
		2.7 V ≤ V _{DD} < 4.0 V	fмск > 16 MHz	20/fMCK and 1000		ns	
			fмcκ ≤ 16 MHz	18/fмск		ns	
		$2.4 \text{ V} \leq \text{Vdd} < 2.7 \text{ V}$		18/fмск and 1200		ns	
SCKp high-/low-level width	tkH2, tkL2	4.0 V ≤ VDD ≤ 5.5 V		tkcy2/2 - 14		ns	
	tkH2, tkL2	2.7 V ≤ V _{DD} < 4.0 V		tkcy2/2 - 16		ns	
		$2.4~\textrm{V} \leq \textrm{V}_\textrm{DD} < 2.7~\textrm{V}$	$2.4 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V}$			ns	
SIp setup time (to SCKp↑) Note 1	tsik2	2.7 V ≤ V _{DD} ≤ 5.5 V		1/fмск + 40		ns	
		$2.4~V \leq V_{DD} < 2.7~V$		1/fмск + 60		ns	
SIp hold time (from SCKp↑) Note 1	tksi2			1/fмск + 62		ns	
Delay time from SCKp↓ to SOp output Note 2	tkso2	C = 30 pF Note 3	$2.7~V \leq V_{DD} \leq 5.5~V$		2/fмск + 190	ns	
			$2.4~\textrm{V} \leq \textrm{V}_\textrm{DD} < 2.7~\textrm{V}$		2/fmck + 250	ns	

- Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" and the SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 3. C is the load capacitance of the SOp output lines.
- **Note 4.** The maximum transfer rate when using the SNOOZE mode is 1 Mbps.
- Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).
- Remark 1. p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)
- Remark 2. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 n: Channel number (mn = 00 to 03))

Simplified SPI (CSI) mode connection diagram (during communication at same potential)

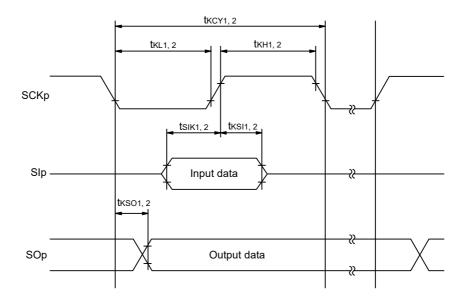


Simplified SPI (CSI) mode connection diagram (during communication at same potential) (Slave Transmission of slave select input function (CSI00))

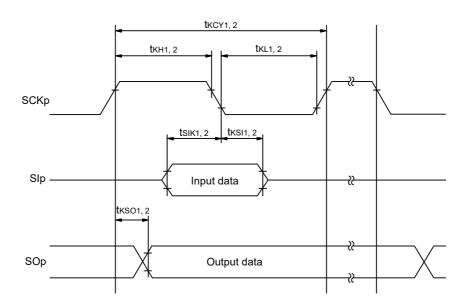


Remark p: CSI number (p = 00, 01, 10 and 11)

Simplified SPI (CSI) mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (during communication at same potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark 1. p: CSI number (p = 00, 01, 10 and 11)

Remark 2. m: Unit number, n: Channel number (mn = 00 to 03)

(4) During communication at same potential (simplified I²C mode)

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

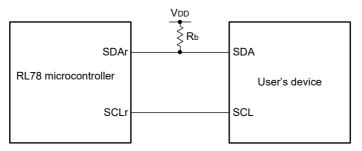
D	Courselle al	O = = 414 i = = =	HS (high-speed	main) Mode	1.1:4
Parameter	Symbol	Conditions	MIN.	MAX.	Unit
SCLr clock frequency	fscL	$2.7 \text{ V} \leq \text{EVdd} \leq 5.5 \text{ V},$ $C_b = 50 \text{ pF, } R_b = 2.7 \text{ k}\Omega$		400 Note 1	kHz
		$2.4~V \leq \text{EVdd} \leq 5.5~V,$ $C_b = 100~\text{pF},~R_b = 3~\text{k}\Omega$		100 Note 1	kHz
Hold time when SCLr = "L"	tLOW	$2.7 \text{ V} \leq \text{EVdd} \leq 5.5 \text{ V},$ $C_b = 50 \text{ pF, } R_b = 2.7 \text{ k}\Omega$	1200		ns
		$2.4~V \leq \text{EVdd} \leq 5.5~V,$ $C_b = 100~\text{pF},~R_b = 3~\text{k}\Omega$	4600		ns
Hold time when SCLr = "H"	thigh	$2.7 \text{ V} \leq \text{EV}_{DD} \leq 5.5 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	1200		ns
		$2.4~V \leq \text{EVdd} \leq 5.5~V,$ $C_b = 100~\text{pF},~R_b = 3~\text{k}\Omega$	4600		ns
Data setup time (reception)	tsu: DAT	$2.7 \text{ V} \leq \text{EVdd} \leq 5.5 \text{ V},$ $C_b = 50 \text{ pF, } R_b = 2.7 \text{ k}\Omega$	1/fмск + 220 Note 2		ns
		$2.4~V \leq \text{EVdd} \leq 5.5~V,$ $C_b = 100~\text{pF},~R_b = 3~\text{k}\Omega$	1/fмск + 580 Note 2		ns
Data hold time (transmission)	thd: dat	$2.7 \text{ V} \leq \text{EV}_{DD} \leq 5.5 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	0	770	ns
		$2.4~V \leq \text{EVdd} \leq 5.5~V,$ $C_b = 100~\text{pF},~R_b = 3~\text{k}\Omega$	0	1420	ns

Note 1. The value must be equal to or less than fmck/4.

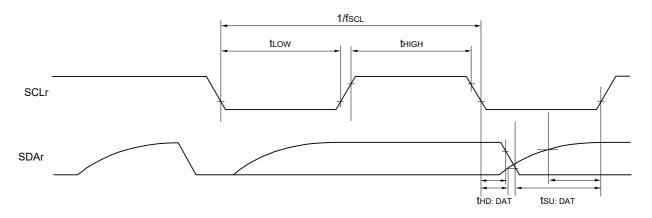
Caution Select the normal input buffer and the N-ch open drain output (EVDD tolerance) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

Note 2. Set the fмcκ value to keep the hold time of SCLr = "L" and SCLr = "H".

Simplified I²C mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



 $\textbf{Remark 1.} \ \, \mathsf{Rb}[\Omega] : \mathsf{Communication line (SDAr) pull-up \ resistance}, \ \mathsf{Cb}[\mathsf{F}] : \mathsf{Communication line (SDAr, SCLr) load \ capacitance}$

Remark 2. r: IIC number (r = 00, 01, 10 and 11), g: PIM number (g = 0, 3 and 5), h: POM number (h = 0, 3 and 5)

Remark 3. fmck: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0),
n: Channel number (n = 0 to 3), mn = 00 to 03)

(5) Communication at different potential (1.8 V, 2.5 V, 3.0 V) (UART mode) (dedicated baud rate generator output)

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(1/2)

Parameter	Symbol		Conditions	HS (high-	speed main) Mode	Unit
Farameter	Syllibol		Conditions	MIN.	MAX.	Offic
Transfer rate		Reception	$4.0 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V},$ $2.3 \text{ V} \le \text{V}_{b} \le 4.0 \text{ V}$		fмск/12 Note 1	bps
			Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		2.0	Mbps
			$2.7 \text{ V} \le \text{EV}_{DD} < 4.0 \text{ V},$ $2.3 \text{ V} \le V_b \le 2.7 \text{ V}$		fmck/12 Note 1	bps
			Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		2.0	Mbps
			$2.4 \text{ V} \le \text{EV}_{DD} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{b} \le 2.0 \text{ V}$		fMCK/12 Notes 1, 2	bps
			Theoretical value of the maximum transfer rate fMCK = fCLK Note 3		1.3	Mbps

- **Note 1.** Transfer rate in the SNOOZE mode is 4,800 bps only.
- **Note 2.** Use it with $EVDD \ge Vb$.
- Note 3. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: 24 MHz (2.7 V \leq VDD \leq 5.5 V)

16 MHz (2.4 V \leq VDD \leq 5.5 V)

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (EVDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

- Remark 1. Vb[V]: Communication line voltage
- Remark 2. q: UART number (q = 0 and 1), g: PIM and POM numbers (g = 0, 2, 3, 5, 12)
- Remark 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03))

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(2/2)

Parameter	Symbol	Conditions		HS (high-	Unit	
raidificter	Cymbol		Conditions	MIN.	MAX.	Offic
Transfer rate		Transmission	$4.0 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{b} \le 4.0 \text{ V}$		Note 1	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 1.4 k Ω , V_b = 2.7 V		2.6 ^{Note 2}	Mbps
			$2.7 \text{ V} \le \text{EV}_{DD} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V}$		Note 3	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 2.7 k Ω , V_b = 2.3 V		1.2 Note 4	Mbps
			$2.4 \text{ V} \le \text{EV}_{DD} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{b} \le 2.0 \text{ V}$		Notes 5, 6	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 5.5 k Ω , V_b = 1.6 V		0.43 Note 7	Mbps

Note 1. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate. Expression for calculating the transfer rate when 4.0 V \leq EV_{DD} \leq 5.5 V and 2.7 V \leq V_b \leq 4.0 V

Maximum transfer rate =
$$\frac{1}{ \left\{ -C_b \times R_b \times ln \ (1 - \frac{2.2}{V_b} \) \right\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- Note 2. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.
- Note 3. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate. Expression for calculating the transfer rate when 2.7 V \leq EVDD \leq 4.0 V and 2.3 V \leq Vb \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{\left\{-C_b \times R_b \times \ln \left(1 - \frac{2.0}{V_b}\right)\right\} \times 3}$$
 [bps]

$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-\text{Cb} \times \text{Rb} \times \text{In } (1 - \frac{2.0}{\text{Vb}})\}}{\text{Transfer rate}} \times 100 \, [\%]$$
Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate}} - \{-\text{Cb} \times \text{Rb} \times \text{In } (1 - \frac{2.0}{\text{Vb}})\}}{\text{Transfer rate}} \times 100 \, [\%]$$

- Note 4. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.
- Note 5. Use it with EVDD $\geq V_b$.

^{*} This value is the theoretical value of the relative difference between the transmission and reception sides

^{*} This value is the theoretical value of the relative difference between the transmission and reception sides

Note 6. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate. Expression for calculating the transfer rate when $2.4 \text{ V} \le \text{EV}_{DD} < 3.3 \text{ V}$ and $1.6 \text{ V} \le \text{V}_{b} \le 2.0 \text{ V}$

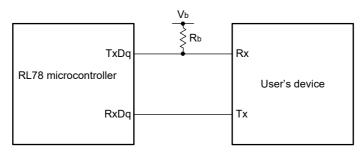
Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{1.5}{V_b})\}}{\times 100 \, [\%]}$$

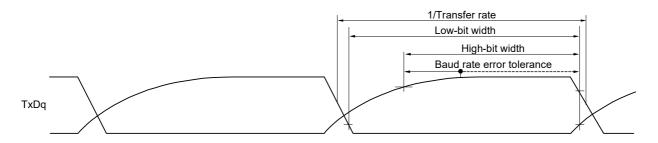
$$(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}$$

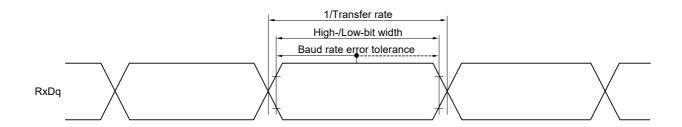
- * This value is the theoretical value of the relative difference between the transmission and reception sides
- **Note 7.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 6 above to calculate the maximum transfer rate under conditions of the customer.
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (EVDD tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)





- **Remark 1.** Rb[Ω]: Communication line (TxDq) pull-up resistance, Cb[F]: Communication line (TxDq) load capacitance, Vb[V]: Communication line voltage
- Remark 2. q: UART number (q = 0 and 1), g: PIM and POM number (g = 0, 2, 3, 5 and 12)
- Remark 3. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 n: Channel number (mn = 00 to 03))

(6) Communication at different potential (1.8 V, 2.5 V, 3.0 V) (Simplified SPI (CSI) mode) (master mode, SCKp... internal clock output)

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(1/2)

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
Parameter	Symbol		Conditions	MIN.	MAX.	Onit
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$ 4.0 \text{ V} \leq \text{EV}_{\text{DD}} \leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 1.4 \text{ k}\Omega $	600		ns
			$ 2.7 \text{ V} \leq \text{EV}_{DD} < 4.0 \text{ V}, 2.3 \text{ V} \leq \text{V}_b \leq 2.7 \text{ V}, \\ C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega $	1000		ns
			$ 2.4 \text{ V} \leq \text{EV}_{DD} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_b \leq 2.0 \text{ V}, \\ C_b = 30 \text{ pF}, \ R_b = 5.5 \text{ k}\Omega $	2300		ns
SCKp high-level width	tкн1	$4.0~V \leq EV_{DD} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ $C_b = 30~pF,~R_b = 1.4~k\Omega$		tксү1/2 - 150		ns
		$2.7~V \leq EV_{DD} < 4.0~V,~2.3~V \leq V_b \leq 2.7~V,$ $C_b = 30~pF,~R_b = 2.7~k\Omega$		tксү1/2 - 340		ns
		$2.4 \text{ V} \leq \text{EV}_{DD} < 3.3 \text{ V}, 1.6 \text{ V} \leq \text{V}_{b} \leq 2.0 \text{ V},$ $C_{b} = 30 \text{ pF}, R_{b} = 5.5 \text{ k}\Omega$		tксү1/2 - 916		ns
SCKp low-level width	tkl1	4.0 V ≤ EV _{DD} C _b = 30 pF, R _b	$\leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{Vb} \leq 4.0 \text{ V},$ $_{0} = 1.4 \text{ k}\Omega$	tkcy1/2 - 24		ns
		$2.7 \text{ V} \leq \text{EV}_{DD} < 4.0 \text{ V}, 2.3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V},$ $C_{b} = 30 \text{ pF}, R_{b} = 2.7 \text{ k}\Omega$		tkcy1/2 - 36		ns
			$.4~V \le EV_{DD} < 3.3~V,~1.6~V \le V_{b} \le 2.0~V,$ $C_{b} = 30~pF,~R_{b} = 5.5~k\Omega$			ns

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (EVDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

(2/2)

Parameter	Symbol	Conditions	HS (high-s	Unit	
			MIN.	MAX.	
SIp setup time (to SCKp↑) Note 1	tsıĸ1	$ 4.0 \text{ V} \leq \text{EVdd} \leq 5.5 \text{ V}, \ 2.7 \text{ V} \leq \text{Vb} \leq 4.0 \text{ V}, $ $ C_b = 30 \text{ pF}, \ R_b = 1.4 \text{ k}\Omega $	162		ns
		$ 2.7 \; \text{V} \leq \text{EV}_{\text{DD}} < 4.0 \; \text{V}, 2.3 \; \text{V} \leq \text{V}_{\text{b}} \leq 2.7 \; \text{V}, \\ C_{\text{b}} = 30 \; \text{pF}, \; R_{\text{b}} = 2.7 \; \text{k}\Omega $	354		ns
		$ 2.4 \text{ V} \leq \text{EV}_{DD} < 3.3 \text{ V}, 1.6 \text{ V} \leq \text{V}_{b} \leq 2.0 \text{ V} \stackrel{Note 3}{,} $ $ C_{b} = 30 \text{ pF}, R_{b} = 5.5 \text{ k}\Omega $	958		ns
SIp hold time (from SCKp↑) Note 1	tksii	$ 4.0 \; \text{V} \leq \text{EV}_{\text{DD}} \leq 5.5 \; \text{V}, 2.7 \; \text{V} \leq \text{V}_{\text{b}} \leq 4.0 \; \text{V}, \\ C_{\text{b}} = 30 \; \text{pF}, R_{\text{b}} = 1.4 \; \text{k}\Omega $	38		ns
		$2.7 \text{ V} \leq \text{EV}_{DD} < 4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V},$ $C_{b} = 30 \text{ pF}, \ R_{b} = 2.7 \text{ k}\Omega$			ns
		$ 2.4 \text{ V} \leq \text{EV}_{DD} < 3.3 \text{ V}, 1.6 \text{ V} \leq \text{V}_{b} \leq 2.0 \text{ V} \text{ Note 3}, \\ C_{b} = 30 \text{ pF}, R_{b} = 5.5 \text{ k}\Omega $			ns
Delay time from SCKp↓ to SOp output Note 1	tkso1	$ 4.0 \; V \leq EV_{DD} \leq 5.5 \; V, 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 30 \; pF, R_b = 1.4 \; k\Omega $		200	ns
		$ 2.7 \; \text{V} \leq \text{EV}_{\text{DD}} < 4.0 \; \text{V}, 2.3 \; \text{V} \leq \text{V}_{\text{b}} \leq 2.7 \; \text{V}, \\ C_{\text{b}} = 30 \; \text{pF}, R_{\text{b}} = 2.7 \; \text{k}\Omega $		390	ns
		$2.4~V \leq EV_{DD} < 3.3~V, \ 1.6~V \leq V_b \leq 2.0~V~^{Note~3},$ $C_b = 30~pF, \ R_b = 5.5~k\Omega$		966	ns
SIp setup time (to SCKp↓) Note 2	tsıĸ1	$ 4.0 \; V \leq EV_{DD} \leq 5.5 \; V, 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 30 \; pF, R_b = 1.4 \; k\Omega $	88		ns
		$2.7 \text{ V} \leq \text{EV}_{DD} < 4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V}, \\ C_{b} = 30 \text{ pF}, \ R_{b} = 2.7 \text{ k}\Omega$			ns
		$ 2.4 \text{ V} \leq \text{EV}_{DD} < 3.3 \text{ V}, 1.6 \text{ V} \leq \text{V}_{b} \leq 2.0 \text{ V} \text{ Note 3}, \\ C_{b} = 30 \text{ pF}, R_{b} = 5.5 \text{ k}\Omega $	220		ns
SIp hold time (from SCKp↓) Note 2	tksii	$ 4.0 \; V \leq EV_{DD} \leq 5.5 \; V, 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b = 30 \; pF, R_b = 1.4 \; k\Omega $	38		ns
		$ 2.7 \; \text{V} \leq \text{EV}_{\text{DD}} < 4.0 \; \text{V}, 2.3 \; \text{V} \leq \text{V}_{\text{b}} \leq 2.7 \; \text{V}, \\ C_{\text{b}} = 30 \; \text{pF}, R_{\text{b}} = 2.7 \; \text{k}\Omega $			
		$2.4~V \leq EV_{DD} < 3.3~V,~1.6~V \leq V_b \leq 2.0~V~^{Note~3},$ $C_b = 30~pF,~R_b = 5.5~k\Omega$			ns
Delay time from SCKp↑ to SOp output Note 2	tkso1	$ 4.0 \; \text{V} \leq \text{EV}_{\text{DD}} \leq 5.5 \; \text{V}, 2.7 \; \text{V} \leq \text{V}_{\text{b}} \leq 4.0 \; \text{V}, \\ C_{\text{b}} = 30 \; \text{pF}, R_{\text{b}} = 1.4 \; \text{k}\Omega $		50	ns
		$2.7 \; \text{V} \leq \text{EV}_{\text{DD}} < 4.0 \; \text{V}, 2.3 \; \text{V} \leq \text{V}_{\text{b}} \leq 2.7 \; \text{V},$ $C_{\text{b}} = 30 \; \text{pF}, R_{\text{b}} = 2.7 \; \text{k}\Omega$			
		$2.4~V \leq EV_{DD} < 3.3~V,~1.6~V \leq V_b \leq 2.0~V~Note~3,$ $C_b = 30~pF,~R_b = 5.5~k\Omega$			ns

Note 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (EVDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

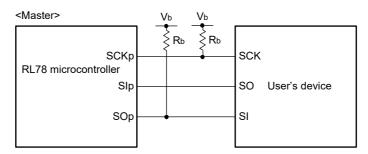
(Remarks are listed on the next page.)



Note 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

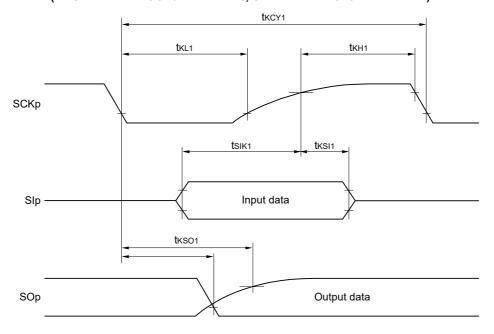
Note 3. Use it with $EVDD \ge Vb$.

Simplified SPI (CSI) mode connection diagram (during communication at different potential)

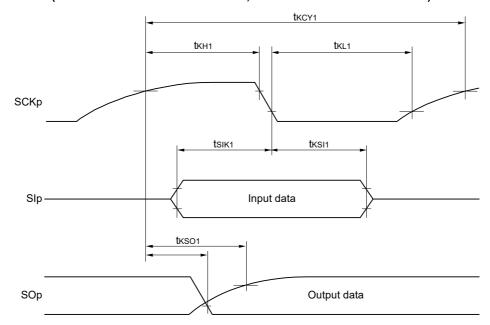


- Remark 1. $Rb[\Omega]$: Communication line (SCKp, SOp) pull-up resistance, Cb[F]: Communication line (SCKp, SOp) load capacitance, Vb[V]: Communication line voltage
- Remark 2. p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)
- Remark 3. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 n: Channel number (mn = 00 to 03))

Simplified SPI (CSI) mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)

(7) Communication at different potential (1.8 V, 2.5 V, 3.0 V) (Simplified SPI (CSI) mode) (slave mode, SCKp... external clock input)

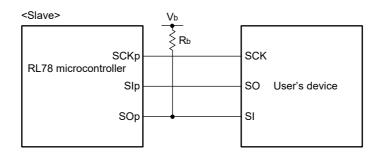
(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, VSS = 0 V)

		Conditions		HS (high-spe	ed main) Mode	
Parameter	Symbol	Con	aitions	MIN.	MAX.	Unit
SCKp cycle time Note 1	tkcy2	$4.0 \text{ V} \leq \text{EV}_{DD} \leq 5.5 \text{ V},$	20 MHz < fмcк ≤ 24 MHz	24/fмск		ns
		$2.7~V \leq V_b \leq 4.0~V$	8 MHz < fмcк ≤ 20 MHz	20/fмск		ns
			4 MHz < fмcк ≤ 8 MHz	16/fмск		ns
			fмcк ≤ 4 MHz	12/fмск		ns
		$2.7 \text{ V} \le \text{EV}_{DD} < 4.0 \text{ V},$	20 MHz < fмcк ≤ 24 MHz	32/fмск		ns
		2.3 V ≤ V _b ≤ 2.7 V	16 MHz < fмcк ≤ 20 MHz	28/fмск		ns
			8 MHz < fмcк ≤ 16 MHz	24/fмск		ns
			4 MHz < fмcк ≤ 8 MHz	16/fмск		ns
			fмcк ≤ 4 MHz	12/fмск		ns
		2.4 V ≤ EV _{DD} < 3.3 V,	20 MHz < fмcк ≤ 24 MHz	72/fмск		ns
		$1.6~V \leq V_b \leq 2.0~V~^{Note~2}$	16 MHz < fмcк ≤ 20 MHz	64/fмск		ns
			8 MHz < fмcк ≤ 16 MHz	52/fмск		ns
			4 MHz < fмcк ≤ 8 MHz	32/fмск		ns
			fмcк ≤ 4 MHz	20/fмск		ns
SCKp high-/low-level width	tkH2, tkL2	$4.0 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{b} \le 4.0 \text{ V}$		tkcy2/2 - 24		ns
		$2.7 \text{ V} \le \text{EV}_{DD} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V}$		tkcy2/2 - 36		ns
		2.4 V ≤ EV _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V Note 2		tkcy2/2 - 100		ns
SIp setup time (to SCKp↑) Note 3	tsık2	$2.7 \text{ V} \le \text{EVdd} \le 5.5 \text{ V}, 2.3$	$1.7 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V}, 2.3 \text{ V} \le \text{V}_{b} \le 4.0 \text{ V}$			ns
		2.4 V ≤ EV _{DD} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V Note 2		1/fмск + 60		ns
SIp hold time (from SCKp↑) Note 4	tksi2			1/fмск + 62		ns
Delay time from SCKp↓ to SOp output Note 5	tkso2	$4.0 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V}, 2.7$ C _b = 30 pF, R _b = 1.4 kΩ	$V \le V_b \le 4.0 V$		2/fмск + 240	ns
		$2.7 \text{ V} \le \text{EV}_{DD} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V}$ $C_{b} = 30 \text{ pF}, R_{b} = 2.7 \text{ k}\Omega$			2/fмcк + 428	ns
		$2.4 \text{ V} \le \text{EV}_{DD} < 3.3 \text{ V}, 1.6$ $C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$	$V \leq V_b \leq 2.0 \ V \ \text{Note 2}$		2/fмск + 1146	ns

(Notes, Caution and Remarks are listed on the next page.)

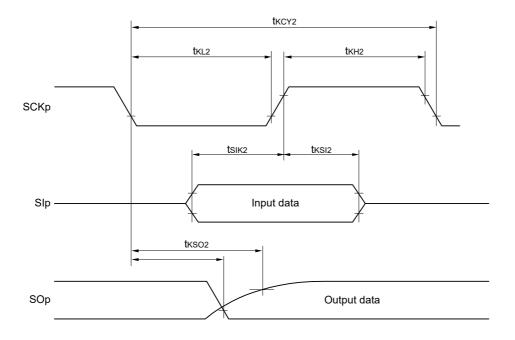
- Note 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
- Note 2. Use it with $EVDD \ge Vb$.
- Note 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Note 5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Caution Select the TTL input buffer for the SIp pin and SCKp pin and the N-ch open drain output (EVDD tolerance) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

Simplified SPI (CSI) mode connection diagram (during communication at different potential)

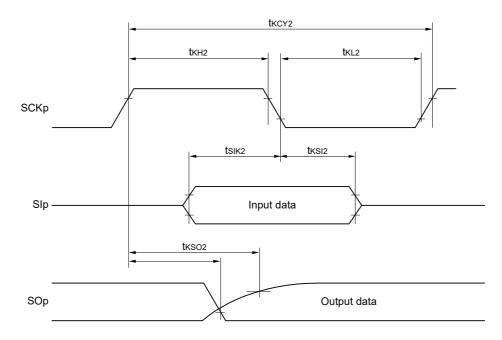


- **Remark 1.** Rb[Ω]: Communication line (SOp) pull-up resistance, Cb[F]: Communication line (SOp) load capacitance, Vb[V]: Communication line voltage
- Remark 2. p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)
- Remark 3. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 n: Channel number (mn = 00 to 03))

Simplified SPI (CSI) mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



Simplified SPI (CSI) mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark p: CSI number (p = 00, 01, 10 and 11), m: Unit number (m = 0), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 2, 3 to 5 and 12)

(8) Communication at different potential (1.8 V, 2.5 V, 3.0 V) (simplified I²C mode)

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

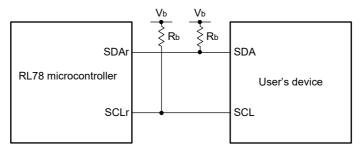
Parameter	Symbol	Conditions	HS (high-speed	main) Mode	Unit	
ı ararlıcıcı	Cyllibol	Conditions	MIN.	MAX.	Offic	
SCLr clock frequency	fscL	$ 4.0 \text{ V} \leq \text{EV}_{DD} \leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_b \leq 4.0 \text{ V}, \\ C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega $		400 Note 1	kHz	
		$ 2.7 \; \text{V} \leq \text{EV}_{DD} < 4.0 \; \text{V}, \; 2.3 \; \text{V} \leq \text{V}_b \leq 2.7 \; \text{V}, \\ C_b = 50 \; \text{pF}, \; R_b = 2.7 \; \text{k}\Omega $		400 Note 1	kHz	
		$ \begin{aligned} &4.0 \text{ V} \leq \text{EV}_{DD} \leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_b \leq 4.0 \text{ V}, \\ &C_b = 100 \text{ pF}, R_b = 2.8 \text{ k}\Omega \end{aligned} $		100 Note 1	kHz	
		$2.7 \text{ V} \leq \text{EV}_{DD} < 4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_b \leq 2.7 \text{ V},$ $C_b = 100 \text{ pF}, \ R_b = 2.7 \text{ k}\Omega$		100 Note 1	kHz	
		$ 2.4 \text{ V} \leq \text{EV}_{DD} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_b \leq 2.0 \text{ V} \text{ Note 2}, $ $ C_b = 100 \text{ pF}, \ R_b = 5.5 \text{ k} \Omega $		100 Note 1	kHz	
Hold time when SCLr = "L"	tLOW	$4.0~\text{V} \leq \text{EV}_{DD} \leq 5.5~\text{V},~2.7~\text{V} \leq \text{V}_{b} \leq 4.0~\text{V},$ $C_{b} = 50~\text{pF},~R_{b} = 2.7~\text{k}\Omega$	1200		ns	
		$2.7 \text{ V} \leq \text{EV}_{DD} < 4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V}, \\ C_{b} = 50 \text{ pF}, \ R_{b} = 2.7 \text{ k}\Omega$	1200		ns	
		$4.0~V \leq EV_{DD} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ $C_b = 100~pF,~R_b = 2.8~k\Omega$	4600		ns	
		$2.7 \text{ V} \leq \text{EV}_{DD} < 4.0 \text{ V}, 2.3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V},$ $C_{b} = 100 \text{ pF, } R_{b} = 2.7 \text{ k}\Omega$	4600		ns	
		$2.4 \text{ V} \leq \text{EV}_{DD} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_{b} \leq 2.0 \text{ V} \text{ Note 2}, \\ C_{b} = 100 \text{ pF}, \ R_{b} = 5.5 \text{ k}\Omega$	4650		ns	
Hold time when SCLr = "H"	thigh	$4.0~V \leq EV_{DD} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ $C_b = 50~pF,~R_b = 2.7~k\Omega$	620		ns	
		$2.7 \text{ V} \leq \text{EV}_{DD} < 4.0 \text{ V}, 2.3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V}, \\ C_{b} = 50 \text{ pF}, R_{b} = 2.7 \text{ k}\Omega$	500		ns	
		$ 4.0 \text{ V} \leq \text{EV}_{DD} \leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{b} \leq 4.0 \text{ V}, $ $C_{b} = 100 \text{ pF}, R_{b} = 2.8 \text{ k}\Omega $	2700		ns	
		$2.7 \text{ V} \leq \text{EV}_{DD} < 4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V},$ $C_{b} = 100 \text{ pF}, \ R_{b} = 2.7 \text{ k}\Omega$	2400		ns	
		$2.4 \text{ V} \leq \text{EV}_{DD} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_{b} \leq 2.0 \text{ V} \text{ Note 2}, \\ C_{b} = 100 \text{ pF}, \ R_{b} = 5.5 \text{ k}\Omega$	1830		ns	
Data setup time (reception)	tsu:dat	$4.0~V \leq \text{EV}_{\text{DD}} \leq 5.5~\text{V},~2.7~\text{V} \leq \text{V}_{\text{b}} \leq 4.0~\text{V},$ $C_{\text{b}} = 50~\text{pF},~R_{\text{b}} = 2.7~\text{k}\Omega$	1/f _{MCK} + 340 Note 3		ns	
		$2.7 \text{ V} \leq \text{EV}_{\text{DD}} < 4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, \ R_{\text{b}} = 2.7 \text{ k}\Omega$	1/f _{MCK} + 340 Note 3		ns	
		$ 4.0 \text{ V} \leq \text{EV}_{DD} \leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{b} \leq 4.0 \text{ V}, $ $C_{b} = 100 \text{ pF, } R_{b} = 2.8 \text{ k}\Omega $	1/f _{MCK} + 760 Note 3		ns	
		$2.7 \text{ V} \leq \text{EV}_{DD} < 4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V},$ $C_{b} = 100 \text{ pF}, \ R_{b} = 2.7 \text{ k}\Omega$	1/f _{MCK} + 760 Note 3		ns	
		$2.4 \text{ V} \leq \text{EV}_{DD} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_{b} \leq 2.0 \text{ V} \text{ Note 2}, \\ C_{b} = 100 \text{ pF}, \ R_{b} = 5.5 \text{ k}\Omega$	1/f _{MCK} + 570 Note 3		ns	
Data hold time (transmission)	thd:dat	$4.0~V \leq \text{EV}_{\text{DD}} \leq 5.5~\text{V},~2.7~\text{V} \leq \text{V}_{\text{b}} \leq 4.0~\text{V},$ $C_{\text{b}} = 50~\text{pF},~R_{\text{b}} = 2.7~\text{k}\Omega$	0	770	ns	
		$2.7 \text{ V} \leq \text{EV}_{\text{DD}} < 4.0 \text{ V}, \ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, \ R_{\text{b}} = 2.7 \text{ k}\Omega$	0	770	ns	
		$4.0~V \leq EV_{DD} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ $C_b = 100~pF,~R_b = 2.8~k\Omega$	0	1420	ns	
		$2.7 \text{ V} \leq \text{EV}_{DD} < 4.0 \text{ V}, 2.3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V},$ $C_{b} = 100 \text{ pF, } R_{b} = 2.7 \text{ k}\Omega$	0	1420	ns	
		2.4 V \leq EV _{DD} $<$ 3.3 V, 1.6 V \leq V _b \leq 2.0 V Note 2, C _b = 100 pF, R _b = 5.5 kΩ	0	1215	ns	



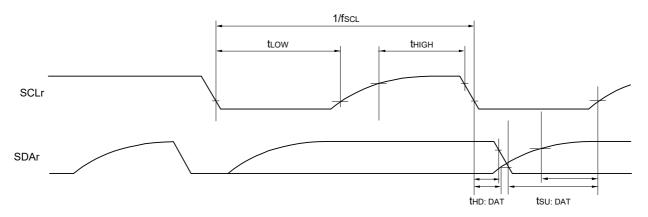
- Note 1. The value must be equal to or less than fMCK/4.
- Note 2. Use it with $EVDD \ge Vb$.
- **Note 3.** Set the fмcκ value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the TTL input buffer and the N-ch open drain output (EVDD tolerance) mode for the SDAr pin and the N-ch open drain output (EVDD tolerance) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



- **Remark 1.** Rb[Ω]: Communication line (SDAr, SCLr) pull-up resistance, Cb[F]: Communication line (SDAr, SCLr) load capacitance, Vb[V]: Communication line voltage
- **Remark 2.** r: IIC number (r = 00, 01, 10 and 11), g: PIM, POM number (g = 0, 3 and 5)
- Remark 3. fmck: Serial array unit operation clock frequency

 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0),

 n: Channel number (n = 0 to 3), mn = 00 to 03)

3.5.2 Serial interface IICA

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, VSS = 0 V)

Parameter	Symbol	Conditions	HS	HS (high-speed main) mode		mode	Unit
			Standa	rd mode	Fast	mode	
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode: fcLK ≥ 3.5 MHz	_	_	0	400	kHz
		Standard mode: fcLk ≥ 1 MHz	0	100	_	_	kHz
Setup time of restart condition	tsu: sta		4.7		0.6		μs
Hold time Note 1	thd: sta		4.0		0.6		μs
Hold time when SCLA0 = "L"	tLOW		4.7		1.3		μs
Hold time when SCLA0 = "H"	thigh		4.0		0.6		μs
Data setup time (reception)	tsu: dat		250		100		ns
Data hold time (transmission) Note 2	thd: dat		0	3.45	0	0.9	μs
Setup time of stop condition	tsu: sto		4.0		0.6		μs
Bus-free time	tBUF		4.7		1.3		μs

Note 1. The first clock pulse is generated after this period when the start/restart condition is detected.

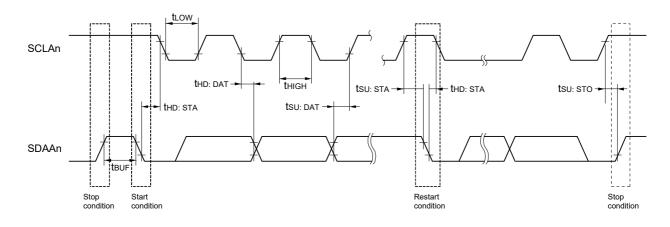
Note 2. The maximum value (MAX.) of thd: DAT is during normal transfer and a clock stretch state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR02) in the peripheral I/O redirection register 0 (PIOR0) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.

Remark The maximum value of C_b (communication line capacitance) and the value of R_b (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: C_b = 400 pF, R_b = 2.7 k Ω Fast mode: C_b = 320 pF, R_b = 1.1 k Ω

IICA serial transfer timing



Remark n = 0, 1

3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Reference Voltage Input channel	Reference voltage (+) = AVREFP Reference voltage (-) = AVREFM	Reference voltage (+) = V _{DD} Reference voltage (-) = Vss	Reference voltage (+) = V _{BGR} Reference voltage (-) = AV _{REFM}
ANI0 to ANI3	Refer to 3.6.1 (1).	Refer to 3.6.1 (3).	Refer to 3.6.1 (4).
ANI16 to ANI22	Refer to 3.6.1 (2).		
Internal reference voltage Temperature sensor output voltage	Refer to 3.6.1 (1) .		_

(1) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI2 and ANI3, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +105°C, 2.4 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution AVREFP = VDD Note 3	2.4 V ≤ AVREFP ≤ 5.5 V		1.2	±3.5	LSB
Conversion time	tconv	10-bit resolution	3.6 V ≤ V _{DD} ≤ 5.5 V	2.125		39	μs
		Target pin: ANI2 and ANI3	2.7 V ≤ V _{DD} ≤ 5.5 V	3.1875		39	μs
			2.4 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
		10-bit resolution	3.6 V ≤ V _{DD} ≤ 5.5 V	2.375		39	μs
		Target pin: Internal reference voltage, and temperature sensor output voltage	2.7 V ≤ V _{DD} ≤ 5.5 V	3.5625		39	μs
			2.4 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution AV _{REFP} = V _{DD} Note 3	2.4 V ≤ AVREFP ≤ 5.5 V			±0.25	%FSR
Full-scale error Notes 1, 2	Ers	10-bit resolution AVREFP = VDD Note 3	2.4 V ≤ AVREFP ≤ 5.5 V			±0.25	%FSR
Integral linearity error Note 1	ILE	10-bit resolution AVREFP = VDD Note 3	2.4 V ≤ AVREFP ≤ 5.5 V			±2.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution AVREFP = VDD Note 3	2.4 V ≤ AVREFP ≤ 5.5 V			±1.5	LSB
Analog input voltage	Vain	ANI2 and ANI3	•	0		AVREFP	V
		Internal reference voltage (2.4 V ≤ VDD ≤ 5.5 V)		V	V _{BGR} Note 4		
		Temperature sensor output voltage (2.4 V ≤ VDD ≤ 5.5 V)		VT	MPS25 No	te 4	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

Note 3. When AVREFP < VDD, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when AVREFP = VDD. Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AVREFP = VDD. Integral linearity error/ Differential linearity error: Add ± 0.5 LSB to the MAX. value when AVREFP = VDD.

Note 4. Refer to 3.6.2 Temperature sensor characteristics/internal reference voltage characteristic.



(2) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI16 to ANI22

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, 2.4 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Cond	litions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution EVDD ≤ AVREFP = VDD Notes 3, 4	2.4 V ≤ AVREFP ≤ 5.5 V		1.2	±5.0	LSB
Conversion time	tconv	10-bit resolution	3.6 V ≤ V _{DD} ≤ 5.5 V	2.125		39	μs
		Target ANI pin: ANI16 to ANI22	2.7 V ≤ V _{DD} ≤ 5.5 V	3.1875		39	μs
			2.4 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution EVDD ≤ AVREFP = VDD Notes 3, 4	2.4 V ≤ AVREFP ≤ 5.5 V			±0.35	%FSR
Full-scale error Notes 1, 2	Ers	10-bit resolution EVDD ≤ AVREFP = VDD Notes 3, 4	$2.4 \text{ V} \le \text{AVREFP} \le 5.5 \text{ V}$			±0.35	%FSR
Integral linearity error Note 1	ILE	10-bit resolution EVDD ≤ AVREFP = VDD Notes 3, 4	$2.4 \text{ V} \le \text{AVREFP} \le 5.5 \text{ V}$			±3.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution EVDD ≤ AVREFP = VDD Notes 3, 4	$2.4 \text{ V} \le \text{AVREFP} \le 5.5 \text{ V}$			±2.0	LSB
Analog input voltage	Vain	ANI16 to ANI22		0		AVREFP and EVDD	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

Note 3. When $EVDD \le AVREFP < VDD$, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when AVREFP = VDD. Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AVREFP = VDD. Integral linearity error/ Differential linearity error: Add $\pm 0.5\%$ FSR to the MAX. value when AVREFP = VDD.

Note 4. When AVREFP < EVDD \leq VDD, the MAX. values are as follows.

Overall error: Add ± 4.0 LSB to the MAX. value when AVREFP = VDD. Zero-scale error/Full-scale error: Add $\pm 0.20\%$ FSR to the MAX. value when AVREFP = VDD. Integral linearity error/ Differential linearity error: Add ± 2.0 LSB to the MAX. value when AVREFP = VDD.

(3) When reference voltage (+) = VDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = Vss (ADREFM = 0), target pin: ANI0 to ANI3, ANI16 to ANI22, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = VDD, Reference voltage (-) = Vss)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V		1.2	±7.0	LSB
Conversion time	tconv	10-bit resolution	3.6 V ≤ V _{DD} ≤ 5.5 V	2.125		39	μs
		Target pin: ANI0 to ANI3, ANI16 to ANI22	2.7 V ≤ V _{DD} ≤ 5.5 V	3.1875		39	μs
			2.4 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
		10-bit resolution	3.6 V ≤ V _{DD} ≤ 5.5 V	2.375		39	μs
		Target pin: internal reference voltage, and temperature sensor output voltage	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$	3.5625		39	μs
			2.4 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±0.60	%FSR
Full-scale error Notes 1, 2	Ers	10-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±0.60	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±4.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	2.4 V ≤ VDD ≤ 5.5 V			±2.0	LSB
Analog input voltage	Vain	ANI0 to ANI3	.	0		Vdd	V
		ANI16 to ANI22		0		EV _{DD}	V
		Internal reference voltage (2.4 V ≤ VDD ≤ 5.5 V)		V _{BGR} Note 3			V
	;	Temperature sensor output voltage (2.4 V \leq VDD \leq 5.5 V)		Vı	V _{TMPS25} Note 3		

- **Note 1.** Excludes quantization error (±1/2 LSB).
- Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.
- Note 3. Refer to 3.6.2 Temperature sensor characteristics/internal reference voltage characteristic.

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI0 to ANI3, ANI16 to ANI22

(TA = -40 to +105°C, 2.4 V \leq VDD \leq 5.5 V, 2.4 V \leq EVDD \leq VDD = 0 V,

Reference voltage (+) = VBGR Note 3, Reference voltage (-) = AVREFM = 0 V Note 4)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES		8			bit
Conversion time	tconv		17		39	μs
Zero-scale error Notes 1, 2	Ezs				±0.60	% FSR
Integral linearity error Note 1	ILE				±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution			±1.0	LSB
Analog input voltage	Vain		0		V _{BGR} Note 3	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

Note 3. Refer to 3.6.2 Temperature sensor characteristics/internal reference voltage characteristic.

Note 4. When reference voltage (-) = Vss, the MAX. values are as follows.

Zero-scale error: Add $\pm 0.35\%$ FSR to the MAX. value when reference voltage (-) = AVREFM. Integral linearity error: Add ± 0.5 LSB to the MAX. value when reference voltage (-) = AVREFM. Differential linearity error: Add ± 0.2 LSB to the MAX. value when reference voltage (-) = AVREFM.

3.6.2 Temperature sensor characteristics/internal reference voltage characteristic

$(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	VTMPS25	Setting ADS register = 80H, TA = +25°C		1.05		V
Internal reference voltage	VBGR	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	FVTMPS	Temperature sensor that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tamp	2.4 V ≤ VDD ≤ 3.6 V	5			μs

3.6.3 D/A converter (channel 1)

(TA = -40 to +105°C, 2.4 V \leq EVss \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Cor	MIN.	TYP.	MAX.	Unit	
Resolution	RES					8	bit
Overall error	AINL	Rload = 4 MΩ	$2.4 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$			±2.5	LSB
		Rload = 8 MΩ	$2.4 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$			±2.5	LSB
Settling time	tset	Cload = 20 pF	$2.7 \text{ V} \le \text{Vdd} \le 5.5 \text{ V}$			3	μs
			2.4 V ≤ V _{DD} < 2.7 V			6	μs

3.6.4 Comparator

(Comparator 0: TA = -40 to +105°C, 2.7 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V) (Comparator 1: TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Co	nditions	MIN.	TYP.	MAX.	Unit
Input voltage range	VIREF0	IVREF0 pin		0		V _{DD} - 1.4 Note 1	V
	VIREF1	IVREF1 pin		1.4 Note 1		VDD	V
	VICMP	IVCMP0 pin		-0.3		V _{DD} + 0.3	V
		IVCMP1 pin	-0.3		EV _{DD} + 0.3	V	
' '	td	V _{DD} = 3.0 V Input slew rate > 50 mV/μs	Comparator high-speed mode, standard mode			1.2	μs
		Comparator high-speed mode, window mode			2.0	μs	
		Comparator low-speed mode, standard mode		3		μs	
			Comparator low-speed mode, window mode		4		μs
Operation stabilization wait time	tcmp			100			μs
Reference voltage declination in channel 0 of internal DAC Note 2	∆VIDAC					±2.5	LSB

Note 1. In window mode, make sure that $VREF1 - VREF0 \ge 0.2 V$.

Note 2. Only in CMP0

3.6.5 PGA

(TA = -40 to +105°C, 2.7 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Cor	nditions	MIN.	TYP.	MAX.	Unit
Input offset voltage	VIOPGA					±10	mV
Input voltage range	VIPGA			0		0.9 × V _{DD} /Gain	٧
Output voltage range	VIOHPGA			$0.93 \times V_{DD}$			V
	VIOLPGA					$0.07 \times V_{DD}$	V
Gain error		x4, x8				±1	%
		x16				±1.5	%
		x32				±2	%
Slew rate		Rising When VIN = 0.1Vpb/gain to 0.9Vpb/gain. 10 to 90% of output	4.0 V ≤ V _{DD} ≤ 5.5 V (Other than x32)	3.5			V/µs
			4.0 V ≤ V _{DD} ≤ 5.5 V (x32)	3.0			
		voltage amplitude	2.7 V ≤ V _{DD} ≤ 4.0V	0.5			
		Falling When VIN= 0.1Vpb/gain to 0.9Vpb/gain.	4.0 V ≤ V _{DD} ≤ 5.5 V (Other than x32)	3.5			
		90 to 10% of output	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} (x32)$	3.0			
	voltage amplitude	$2.7 \text{ V} \leq \text{V}_{DD} \leq 4.0 \text{V}$	0.5				
Reference voltage	t PGA	x4, x8				5	μs
stabilization wait time ^{Note}		x16, x32				10	μs

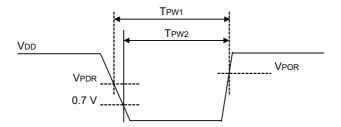
Note Time required until a state is entered where the DC and AC specifications of the PGA are satisfied after the PGA operation has been enabled (PGAEN = 1).

3.6.6 POR circuit characteristics

(TA = -40 to +105°C, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	VPOR	The power supply voltage is rising.	1.45	1.51	1.57	V
	VPDR	The power supply voltage is falling. Note 1	1.44	1.50	1.56	V
Minimum pulse width Note 2	Tpw1	Other than STOP/SUB HALT/SUB RUN	300			μs
	Tpw2	STOP/SUB HALT/SUB RUN	300			μs

- **Note 1.** However, when the operating voltage falls while the LVD is off, enter STOP mode, or enable the reset status using the external reset pin before the voltage falls below the operating voltage range shown in 3.4 AC Characteristics.
- Note 2. Minimum time required for a POR reset when VDD exceeds below VPDR. This is also the minimum time required for a POR reset from when VDD exceeds below 0.7 V to when VDD exceeds VPOR while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



3.6.7 LVD circuit characteristics

(1) LVD Detection Voltage of Reset Mode and Interrupt Mode

(TA = -40 to +105°C, VPDR \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Р	arameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	Supply voltage level	VLVD0	The power supply voltage is rising.	3.90	4.06	4.22	V
			The power supply voltage is falling.	3.83	3.98	4.13	V
		VLVD1	The power supply voltage is rising.	3.60	3.75	3.90	V
			The power supply voltage is falling.	3.53	3.67	3.81	V
		VLVD2	The power supply voltage is rising.	3.01	3.13	3.25	V
			The power supply voltage is falling.	2.94	3.06	3.18	V
		VLVD3	The power supply voltage is rising.	2.90	3.02	3.14	V
			The power supply voltage is falling.	2.85	2.96	3.07	V
		VLVD4	The power supply voltage is rising.	2.81	2.92	3.03	V
			The power supply voltage is falling.	2.75	2.86	2.97	V
		VLVD5	The power supply voltage is rising.	2.71	2.81	2.92	V
			The power supply voltage is falling.	2.64	2.75	2.86	V
		VLVD6	The power supply voltage is rising.	2.61	2.71	2.81	V
			The power supply voltage is falling.	2.55	2.65	2.75	V
		VLVD7	The power supply voltage is rising.	2.51	2.61	2.71	V
			The power supply voltage is falling.	2.45	2.55	2.65	V
Minimum pulse widt	th	tLW		300			μs
Detection delay time	е					300	μs

(2) LVD Detection Voltage of Interrupt & Reset Mode

(TA = -40 to +105°C, VPDR \leq EVDD \leq VDD \leq 5.5 V, VSS = 0 V)

Parameter	Symbol	Conditi	ions	MIN.	TYP.	MAX.	Unit
Interrupt and	VLVDD0	VPOC0, VPOC1, VPOC2 = 0, 1, 1, fallin	ng reset voltage	2.64	2.75	2.86	V
reset mode	VLVDD1	LVIS0, LVIS1 = 1, 0	2.81	2.92	3.03	V	
			Falling interrupt voltage	2.75	2.86	2.97	V
	VLVDD2	LVIS0, LVIS1 = 0, 1	Rising release reset voltage	2.90	3.02	3.14	V
			Falling interrupt voltage	2.85	2.96	3.07	V
	VLVDD3	LVIS0, LVIS1 = 0, 0	Rising release reset voltage	3.90	4.06	4.22	V
			Falling interrupt voltage	3.83	3.98	4.13	V

3.6.8 Power supply voltage rising slope characteristics

$(TA = -40 \text{ to } +105^{\circ}\text{C}, Vss = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until VDD reaches the operating voltage range shown in 3.4 AC Characteristics.

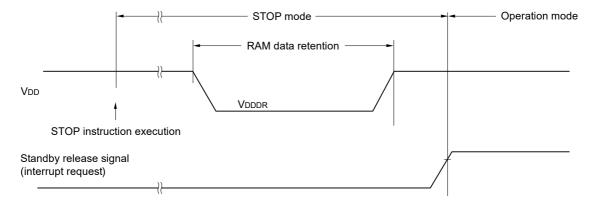


3.7 RAM Data Retention Characteristics

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, VSS = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.44 Note		5.5	V

Note The value depends on the POR detection voltage. When the voltage drops, the RAM data is retained before a POR reset is effected, but RAM data is not retained when a POR reset is effected.



3.8 Flash Memory Programming Characteristics

$(TA = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EVDD} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditi	MIN.	TYP.	MAX.	Unit	
System clock frequency	fclk	2.4 V ≤ VDD ≤ 5.5 V	1		24	MHz	
Number of code flash rewrites Notes 1, 2, 3	Cerwr	Retained for 20 years	TA = 85°C	1,000			Times
Number of data flash rewrites		Retained for 1 year	TA = 25°C		1,000,000		
Notes 1, 2, 3		Retained for 5 years	TA = 85°C	100,000			
		Retained for 20 years	Ta = 85°C	10,000			

- Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.
- Note 2. When using flash memory programmer and Renesas Electronics self-programming library
- **Note 3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

3.9 Dedicated Flash Memory Programmer Communication (UART)

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

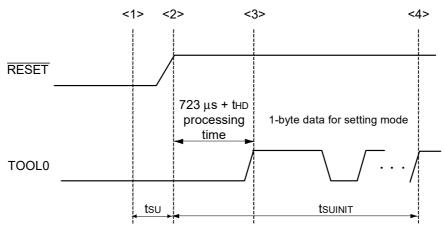
3.10 Timing of Entry to Flash Memory Programming Modes

(TA = -40 to +105°C, 2.4 V \leq EVDD \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
How long from when an external reset ends until the initial communication settings are specified Note 1	tsuinit	POR and LVD reset must end before the external reset ends.			100	ms
How long from when the TOOL0 pin is placed at the low level until an external reset ends Note 1	tsu	POR and LVD reset must end before the external reset ends.	10			μs
How long the TOOL0 pin must be kept at the low level after an external reset ends (excluding the processing time of the firmware to control the flash memory) Notes 1, 2	thD	POR and LVD reset must end before the external reset ends.	1			ms

Note 1. Deassertion of the POR and LVD reset signals must precede deassertion of the pin reset signal.

Note 2. This excludes the flash firmware processing time (723 μ s).



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset ends (POR and LVD reset must end before the external reset ends).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

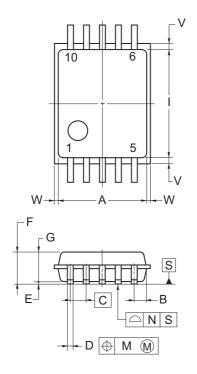
Remark tsuinit: The segment shows that it is necessary to finish specifying the initial communication settings within 100 ms from when the external resets end.

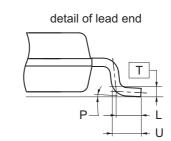
tsu: How long from when the TOOL0 pin is placed at the low level until a pin reset ends
thd: How long to keep the TOOL0 pin at the low level from when the external resets end
(excluding the processing time of the firmware to control the flash memory)

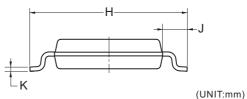
4. PACKAGE DRAWINGS

4.1 10-pin package

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP10-4.4x3.6-0.65	PLSP0010JA-A	P10MA-65-CAC-2	0.05







ITEM DIMENSIONS Α 3.60±0.10 В 0.50 С 0.65 (T.P.) D 0.24 ± 0.08 Е 0.10 ± 0.05 F 1.45 MAX. G 1.20±0.10 Н 6.40 ± 0.20 4.40 ± 0.10 J

0.25 MAX.

0.15 MAX.

©2012 Renesas Electronics Corporation. All rights reserved.

٧

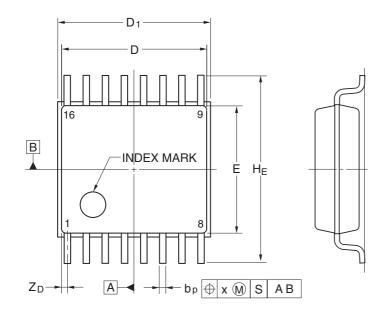
W

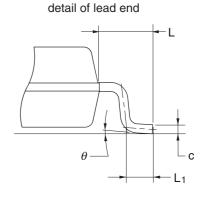
NOTE

Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.

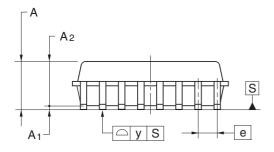
16-pin package 4.2

JEITA Package code	RENESAS code	Previous code	MASS(TYP.)[g]
P-SSOP16-4.4x5-0.65	PRSP0016JC-B	P16MA-65-FAB	0.08



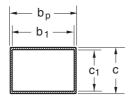


Dimension in Millimeters

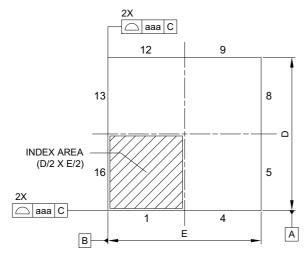


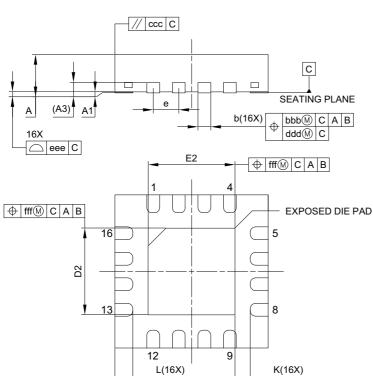
Referance Symbol Nom Max Min 4.85 5.00 5.15 5.20 D₁ 5.05 5.35 Ε 4.40 4.20 4.60 1.50 0.075 0.125 0.175 Α 1.725 0.17 0.32 bр 0.24 0.22 $b_1 \\$ С 0.17 0.20 0.14 c_1 0.15 8° 0° H_{E} 6.40 6.20 6.60 е 0.65 Х 0.13 0.10 Z_{D} 0.225 L 0.50 0.65 0.35 1.00 L_1

Terminal cross section



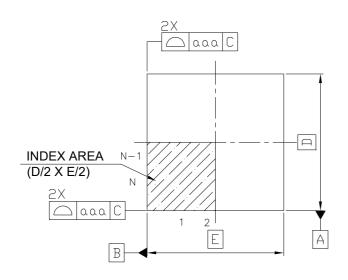
JEITA Package code	RENESAS code	MASS(TYP.)[g]
P-HWQFN016-3x3-0.50	PWQN0016KD-A	0.02

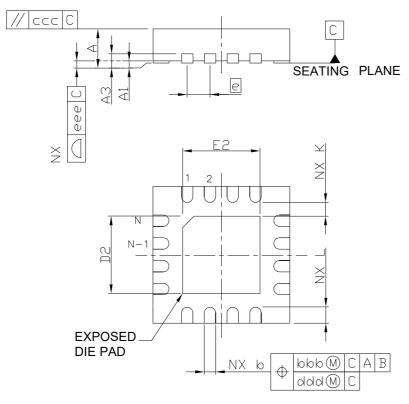




Dimension in Millimeters		
Min.	Nom.	Max.
_	_	0.80
0.00	0.02	0.05
	0.203 REF	=
0.20	0.25	0.30
3.00 BSC		
3.00 BSC		
0.50 BSC		
0.30	0.35	0.40
0.20	_	_
1.65	1.70	1.75
1.65	1.70	1.75
	0.15	
	0.10	
0.10		
	0.05	
0.08		
0.10		
	Min. — 0.00 0.20 0.30 0.20 1.65	Min. Nom. 0.00 0.02 0.203 REF 0.20 0.25 3.00 BSC 3.00 BSC 0.50 BSC 0.30 0.35 0.20 - 1.65 1.70 1.65 1.70 0.15 0.10 0.10 0.05 0.08

JEITA Package Code	RENESAS Code	MASS(Typ.)[g]
P-HWQFN16-3×3-0.50	PWQN0016KE-A	0.02

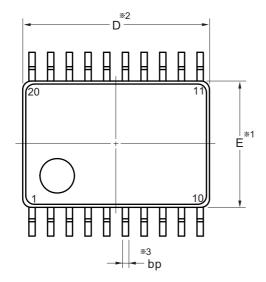




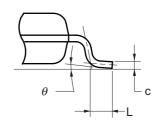
Reference	Dimension in Millimeters		
Symbol	Min.	Nom.	Max.
Α	_	_	0.80
A ₁	0.00	_	0.05
A ₃	0	.20 REF	=.
b	0.20	0.25	0.30
D	_	3.00	_
E	_	3.00	_
е	1	0.50	_
N		16	
L	0.25	0.35	0.45
K	0.20	_	_
D ₂	1.60	1.70	1.80
E ₂	1.60	1.70	1.80
aaa	_	_	0.15
bbb	_	_	0.10
ccc	_	_	0.10
ddd	_	_	0.05
eee	_	_	0.08

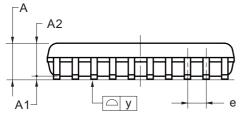
4.3 20-pin package

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP20-4.4x6.5-0.65	PLSP0020JB-A	P20MA-65-NAA-1	0.1



detail of lead end







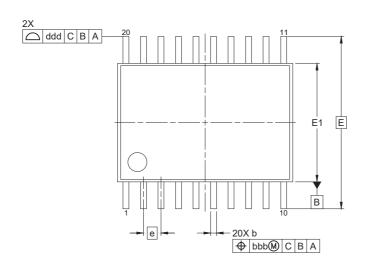
NOTE

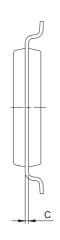
- 1. Dimensions "%1" and "%2" do not include mold flash.
- 2.Dimension "X3" does not include trim offset.

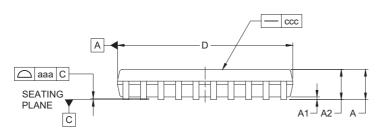
	(UNIT:mm)
ITEM	DIMENSIONS
D	6.50±0.10
E	4.40±0.10
HE	6.40±0.20
Α	1.45 MAX.
A1	0.10±0.10
A2	1.15
е	0.65±0.12
bp	0.22 + 0.10 -0.05
С	$0.15 \pm 0.05 \\ -0.02$
L	0.50±0.20
У	0.10
θ	0° to 10°

 \bigcirc 2012 Renesas Electronics Corporation. All rights reserved.

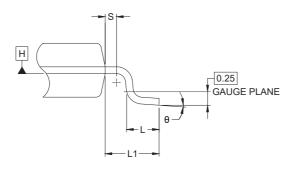
JEITA Package code	RENESAS code	MASS(TYP.)[g]
P-TSSOP20-4.40x6.50-0.65	PTSP0020JI-A	0.08







Detail of Lead End



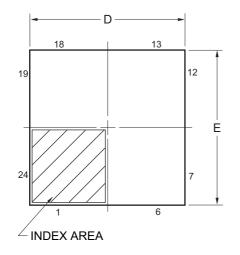
NO	т	FS:

- 1.DIMENSION 'D' AND 'E1' DOES NOT INCLUDE MOLD FLASH.
 2.DIMENSION 'b' DOES NOT INCLUDE TRIM OFFSET.
 3.DIMENSION 'D' AND 'E1' TO BE DETERMINED AT DATUM PLANE H.

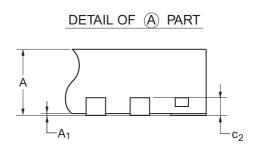
Reference	Dimension in Millimeters			
Symbol	Min.	Nom.	Max.	
А	_	_	1.20	
A1	0.05	-	0.15	
A2	0.80	1.00	1.05	
b	0.19	_	0.30	
С	0.09	0.127	0.20	
D	6.40	6.50	6.60	
E1	4.30	4.40	4.50	
E	6.40 BSC			
е		0.65 BSC		
L1		1.00 REF		
L	0.50	0.60	0.75	
S	0.20	_	_	
θ	0°	_	8°	
aaa		0.10		
bbb		0.10		
ccc		0.05		
ddd	0.20			

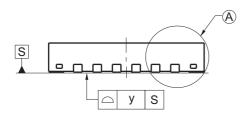
4.4 24-pin package

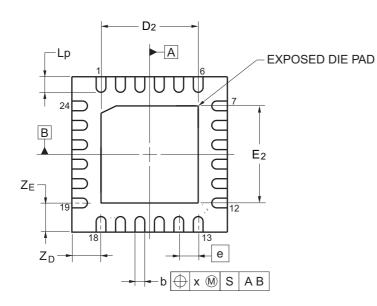
JEITA Package code	RENESAS code	Previous code	MASS(TYP.)[g]
P-HWQFN24-4x4-0.50	PWQN0024KE-A	P24K8-50-CAB-3	0.04







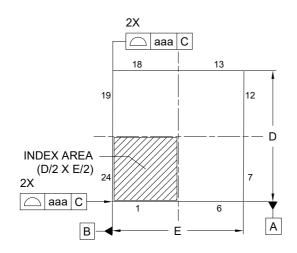


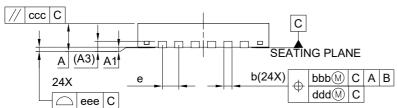


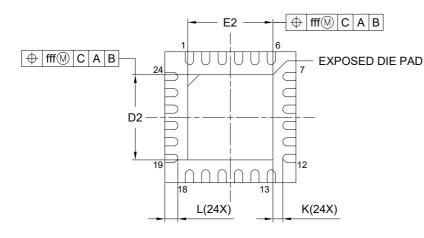
Referance	Dimens	sion in Mil	sion in Millimeters	
Symbol	Min	Nom	Max	
D	3.95	4.00	4.05	
Е	3.95	4.00	4.05	
Α			0.80	
A ₁	0.00			
b	0.18	0.25	0.30	
е		0.50		
Lp	0.30	0.40	0.50	
х			0.05	
у			0.05	
Z _D		0.75		
Z _E		0.75		
c ₂	0.15	0.20	0.25	
D ₂		2.50		
E ₂		2.50		

©2013 Renesas Electronics Corporation. All rights reserved.

JEITA Package code	RENESAS code	MASS(TYP.)[g]
P-HWQFN024-4x4-0.50	PWQN0024KF-A	0.04

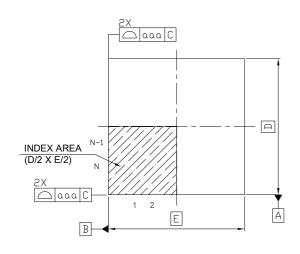


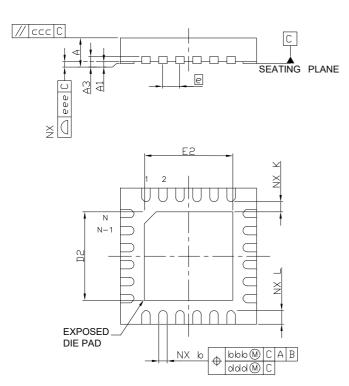




Reference	Dimen	sion in Milli	meters
Symbol	Min.	Nom.	Max.
Α	_	_	0.80
A1	0.00	0.02	0.05
A3		0.203 REF	
b	0.18	0.25	0.30
D		4.00 BSC	
E		4.00 BSC	
е	0.50 BSC		
L	0.35	0.40	0.45
K	0.20	_	_
D2	2.55	2.60	2.65
E2	2.55	2.60	2.65
aaa	0.15		
bbb		0.10	
ccc	0.10		
ddd	0.05 0.08		
eee			
fff	0.10		

JEITA Package Code	RENESAS Code	MASS(Typ.)[g]
P-HWQFN24-4×4-0.50	PWQN0024KH-A	0.04

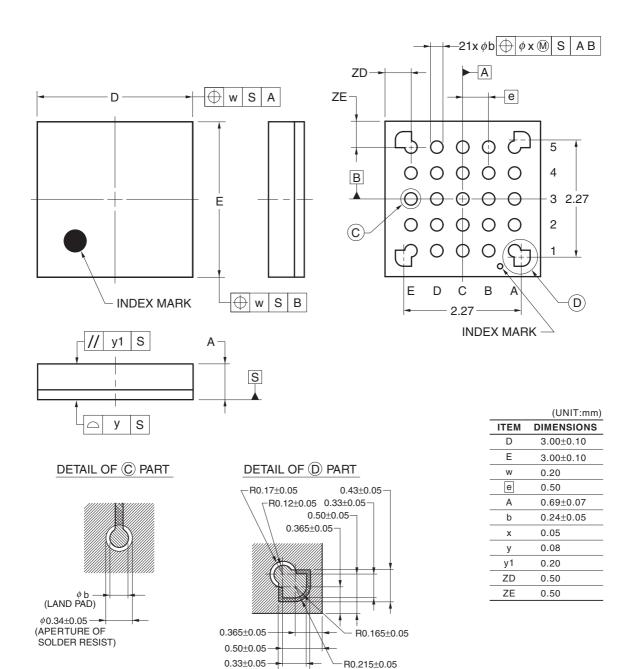




Reference	Dimension in Millimeters			
Symbol	Min.	Nom.	Max.	
А	_	_	0.80	
A ₁	0.00	_	0.05	
A_3	0	.20 REF	=.	
b	0.20	0.25	0.30	
D	_	4.00	_	
E	_	4.00	_	
е	_	0.50	_	
N	24			
L	0.30	0.40	0.50	
K	0.20	_	_	
D ₂	2.50	2.60	2.70	
E ₂	2.50	2.60	2.70	
aaa	_	_	0.15	
bbb	_	_	0.10	
ссс	_	_	0.10	
ddd	_	_	0.05	
eee	_	_	0.08	

4.5 25-pin package

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-WFLGA25-3x3-0.50	PWLG0025KA-A	P25FC-50-2N2-2	0.01



©2012 Renesas Electronics Corporation. All rights reserved.

0.43±0.05

RF\	/ISION	JHIST	TORY
1 \L V			

RL78/G11 Datasheet

Description Description		Description	
Rev.	Date	Page	Summary
0.50	Mar 31 2016	_	First Edition issued
1.00	1.00 Sep 28 2016 p.7		Modification of Pin Configuration in 1.3.3 25-pin products
		p.9	Addition of 1.5.1 20-pin products
		p.10	Addition of product name and Modification of Block Diagram in 1.5.2 24-pin, 25-pin products
		p.12	Addition of I ² C bus in 1.6 Outline of Functions
		p.15	Modification of Conditions of IOH1, IOL1 in 2.1 Absolute Maximum Ratings
		p.16	Modification of High-speed on-chip oscillator clock frequency accuracy and addition of DIMT, DIMV in 2.2.2 On-chip oscillator characteristics
		p.17	Modification of Caution in 2.3.1 Pin characteristics
		p.19	Modification of Input voltage, high and Input voltage, low in 2.3.1 Pin characteristics
		p.19, 20	Modification of Caution in 2.3.1 Pin characteristics
		p.22, 23, 24, 26, 27	Modification of specifications in 2.3.2 Supply current characteristics
		p.29, 30	Modification of specification in 2.4 AC Characteristics
		p.35	Modification of specifications in 2.5.1 Serial array unit (1)
		p.39	Modification of specifications in 2.5.1 Serial array unit (3)
		p.40, 42	Modification of specification in 2.5.1 Serial array unit (4)
		p.62	Addition of LP (Low-power main) mode in 2.5.2 Serial interface IICA (1)
		p.64	Addition of LP (Low-power main) mode in 2.5.2 Serial interface IICA (2)
		p.65	Addition of LP (Low-power main) mode in 2.5.2 Serial interface IICA (3)
		p.70	Modification of Conditions in 2.6.2 Temperature sensor haracteristics/internal reference voltage characteristic
		p.79	Addition of description in 3 ELECTRICAL SPECIFICATIONS (TA = -40 to +105°C)
		p.82	Modification of High-speed on-chip oscillator clock frequency accuracy and addition of DIMT, DIMV in 3.2.2 On-chip oscillator characteristics
		p.83	Modification of Caution in 3.3.1 Pin characteristics
		p.85	Modification of Input voltage, high and Input voltage, low in 3.3.1 Pin characteristics
		p.85, 86	Modification of Caution in 3.3.1 Pin characteristics
		p.88 to 91	Modification of specifications in 3.3.2 Supply current characteristics
		p.97	Modification of specifications and specification table in 3.5.1 Serial array unit (1)
		p.103	Modification of specifications in 3.5.1 Serial array unit (3)
		p.125	Modification of Conditions in 3.6.1 A/D converter characteristics (4)
		p.126	Modification of Conditions in 3.6.2 Temperature sensor haracteristics/internal reference voltage characteristic
1.10	Dec 28 2016	p.4	Modification of 1.2 Ordering Information
2.00	Feb 15, 2018	Throughout	Addition of specifications of 10-pin and 16-pin products
		p.2	Modification of description in 1.1 Features
		p.6	Modification of figure in 1.3.4 24-pin products
		p.11	Modification of figure in 1.5.3 20-pin products
		p.12	Modification of figure in 1.5.4 24-pin, 25-pin products

Pov	Data		Description
Rev.	Date	Page	Summary
2.00	Feb 15, 2018	p.13, 14	Modification of table in 1.6 Outline of Functions
		p.18	Modification of 2.2.2 On-chip oscillator characteristics
		p.19, 21	Modification of 2.3.1 Pin characteristics
		p.24	Modification of 2.3.2 Supply current characteristics
		p.32	Modification of 2.4 AC Characteristics
		p.79	Modification of figure in 2.10 Timing of Entry to Flash Memory Programming Modes
		p.84	Modification of 3.2.1 X1 characteristics
		p.84	Modification of 3.2.2 On-chip oscillator characteristics
		p.85, 86, 87	Modification of 3.3.1 Pin characteristics
		p.95	Modification of 3.4 AC Characteristics
		p.99	Modification of note in 3.5.1 Serial array unit (1)
		p.134	Modification of figure in 3.10 Timing of Entry to Flash Memory Programming Modes
2.20	Apr 26, 2019	p.3	Addition of note in Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G11
		p.5	Modification of figure in 1.3.1 10-pin products
		p.5	Modification of figure in 1.3.2 16-pin products
		p.5	Modification of figure in 1.3.3 20-pin products
		p.6	Modification of figure in 1.3.4 24-pin products
		p.13, 14	Modification of table in 1.6 Outline of Functions
		p.16	Modification of specification in 2.1 Absolute Maximum Ratings
		p.19, 22	Modification of specification in 2.3.1 Pin characteristics
		p.25, 27	Modification of note 1 in 2.3.2 Supply current characteristics
		p.29, 30	Modification of specification and addition of note 14 in 2.3.2 Supply current characteristics, Peripheral Functions (Common to all products)
		p.32	Modification of specification in 2.4 AC Characteristics
		p.36	Modification of note 2 in 2.5.1 Serial array unit, (1) During communication at same potential (UART mode)
		p.41	Modification of specification in 2.5.1 Serial array unit, (3) During communication at same potential (CSI mode) (master mode, SCKp internal clock output), When P20 is used as SO10 pin
		p.43	Modification of specification in 2.5.1 Serial array unit, (4) During communication at same potential (CSI mode) (slave mode, SCKp external clock input), When P01, P32, P53, P54 and P56 are used as SOmn pins
		p.44	Modification of specification in 2.5.1 Serial array unit, (4) During communication at same potential (CSI mode) (slave mode, SCKp external clock input), When P20 is used as SO10 pin
		p.47	Modification of specification in 2.5.1 Serial array unit, (5) During communication at same potential (simplified I ² C mode)
		p.53, 54	Modification of specification in 2.5.1 Serial array unit, (7) Communication at different potential (1.8 V, 2.5 V, 3.0 V) (CSI mode) (master mode, SCKp internal clock output, corresponding CSI00 only)
		p.60	Modification of note 3 in 2.5.1 Serial array unit, (9) Communication at different potential (1.8 V, 2.5 V, 3.0 V) (CSI mode) (slave mode, SCKp external clock input)

	. Date		Description
Rev.		Page	Summary
2.20	0 Apr 26, 2019	p.69	Modification of note 3 in 2.6.1 A/D converter characteristics, (2) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI16 to ANI22
		p.70	Modification of specification in 2.6.1 A/D converter characteristics, (3) When reference voltage (+) = VDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = Vss (ADREFM = 0), target pin: ANI0 to ANI3, ANI16 to ANI22, internal reference voltage, and temperature sensor output voltage
		p.71	Modification of specification in 2.6.1 A/D converter characteristics, (4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI0, ANI2 and ANI3, ANI16 to ANI22
		p.72	Modification of title in 2.6.3 D/A converter (channel 1)
		p.73	Modification of specification in 2.6.4 Comparator
		p.82	Modification of specification in 3.1 Absolute Maximum Ratings
		p.84	Modification of specification in 3.2.1 X1 characteristics
		p.85, 87, 88	Modification of specification in 3.3.1 Pin characteristics
		p.93	Modification of specification in 3.3.2 Supply current characteristics, Peripheral Functions (Common to all products)
		p.99	Modification of specification in 3.5.1 Serial array unit, (1) during communication at same potential (UART mode), When P20 is used as TxD1 pin
		p.101	Modification of specification in 3.5.1 Serial array unit, (2) During communication at same potential (CSI mode) (master mode, SCKp internal clock output), When P01, P32, P53, P54 and P56 are used as Somn pins
		p.102	Modification of specification in 3.5.1 Serial array unit, (2) During communication at same potential (CSI mode) (master mode, SCKp internal clock output), When P20 is used as SO10 pin
		p.103	Modification of note 1 in 3.5.1 Serial array unit, (3) During communication at same potential (CSI mode) (slave mode, SCKp external clock input), When P01, P32, P53, P54 and P56 are used as SOmn pins
		p.105	Modification of specification and note 1 in 3.5.1 Serial array unit, (3) During communication at same potential (CSI mode) (slave mode, SCKp external clock input), When P20 is used as SO10 pin
		p.124	Modification of specification in 3.6.1 A/D converter characteristics, (1) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI2 and ANI3, internal reference voltage, and temperature sensor output voltage
		p.125	Modification of note 3 in 3.6.1 A/D converter characteristics, (2) When reference voltage (+) = AVREFP/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI16 to ANI22
		p.127	Modification of specification in 3.6.1 A/D converter characteristics, (4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI0 to ANI3, ANI16 to ANI22
		p.128	Modification of title in 3.6.3 D/A converter (channel 1)
		p.129	Modification of specification in 3.6.4 Comparator
		p.131	Modification of specification in 3.6.6 POR circuit characteristics
		p.132	Modification of specification in 3.6.7 LVD circuit characteristics, (1) LVD Detection Voltage of Reset Mode and Interrupt Mode

Rev.	Date		Description
Rev.		Page	Summary
2.30	June 30, 2020	p.3	Modification of Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G11
		p.4	Modification of table in 1.2 Ordering Information
		p.5	Modification of description in 1.3.3 20-pin products
		p.26	Modification of specification in 2.3.2 Supply current characteristics
		p.138	Addition of package drawing in 4.3 20-pin package
		p.140	Addition of package drawing in 4.4 24-pin package
2.40	Oct 30, 2020	p.3	Modification of Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G11
		p.4	Modification of table in 1.2 Ordering Information
		p.6	Addition of description and figure in 1.3.2 16-pin products
		p.138	Addition of package drawing in 4.2 16-pin package
2.50	Mar 20, 2023	All	The module name for CSI was changed to Simplified SPI (CSI)
		All	"wait" for IIC was modified to "clock stretch"
		p.2	Addition of Note 1 in 1 Features
		p.4	Addition of Table Title and modification of Table 1-1 List of Ordering Part Numbers
		p.26	Modification of Note 1 in Table (TA = -40 to +85°C, 1.6 V ≤ EEVDD ≤ VDD ≤ 5.5 V, VSS = 0
			V) (2/4) of 2.3.2 Supply current characteristics
		p.28	Modification of Note 1 in Table (TA = -40 to +85°C, 1.6 V ≤ EEVDD ≤ VDD ≤ 5.5 V, Vss = 0
			V) (3/4) of 2.3.2 Supply current characteristics
		p.29	Modification of Note 1 in Table (TA = -40 to +85°C, 1.6 V \leq EEVDD \leq VDD \leq 5.5 V, VSS = 0
		04	V) (4/4) of 2.3.2 Supply current characteristics
		p.91	Modification of Note 1 in Table (TA = -40 to +105°C, 2.4 V ≤ EVDD≤ VDD ≤ 5.5 V, Vss = 0 V)) (1/3) of 2.3.2 Supply current characteristics
		p.92	Modification of Note 1 in Table (TA = -40 to +105°C, 2.4 V ≤ EVDD≤ VDD ≤ 5.5 V, Vss = 0
			V)) (2/3) of 2.3.2 Supply current characteristics
		p.93	Modification of Note 1 in Table (TA = -40 to +105°C, 2.4 V ≤ EVDD≤ VDD ≤ 5.5 V, Vss = 0
			V)) (3/3) of 2.3.2 Supply current characteristics
		p.139	Addition of package drawing in 4.2 16-pin Package
		p.144	Addition of package drawing in 4.4 24-pin Package
2.60	Mar 29, 2024	p.3	Modification of Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G11
		p.4	Modification of Table 1 - 1 List of Ordering Part Numbers

SuperFlash is a registered trademark of Silicon Storage Technology, Inc. in several countries including the United States and Japan.

Caution: This product uses SuperFlash® technology licensed from Silicon Storage Technology, Inc.

All trademarks and registered trademarks are the property of their respective owners.

General Precautions in the Handling of Microprocessing Unit and Microcontroller Unit Products

The following usage notes are applicable to all Microprocessing unit and Microcontroller unit products from Renesas. For detailed usage notes on the products covered by this document, refer to the relevant sections of the document as well as any technical updates that have been issued for the products.

1. Precaution against Electrostatic Discharge (ESD)

A strong electrical field, when exposed to a CMOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop the generation of static electricity as much as possible, and quickly dissipate it when it occurs. Environmental control must be adequate. When it is dry, a humidifier should be used. This is recommended to avoid using insulators that can easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors must be grounded. The operator must also be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions must be taken for printed circuit boards with mounted semiconductor devices.

2. Processing at power-on

The state of the product is undefined at the time when power is supplied. The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the time when power is supplied. In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the time when power is supplied until the reset process is completed. In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the time when power is supplied until the power reaches the level at which resetting is specified.

3. Input of signal during power-off state

Do not input signals or an I/O pull-up power supply while the device is powered off. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Follow the guideline for input signal during power-off state as described in your product documentation.

4. Handling of unused pins

Handle unused pins in accordance with the directions given under handling of unused pins in the manual. The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of the LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible.

5. Clock signals

After applying a reset, only release the reset line after the operating clock signal becomes stable. When switching the clock signal during program execution, wait until the target clock signal is stabilized. When the clock signal is generated with an external resonator or from an external oscillator during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Additionally, when switching to a clock signal produced with an external resonator or by an external oscillator while program execution is in progress, wait until the target clock signal is stable.

6. Voltage application waveform at input pin

Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between V_{IL} (Max.) and V_{IH} (Min.) due to noise, for example, the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between V_{IL} (Max.) and V_{IH} (Min.).

7. Prohibition of access to reserved addresses

Access to reserved addresses is prohibited. The reserved addresses are provided for possible future expansion of functions. Do not access these addresses as the correct operation of the LSI is not guaranteed.

8. Differences between products

Before changing from one product to another, for example to a product with a different part number, confirm that the change will not lead to problems. The characteristics of a microprocessing unit or microcontroller unit products in the same group but having a different part number might differ in terms of internal memory capacity, layout pattern, and other factors, which can affect the ranges of electrical characteristics, such as characteristic values, operating margins, immunity to noise, and amount of radiated noise. When changing to a product with a different part number, implement a system-evaluation test for the given product.

Notice

- 1. Descriptions of circuits, software and other related information in this document are provided only to illustrate the operation of semiconductor products and application examples. You are fully responsible for the incorporation or any other use of the circuits, software, and information in the design of your product or system. Renesas Electronics disclaims any and all liability for any losses and damages incurred by you or third parties arising from the use of these circuits, software, or information.
- Renesas Electronics hereby expressly disclaims any warranties against and liability for infringement or any other claims involving patents, copyrights, or other intellectual property rights of third parties, by or arising from the use of Renesas Electronics products or technical information described in this document, including but not limited to, the product data, drawings, charts, programs, algorithms, and application examples.
- No license, express, implied or otherwise, is granted hereby under any patents, copyrights or other intellectual property rights of Renesas Electronics or others.
- 4. You shall be responsible for determining what licenses are required from any third parties, and obtaining such licenses for the lawful import, export, manufacture, sales, utilization, distribution or other disposal of any products incorporating Renesas Electronics products, if required.
- 5. You shall not alter, modify, copy, or reverse engineer any Renesas Electronics product, whether in whole or in part. Renesas Electronics disclaims any and all liability for any losses or damages incurred by you or third parties arising from such alteration, modification, copying or reverse engineering.
- 6. Renesas Electronics products are classified according to the following two quality grades: "Standard" and "High Quality". The intended applications for each Renesas Electronics product depends on the product's quality grade, as indicated below.
 - "Standard": Computers; office equipment; communications equipment; test and measurement equipment; audio and visual equipment; home electronic appliances; machine tools; personal electronic equipment; industrial robots; etc.
 - "High Quality": Transportation equipment (automobiles, trains, ships, etc.); traffic control (traffic lights); large-scale communication equipment; key financial terminal systems; safety control equipment; etc.

Unless expressly designated as a high reliability product or a product for harsh environments in a Renesas Electronics data sheet or other Renesas Electronics document, Renesas Electronics products are not intended or authorized for use in products or systems that may pose a direct threat to human life or bodily injury (artificial life support devices or systems; surgical implantations; etc.), or may cause serious property damage (space system; undersea repeaters; nuclear power control systems; aircraft control systems; key plant systems; military equipment; etc.). Renesas Electronics disclaims any and all liability for any damages or losses incurred by you or any third parties arising from the use of any Renesas Electronics product that is inconsistent with any Renesas Electronics data sheet, user's manual or other Renesas Electronics document.

- 7. No semiconductor product is absolutely secure. Notwithstanding any security measures or features that may be implemented in Renesas Electronics hardware or software products, Renesas Electronics shall have absolutely no liability arising out of any vulnerability or security breach, including but not limited to any unauthorized access to or use of a Renesas Electronics product or a system that uses a Renesas Electronics product. RENESAS ELECTRONICS DOES NOT WARRANT OR GUARANTEE THAT RENESAS ELECTRONICS PRODUCTS, OR ANY SYSTEMS CREATED USING RENESAS ELECTRONICS PRODUCTS WILL BE INVULNERABLE OR FREE FROM CORRUPTION, ATTACK, VIRUSES, INTERFERENCE, HACKING, DATA LOSS OR THEFT, OR OTHER SECURITY INTRUSION ("Vulnerability Issues"). RENESAS ELECTRONICS DISCLAIMS ANY AND ALL RESPONSIBILITY OR LIABILITY ARISING FROM OR RELATED TO ANY VULNERABILITY ISSUES. FURTHERMORE, TO THE EXTENT PERMITTED BY APPLICABLE LAW, RENESAS ELECTRONICS DISCLAIMS ANY AND ALL WARRANTIES, EXPRESS OR IMPLIED, WITH RESPECT TO THIS DOCUMENT AND ANY RELATED OR ACCOMPANYING SOFTWARE OR HARDWARE, INCLUDING BUT NOT LIMITED TO THE IMPLIED WARRANTIES OF MERCHANTABILITY, OR FITNESS FOR A PARTICULAR PURPOSE.
- 8. When using Renesas Electronics products, refer to the latest product information (data sheets, user's manuals, application notes, "General Notes for Handling and Using Semiconductor Devices" in the reliability handbook, etc.), and ensure that usage conditions are within the ranges specified by Renesas Electronics with respect to maximum ratings, operating power supply voltage range, heat dissipation characteristics, installation, etc. Renesas Electronics disclaims any and all liability for any malfunctions, failure or accident arising out of the use of Renesas Electronics products outside of such specified ranges.
- 9. Although Renesas Electronics endeavors to improve the quality and reliability of Renesas Electronics products, semiconductor products have specific characteristics, such as the occurrence of failure at a certain rate and malfunctions under certain use conditions. Unless designated as a high reliability product or a product for harsh environments in a Renesas Electronics data sheet or other Renesas Electronics document, Renesas Electronics products are not subject to radiation resistance design. You are responsible for implementing safety measures to guard against the possibility of bodily injury, injury or damage caused by fire, and/or danger to the public in the event of a failure or malfunction of Renesas Electronics products, such as safety design for hardware and software, including but not limited to redundancy, fire control and malfunction prevention, appropriate treatment for aging degradation or any other appropriate measures. Because the evaluation of microcomputer software alone is very difficult and impractical, you are responsible for evaluating the safety of the final products or systems manufactured by you.
- 10. Please contact a Renesas Electronics sales office for details as to environmental matters such as the environmental compatibility of each Renesas Electronics product. You are responsible for carefully and sufficiently investigating applicable laws and regulations that regulate the inclusion or use of controlled substances, including without limitation, the EU RoHS Directive, and using Renesas Electronics products in compliance with all these applicable laws and regulations. Renesas Electronics disclaims any and all liability for damages or losses occurring as a result of your noncompliance with applicable laws and regulations.
- 11. Renesas Electronics products and technologies shall not be used for or incorporated into any products or systems whose manufacture, use, or sale is prohibited under any applicable domestic or foreign laws or regulations. You shall comply with any applicable export control laws and regulations promulgated and administered by the governments of any countries asserting jurisdiction over the parties or transactions.
- 12. It is the responsibility of the buyer or distributor of Renesas Electronics products, or any other party who distributes, disposes of, or otherwise sells or transfers the product to a third party, to notify such third party in advance of the contents and conditions set forth in this document.
- 13. This document shall not be reprinted, reproduced or duplicated in any form, in whole or in part, without prior written consent of Renesas Electronics.
- 14. Please contact a Renesas Electronics sales office if you have any questions regarding the information contained in this document or Renesas Electronics products.
- (Note1) "Renesas Electronics" as used in this document means Renesas Electronics Corporation and also includes its directly or indirectly controlled subsidiaries.
- (Note2) "Renesas Electronics product(s)" means any product developed or manufactured by or for Renesas Electronics.

(Rev.5.0-1 October 2020)

Corporate Headquarters

TOYOSU FORESIA, 3-2-24 Toyosu, Koto-ku, Tokyo 135-0061, Japan www.renesas.com

Trademarks

Renesas and the Renesas logo are trademarks of Renesas Electronics Corporation. All trademarks and registered trademarks are the property of their respective owners.

Contact Information

For further information on a product, technology, the most up-to-date version of a document, or your nearest sales office, please visit: www.renesas.com/contact/

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Renesas Electronics:

<u>R5F1057AANA#60</u> <u>R5F1056AASM#70</u> <u>R5F1057AGNA#60</u> <u>R5F1051AASP#70</u> <u>R5F1051AGSP#70</u> R5F1056AGSM#70 R5F1054AGNA#60 R5F1054AANA#60 R5F1054AASP#70 R5F1054AGSP#70